



INTRODUCCION A NANOCIENCIA

*Conceptos básicos y aplicaciones en Nanociencia
y Nanotecnología*

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CENM**

Universidad del Valle



CENM

Centro de Excelencia en Nuevos Materiales



Que somos
Motivación
Lineas de investigación
Miembros participantes
Sectores de aplicación
Grupos científicos
Artículos Científicos
Bibliografía adquirida
Convocatorias
Marco legal
Formatos
Organigrama
Directorio
Equipo adquirido
Financiación
Prospectiva y vigilancia
Informes
Eventos
Contáctenos
Inicio



intro...

FP 7 Program :



**European Union and
American Ti, Oxides,
Nanostructures - EUL
Project 2007
FP7-NMP-2007-2007-4
Sub-Scheme CSA-CA**

Información....

CENTER OF EXCELLENCE FOR NOVEL MATERIALS



- ❑ 19 research groups Researchers: 80 PhDs
- ❑ Sponsorship: PhD and Msc. students:
- ❑ Publications: 238

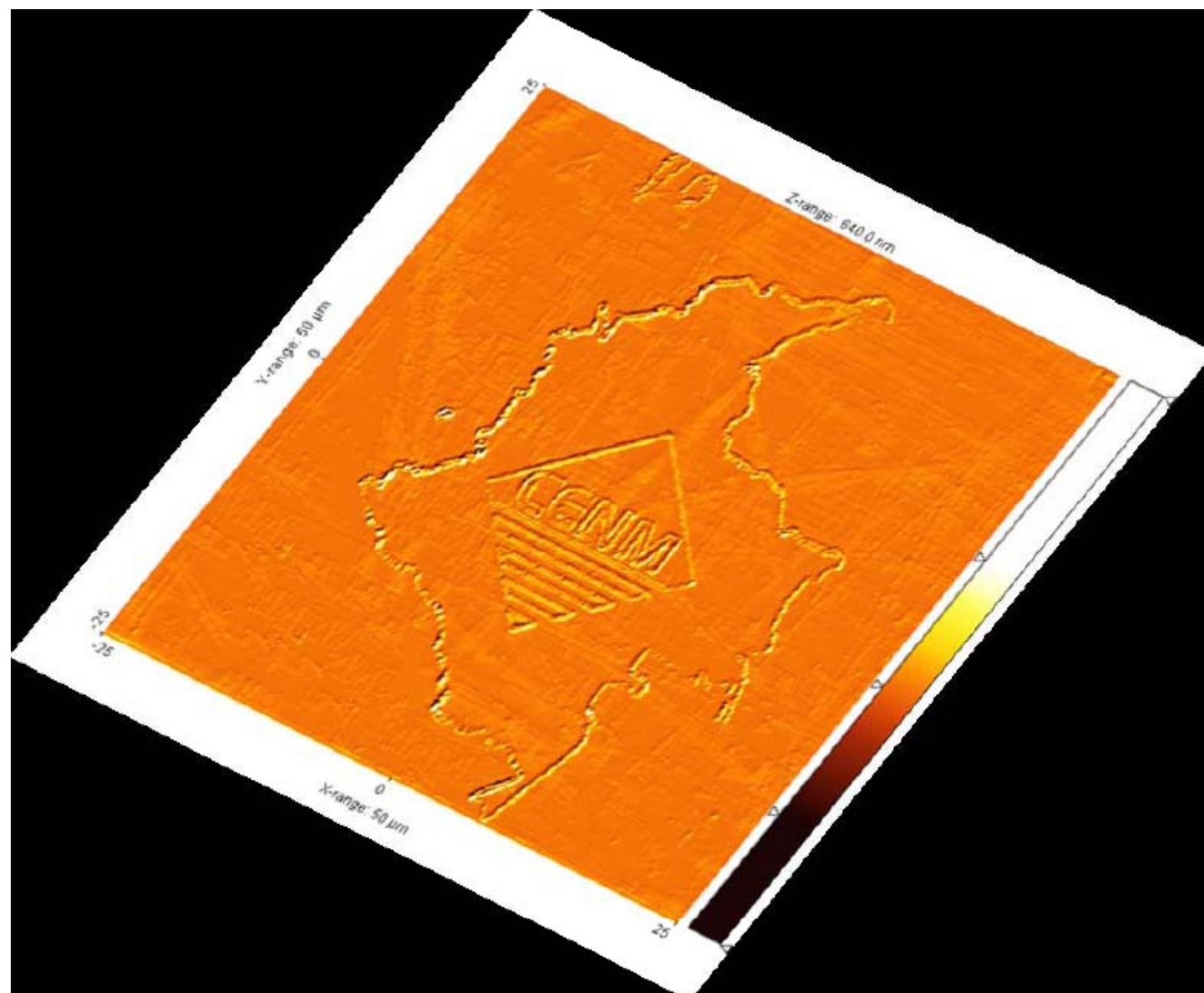
- ❑ High-tech robust equipment:
PPMS (Physical Property Measurement System)

AFM Atomic Force microscope

Microraman

Spectrophotometers

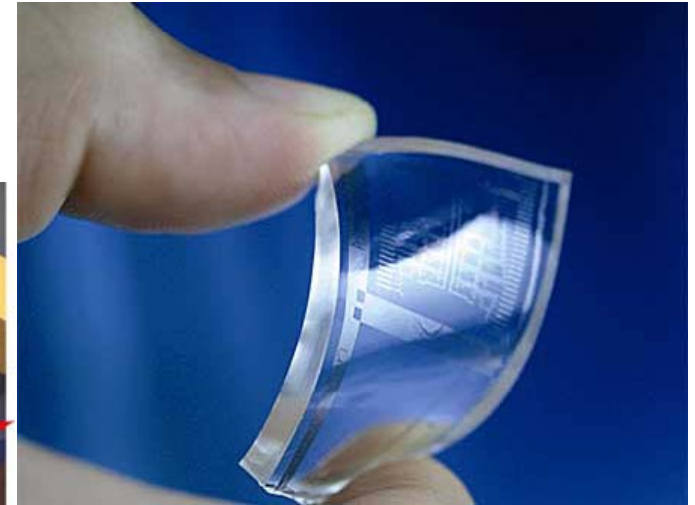
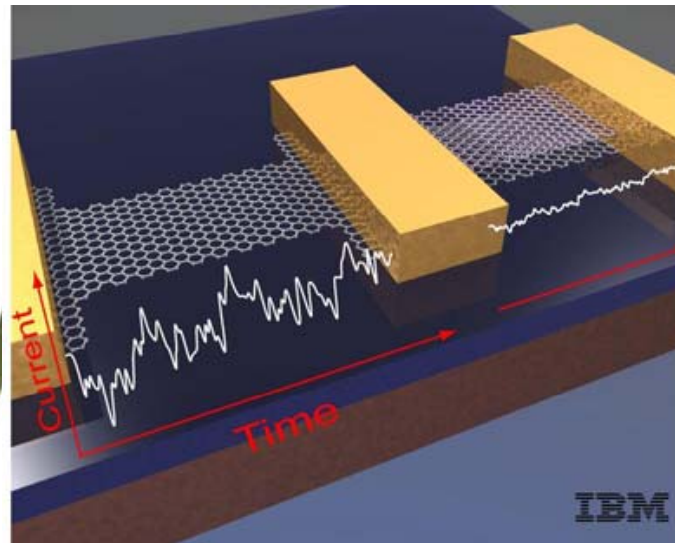
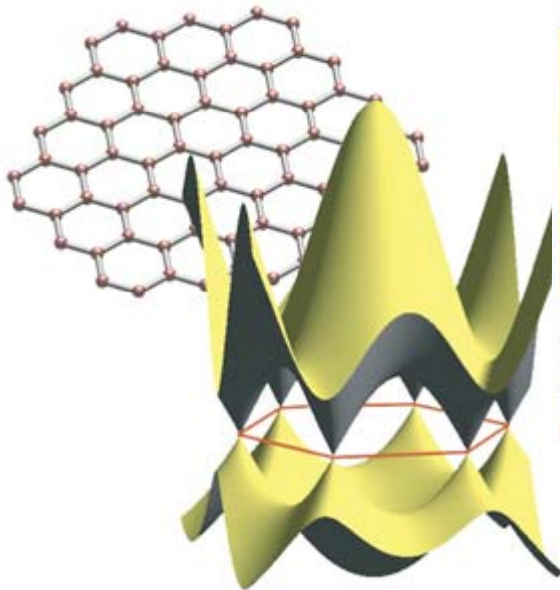
SEM Scanning Electron Microscope





The 2010 Nobel Prize for physics was awarded Professor Andrei Geim (left) and Professor Konstantin Novoselov for their work with graphene at Manchester University.

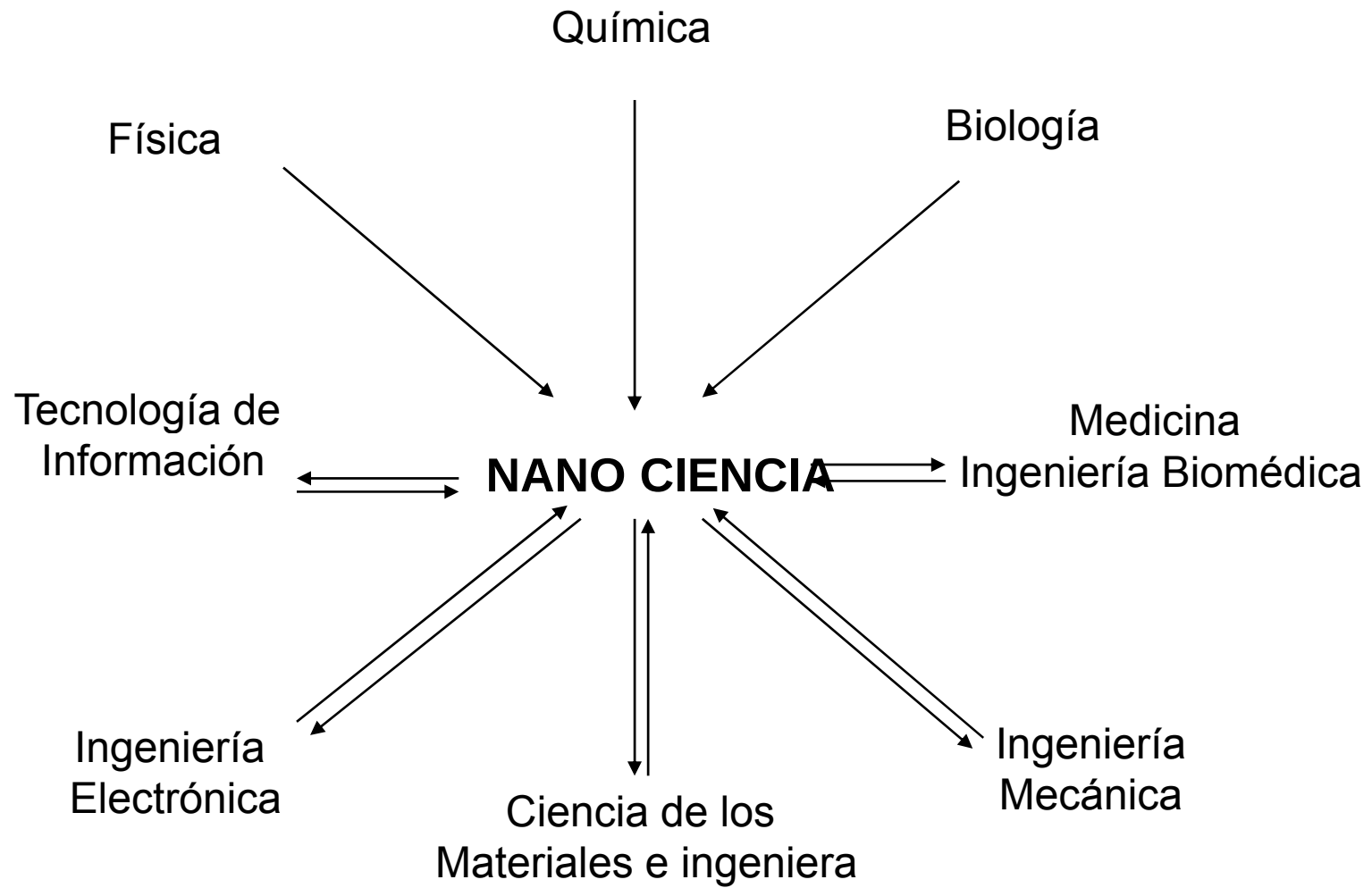
A nano-material called GRAPHENE



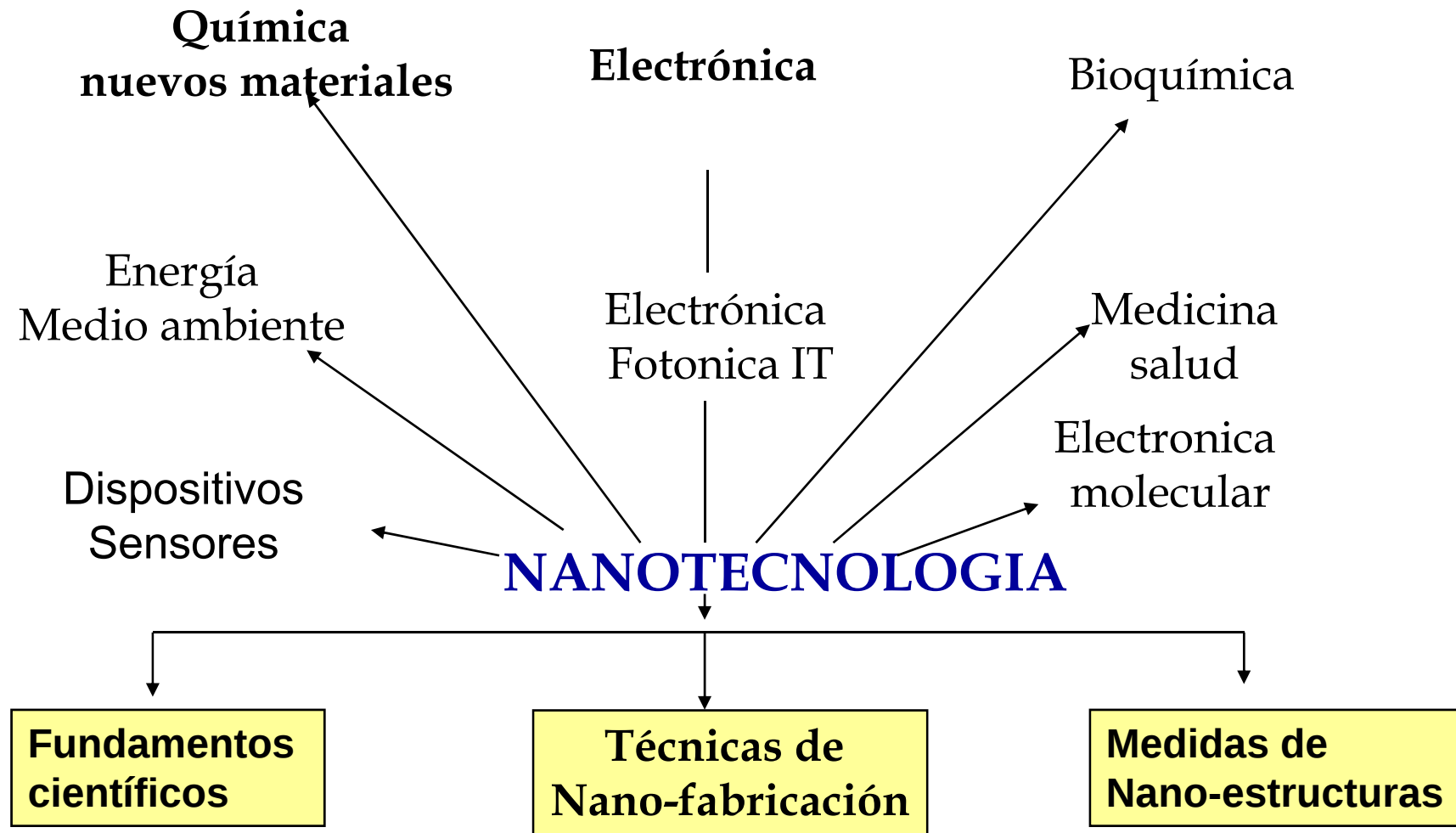
Contenido

- ✓ Conceptos básicos y aplicaciones en Nanociencia y Nanotecnología
- ✓ La mecánica cuántica y la naturaleza a la nanoescala
- ✓ Propiedades de materiales nanoestructurados
- ✓ Técnicas Top-Down para preparación de nanoestructuras
- ✓ Métodos de fabricación Bottom-up
- ✓ Autoensamblaje de nanoestructuras

CIENCIA MULTIDISCIPLINARIA



AREAS DE INFLUENCIA DE LA NANOTECNOLOGIA



Antecedentes

“There's Plenty of Room at the Bottom”

Richard Feynman, December 29th 1959

Now, the name of this talk is “There is Plenty of Room at the Bottom” - not just “There is Room at the Bottom.” What I have demonstrated is that there is room - that you can decrease the size of things in a practical way. I now want to show that there is plenty of room. I will not now discuss how we are going to do it, but only what is possible in principle - in other words, what is possible according to the laws of physics. I am not inventing anti-gravity, which is possible someday only if the laws are not what we think. I am telling you what could be done if the laws are what we think; we are not doing it simply because we haven't yet gotten around to it.

Feynman propone que no hay límites teóricos para la miniaturización



Antecedentes

Durante 1856-7 Michael Faraday fue el primero en preparar oro coloidal mediante la reducción de cloruro de oro con fósforo para obtener una solución color “rubí”. Faraday mostró mediante ensayos químicos que el oro ya no permanecía en forma iónica y que los reactantes que disolvían el metal eran capaces de eliminar el color.

Su conclusión fue que el oro era dispersado en el líquido de forma finamente dividida, y su presencia podía ser detectada mediante la opalescencia azulada cuando un intenso y estrecho haz de luz atravesaba el líquido.



Opalescencia en el líquido con NP de Au Faraday, 1856

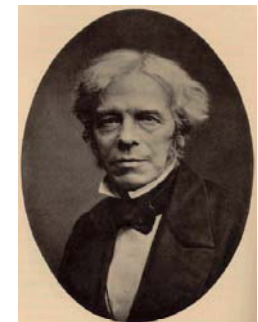


Opalescencia en el atardecer de Emberger Alm, Austria



Cuadro de una clase de Faraday, tomado de las ilustraciones de London News en 1856.

M. Faraday, 'The Bakerian lecture: experimental relations of gold (and other metals) to light', *Philosophical Transactions of the Royal Society of London*, Vol. 147 (1847) 145-181 n 159



Michael Faraday
1791-1867

Antecedentes

Cronología:

1959: R.P. Feynmann: "There's Plenty of Room at the Bottom"

1974: N. Taniguchi: "Nanotechnology" ($d = 100 \text{ nm}$)

1981: Binnig y Rohrer: Microscopio de efecto túnel.

1986: H.W.Kroto, J.R.Heath, S.C. O'Brien, R.F.Curl, R.E. Smalley: estructura de los fullerenos.

1986: Quate and Gerber: Microscopio de Fuerza Atómica (AFM).

1989: IBM: Litografía atómica

1991: S. Iijima: nanotubos de carbono

1996: G. Whitesides: electrónica molecular

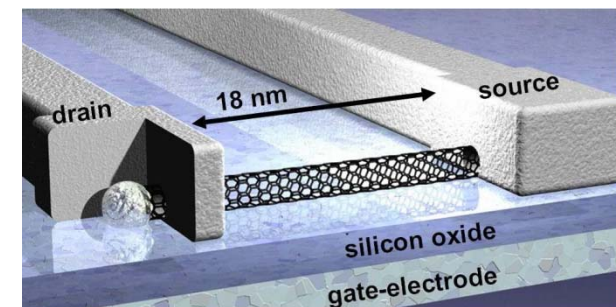
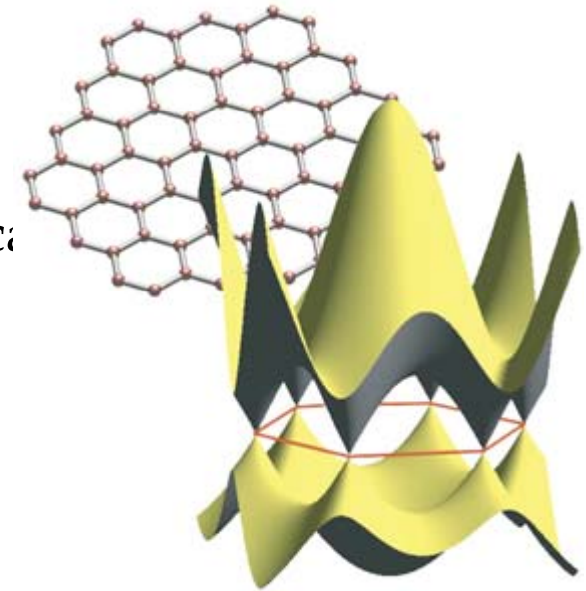
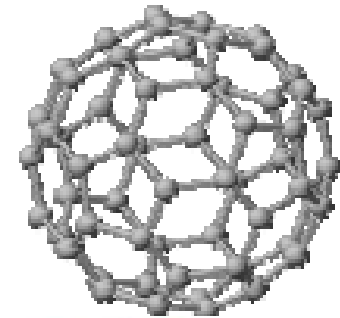
1998: C. Dekker: nano-transistor

1999: J. Tour y M. Reed: interruptor molecular

2000: D. Eigler (IBM): corral cuántico

2007 P Grumberg A. Fert GMR Sensor

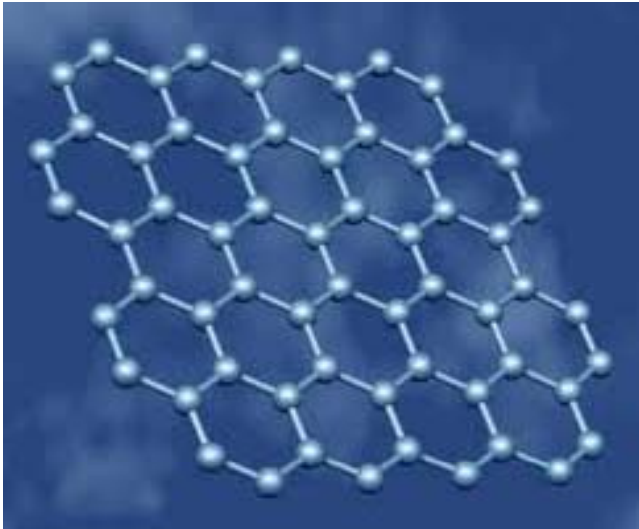
2010 A. Geim Professor K. Novoselov Grafeno



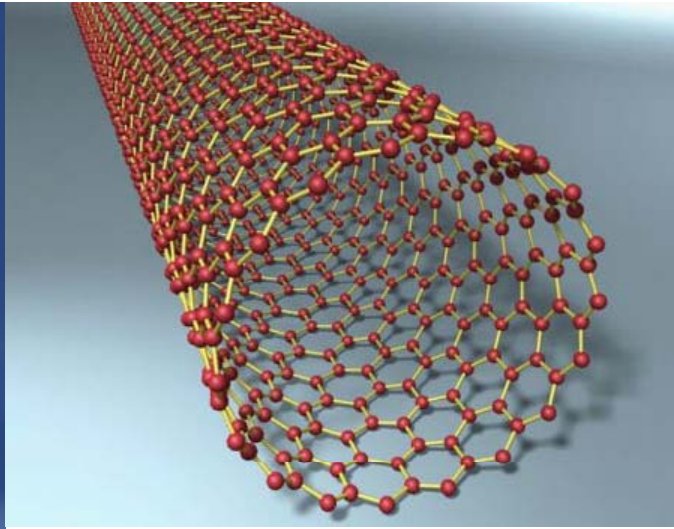
Que es Nanociencia?

Cuando se comienza a hablar de Nanociencia se empiezan a describir cosas

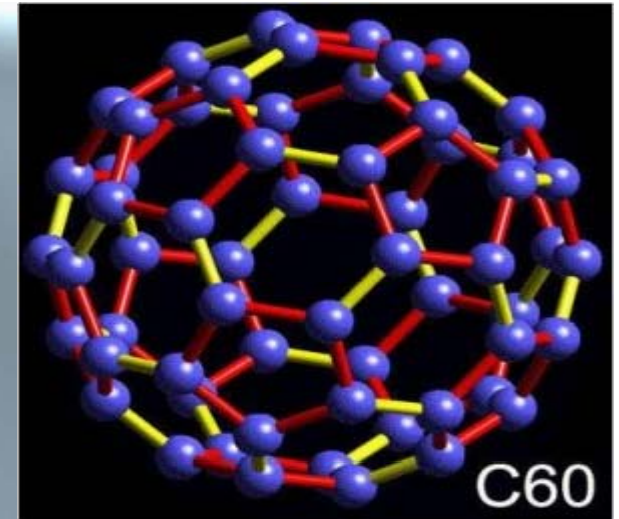
Los Físicos y los ingenieros en materiales apuntan a cosas tales como los nanomateriales basados en carbón



Graphene



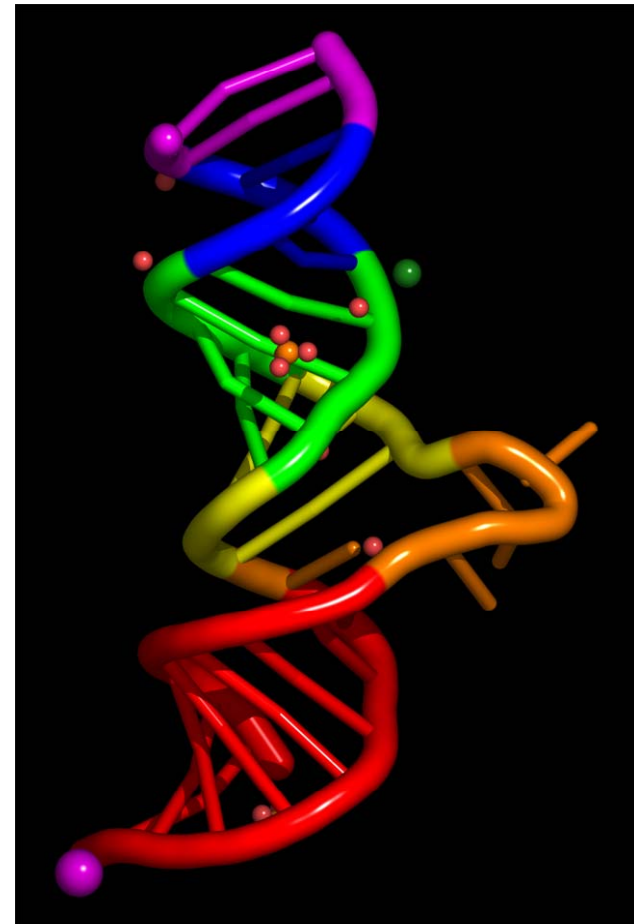
Carbon Nanotube



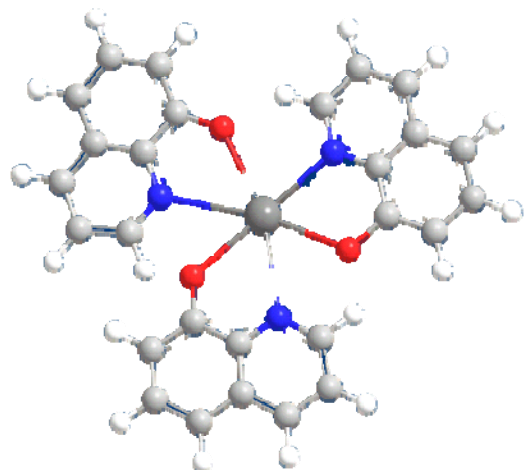
C60 Buckminster Fullerene

Los Biólogos responden que el nano-carbón es un descubrimiento reciente

Ellos han estado estudiando el DNA y el RNA por mucho mas tiempo

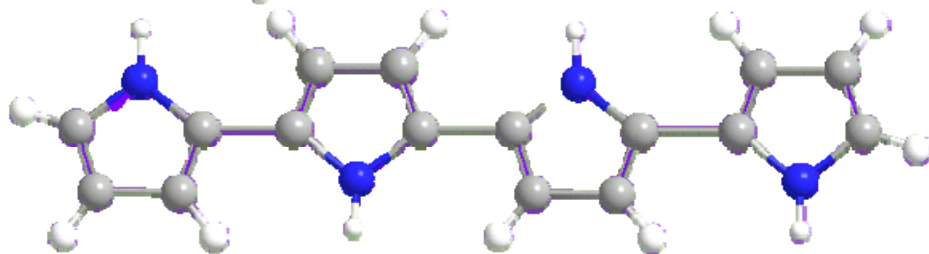


Los Químicos responden Hemos estado sintetizando moléculas por siglos!!!

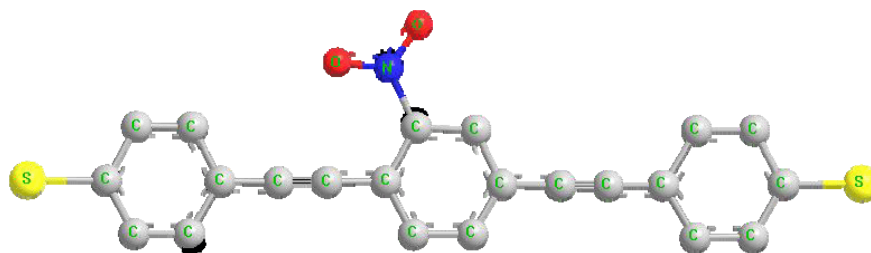


Primer Material para OLED:
tris 8-hydroxyquinoline aluminum

(OLED = Organic Light Emitting Diode)



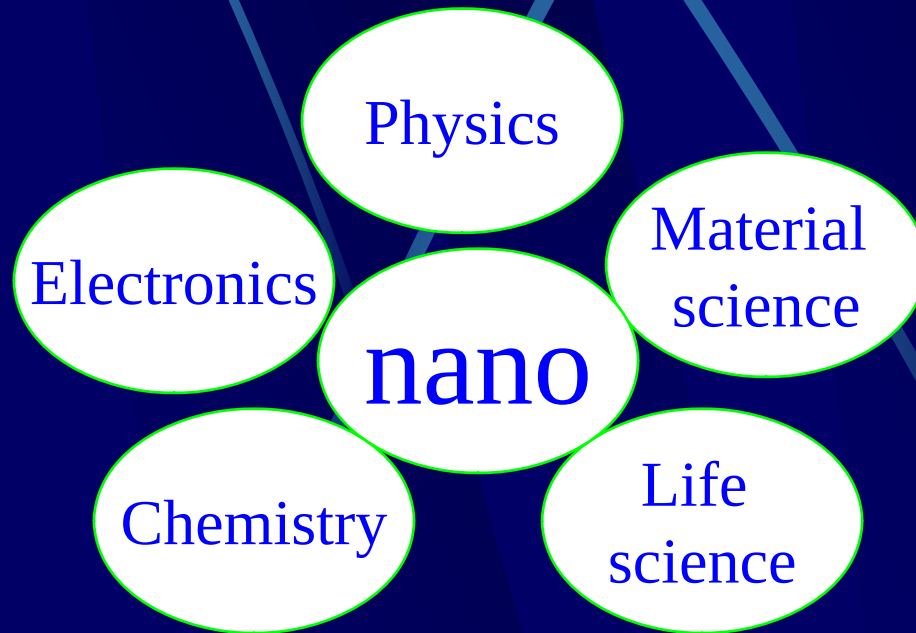
Material para OLED Comerciales:
Polypyrrole



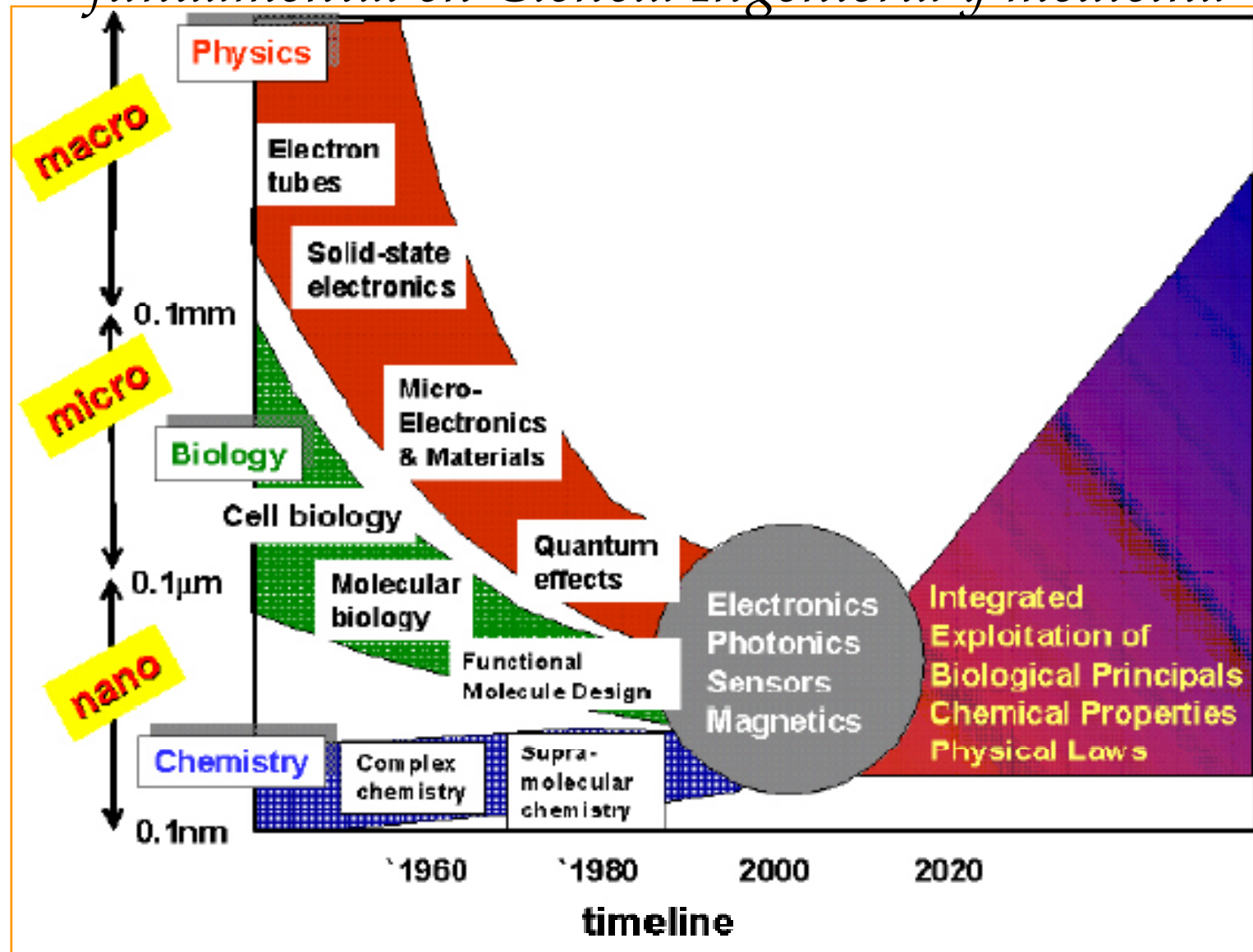
El Material más ampliamente investigado
para interruptores en electrónica
molecular :

Nitro oligo phenylene ethynylene

Nanotechnology is multi-disciplinary

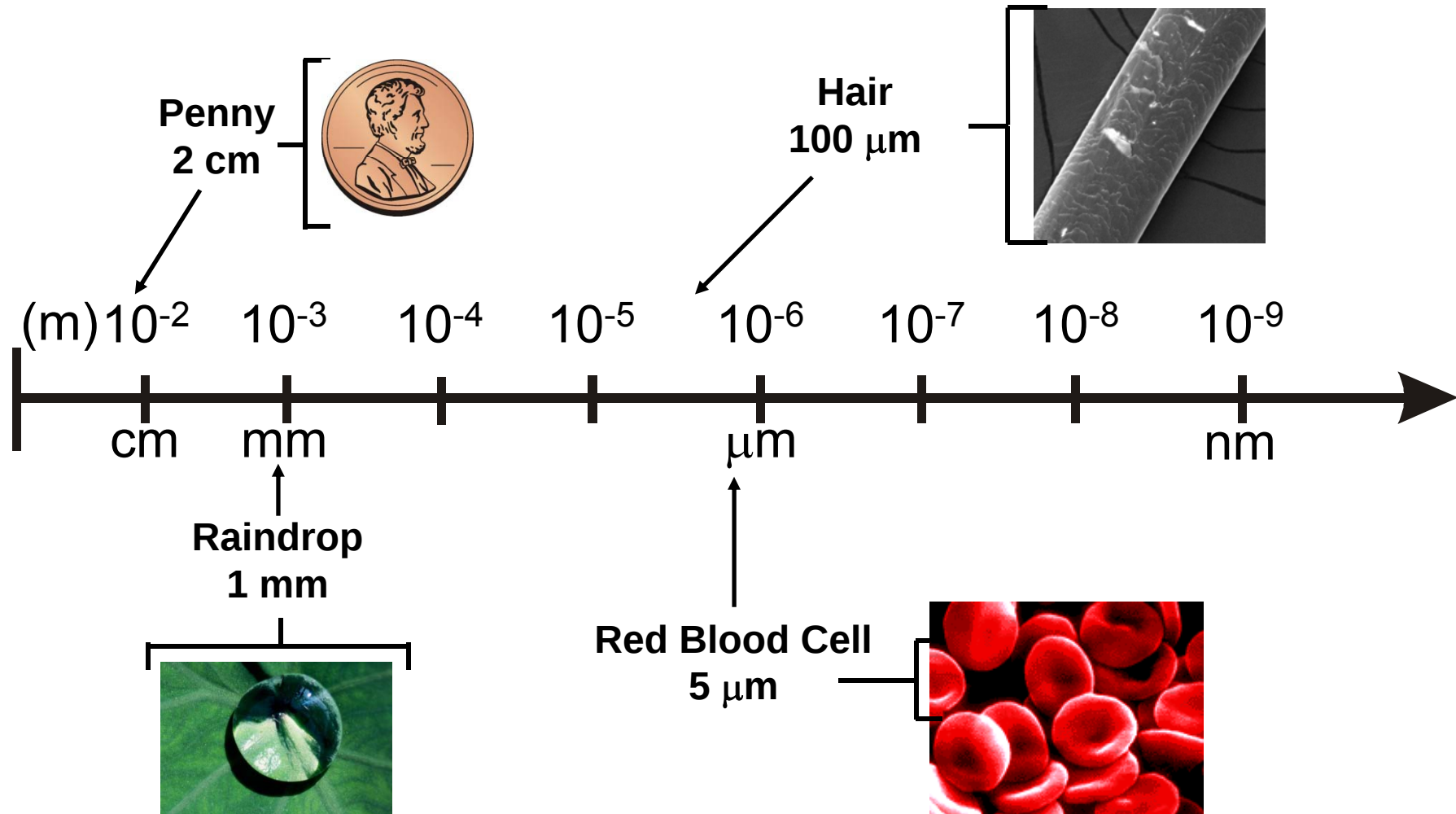


El Nanómetro como escala de longitud fundamental en Ciencia Ingeniería y medicina

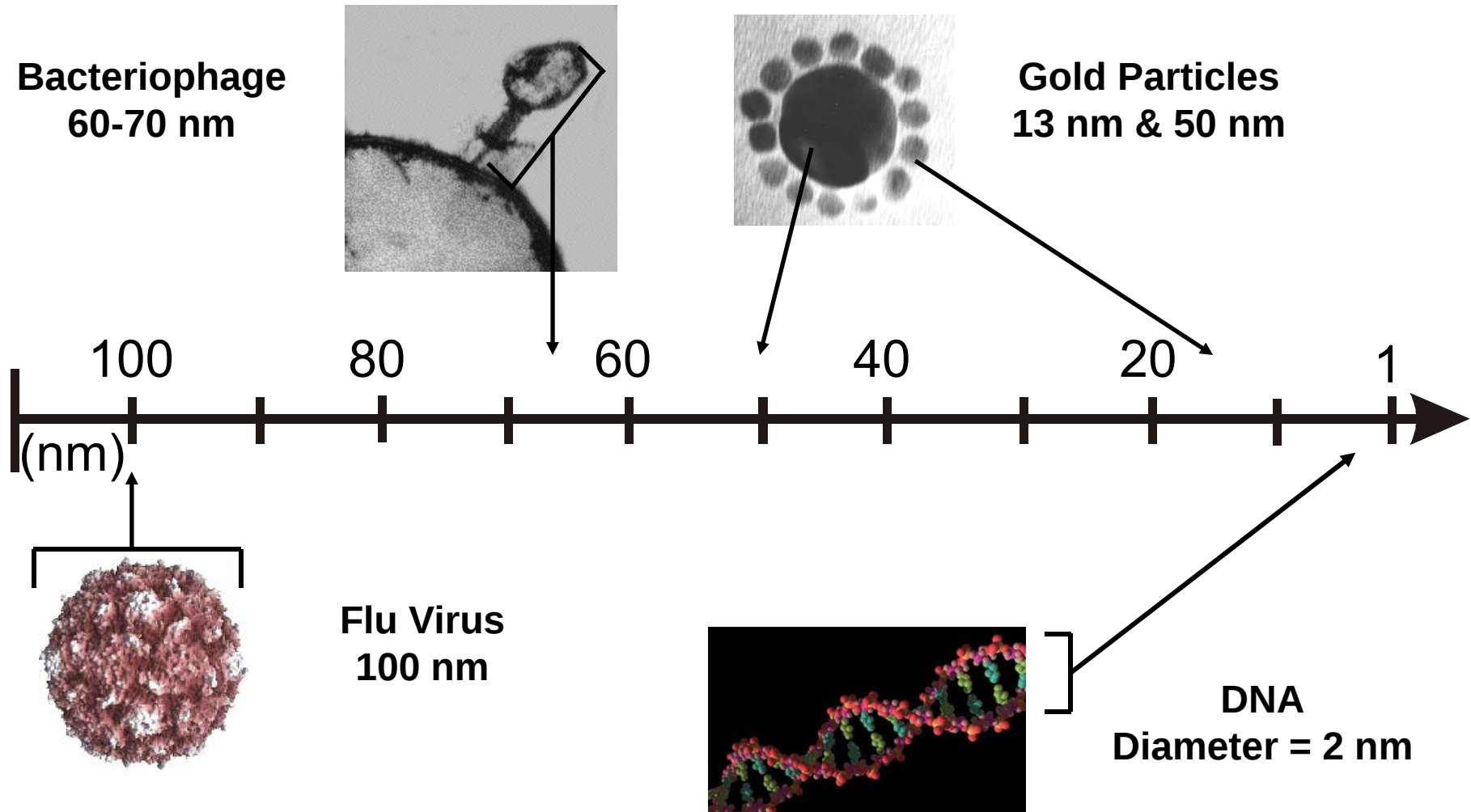


Adapted from the Asia-Pacific Economic Cooperation on Nanotechnology (<http://www.apectf.nstda.or.th/html/nano.html>).

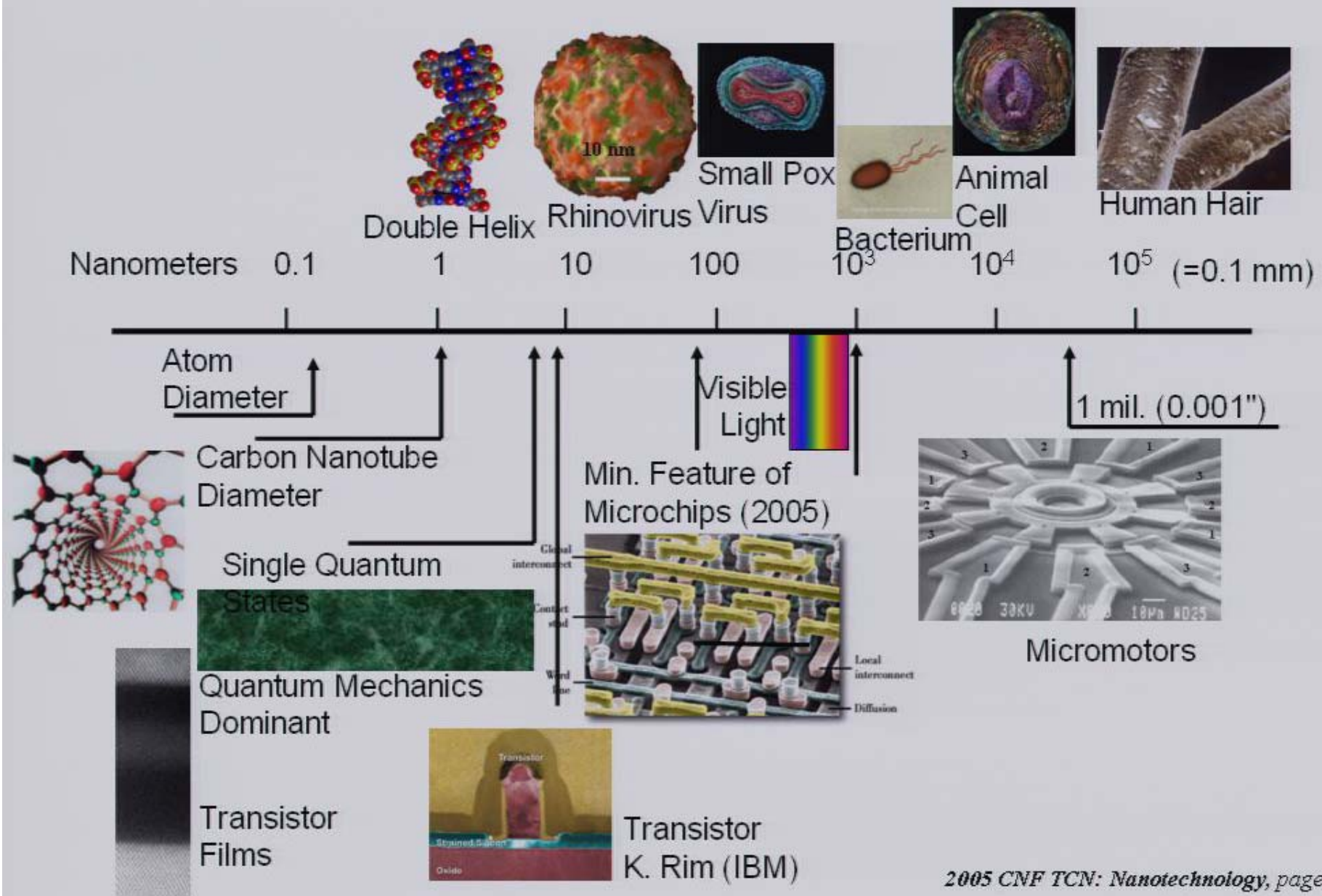
What Is A Nanometer?



Now Entering The NANO-ZONE



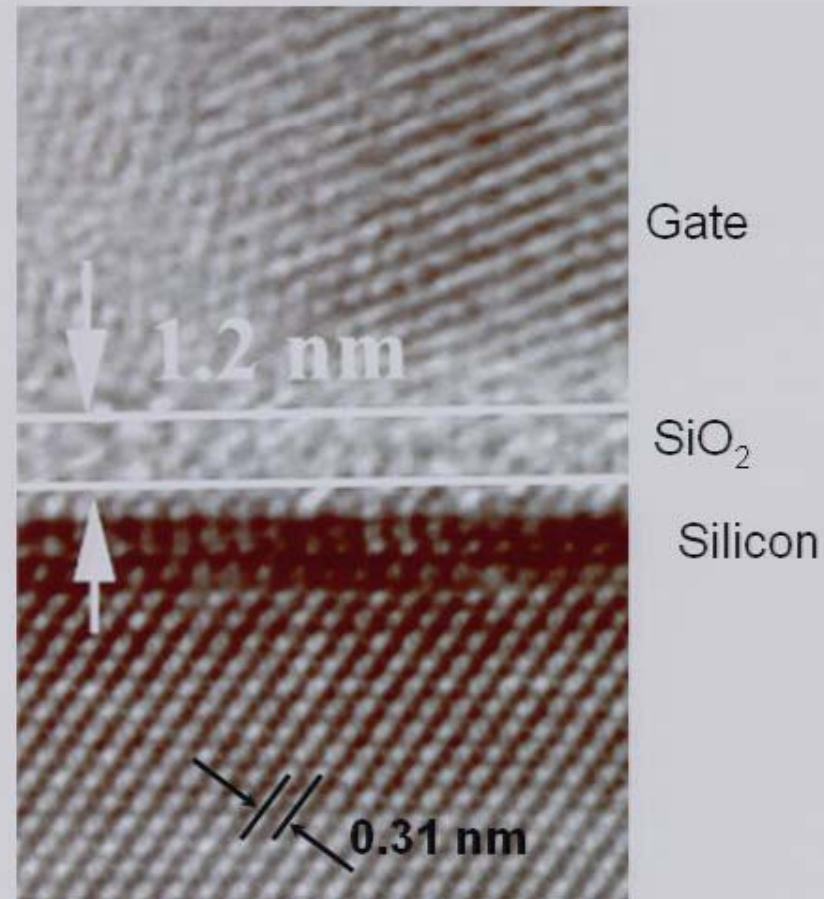
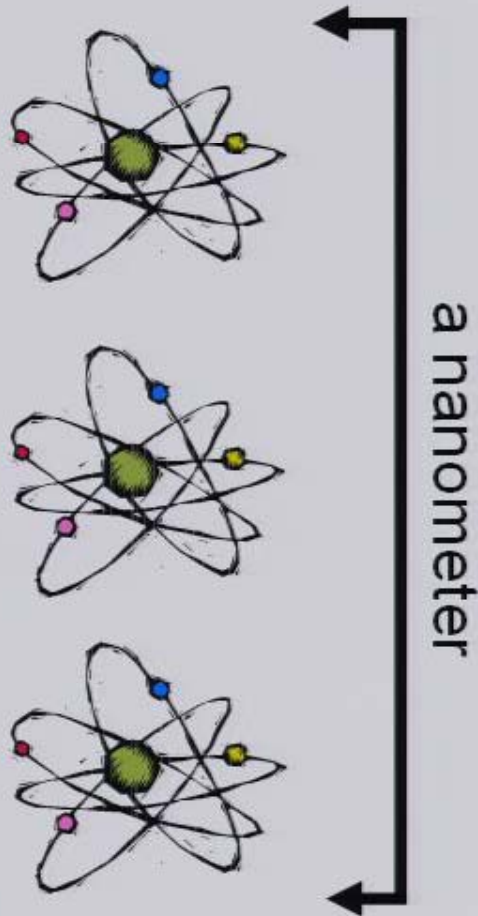
Nanostructure Size Scales



QUE ES NANO?: EL CONCEPTO DE LONGITUD

SI unit (abbreviation)	Description
meter (m)	About three feet
centimeter (cm)	1/100 of a meter
milimeter (mm)	1/1000 of a meter
micrometer (μm)	1/1,000,000 (10^{-6}) of a meter
nanometer (nm)	1/1,000,000,000 (10^{-9}) of a meter
Ångström (Å)	The smallest length unit (10^{-10} m), defined by Swedish physicist Anders Jonas Ångström (Aug. 13, 1814 - June 31, 1874)

What is a Nanometer?



- A nanometer is one-billionth of a meter. Tiwari, MNE (1999)
- A stack of *three* silicon atoms is a nanometer high. This is approximately the thickness of the inversion layer – the conducting electron region of a transistor.

Nanociencia

“Today, at the beginning of the 21st century, research in the life sciences, the information technologies, and the materials sciences converges upon a commonality: the domain of the nanometer, and the manipulation of atoms and molecules. Continued technological progress becomes dependent upon achieving control of materials at the nano scale”

“Nanotechnology can not be defined in terms of dimension or geometry alone. In fact, it represents a convergence of the traditional disciplines of physics, chemistry and biology at a common research frontier”

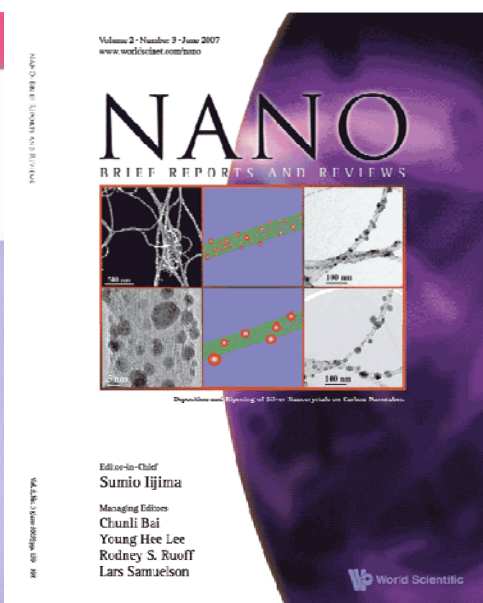
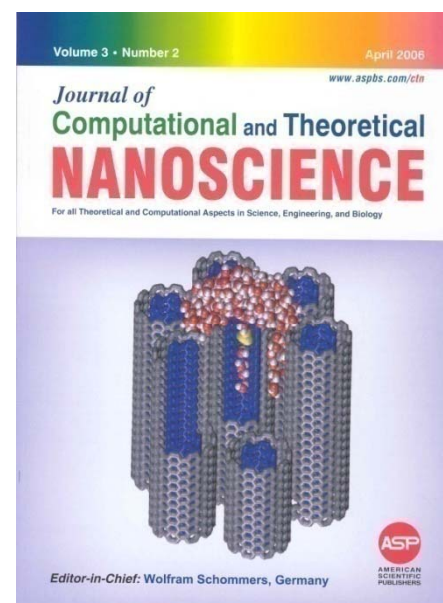
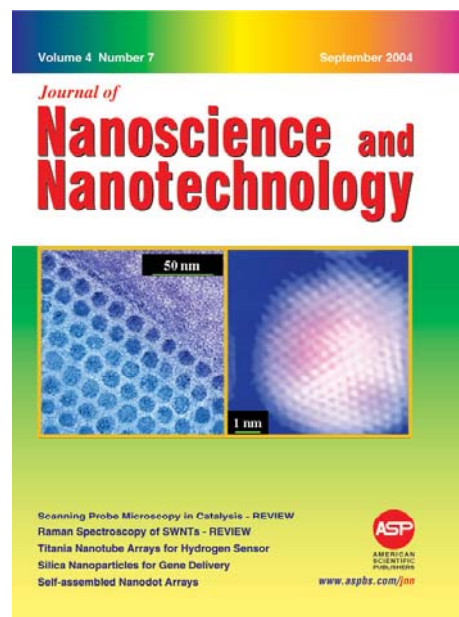
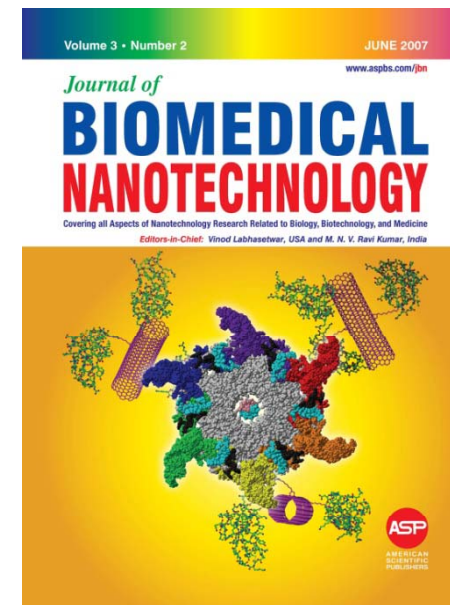
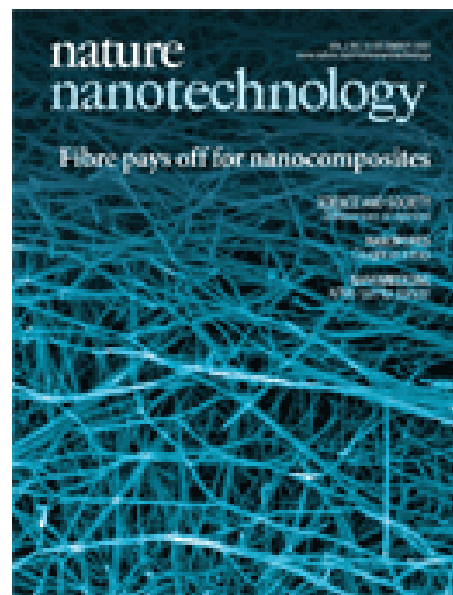
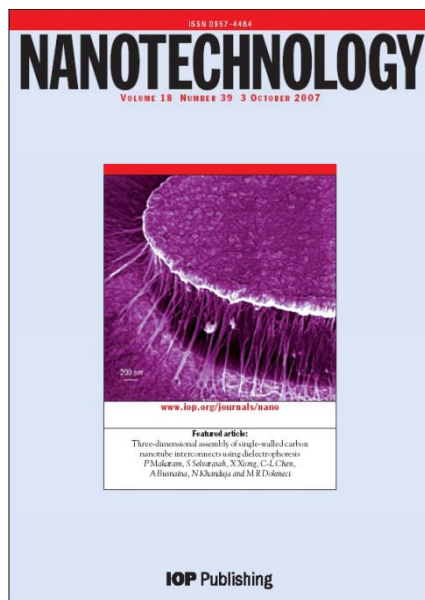
*EC Commissioner Busquin
Proceedings EC/NSF workshop Toulouse,
Oct. 2001. Office for Official Publications,
ISBN 92-894-0793-X*

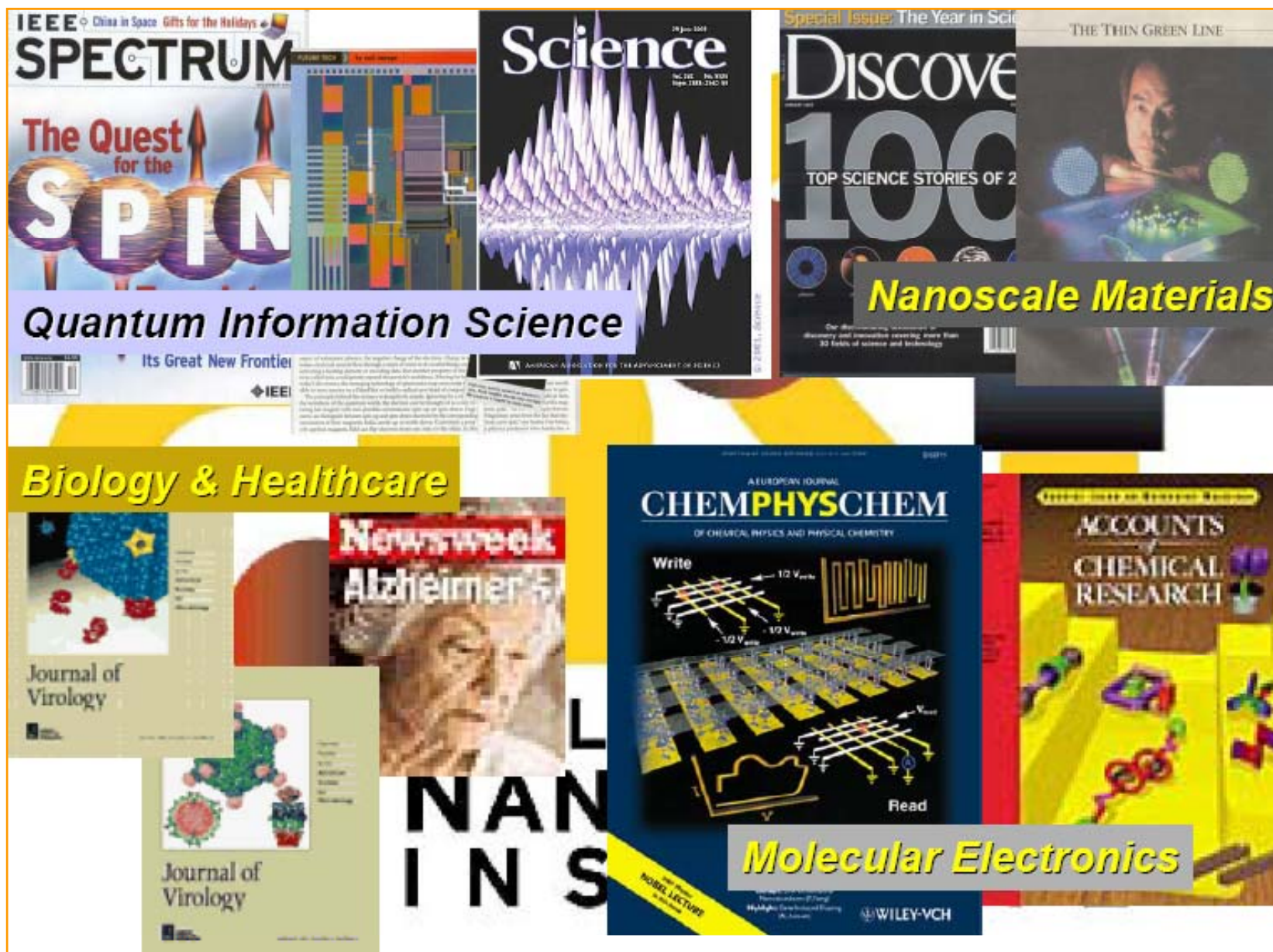
Que es la nanotecnología?

La Nanotecnología es la creación de Materiales Funcionales, Dispositivos y Sistemas a través del control de la materia a escalas de longitud de los nanómetros y la explicación de nuevos fenómenos y propiedades de los materiales (Físicas, Químicas y Biológicas) a estas escalas de longitud.

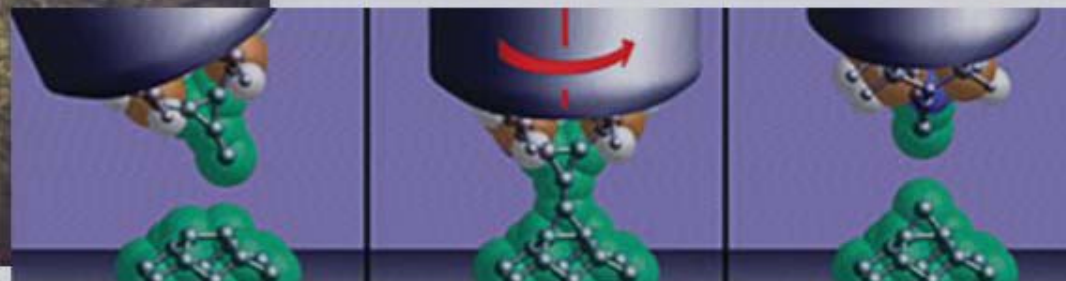
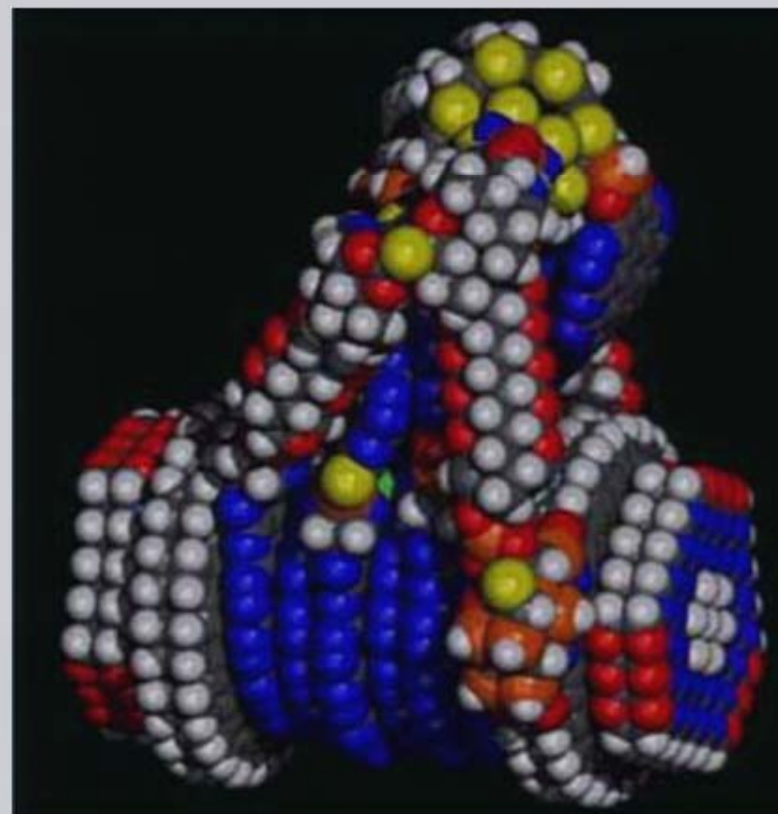
“If I were asked for an area of science and engineering that will most likely produce the breakthroughs of tomorrow, I would point to nanoscale science and engineering.”

-Neal Lane Assistant to the President for S & T





Fantasy (?)



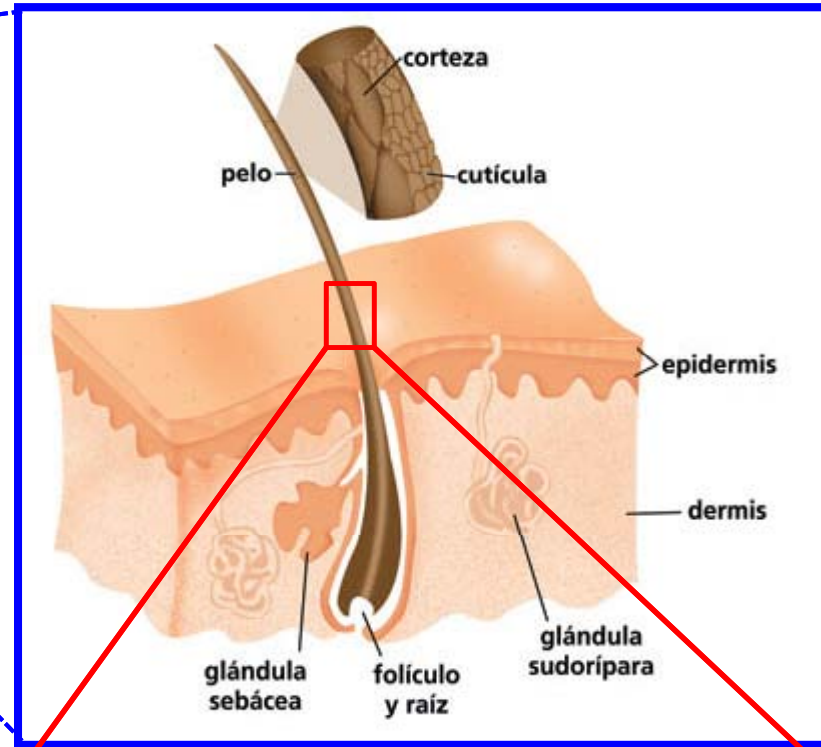
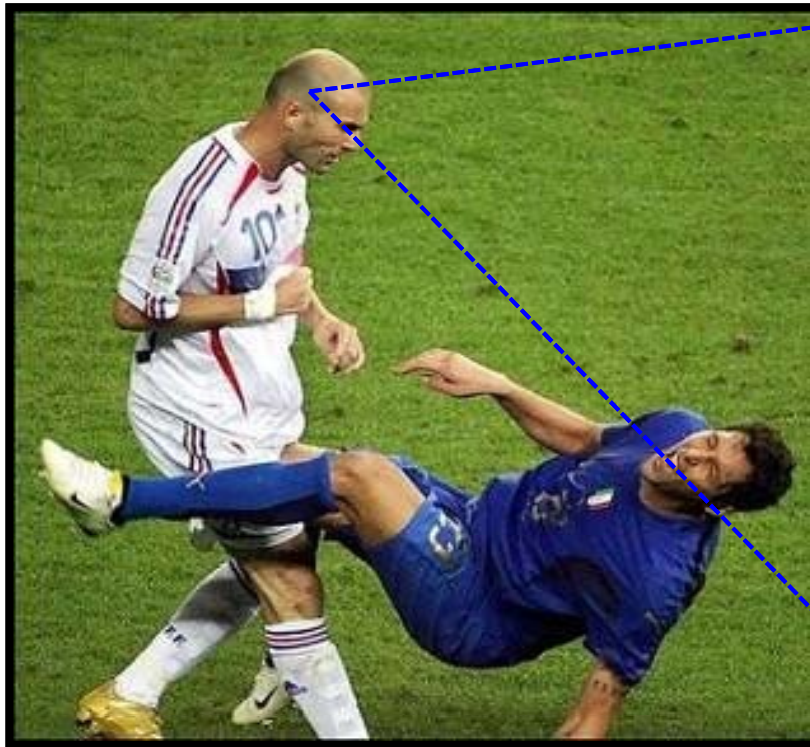
La escala de las cosas

Ciencia y tecnología en la escala de los nanómetros (<100 nm).

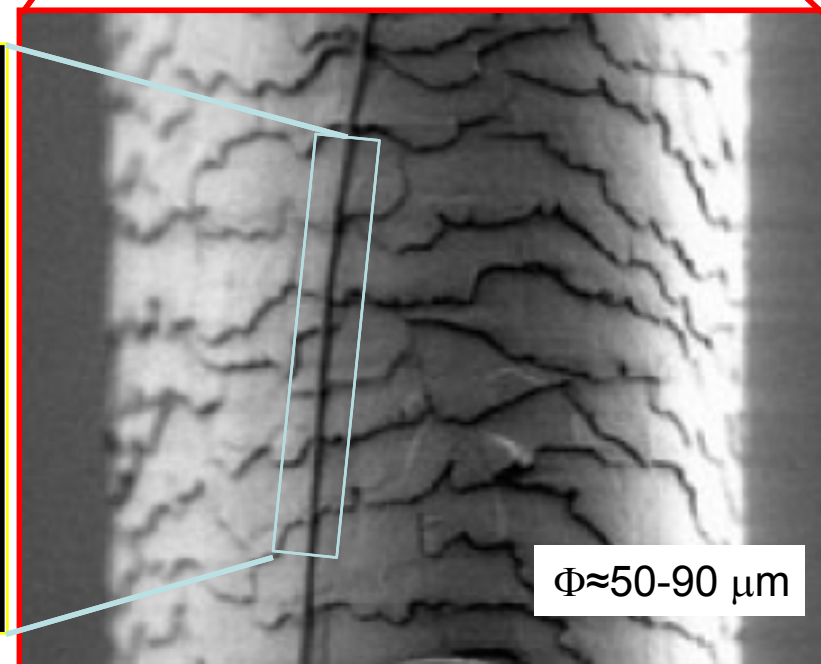
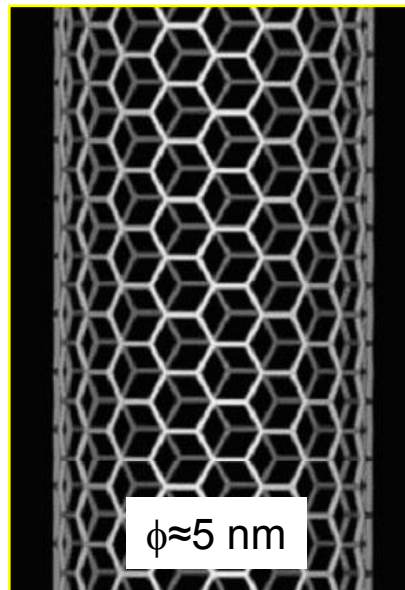
1 metro = 1000'000.000 nm = 10^9 nm



Cortesía J Restrepo UdeA

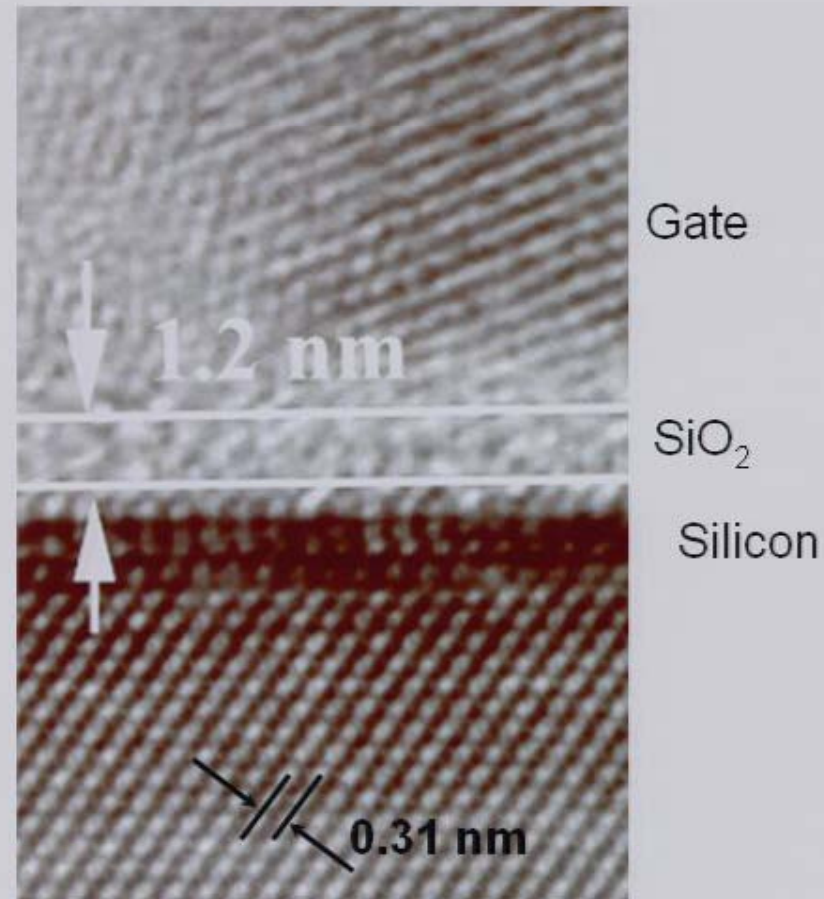
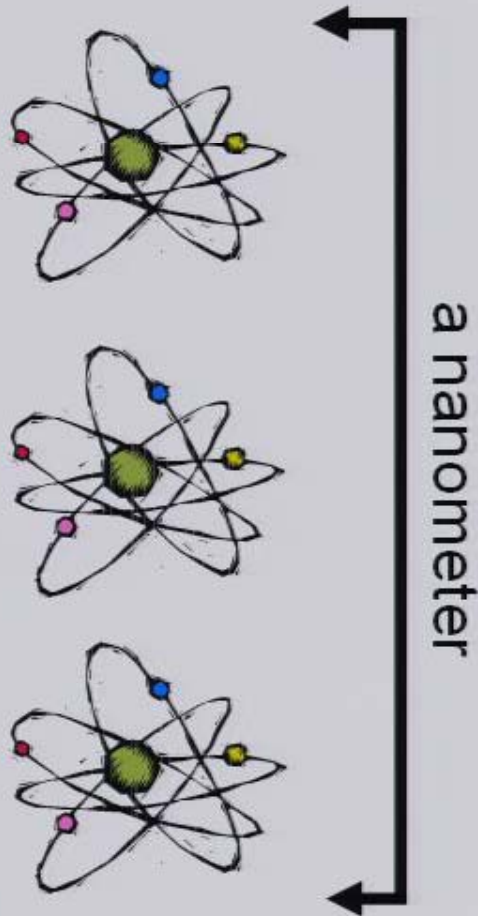


Sustancias opacas pasan a ser transparentes (el cobre); materiales inertes pasan a ser catalizadores (el platino); materiales estables se tornan combustibles (el aluminio); algunos sólidos se vuelven líquidos a temperatura ambiente (el oro); y algunos materiales aislantes llegan a ser conductores (el silicio).

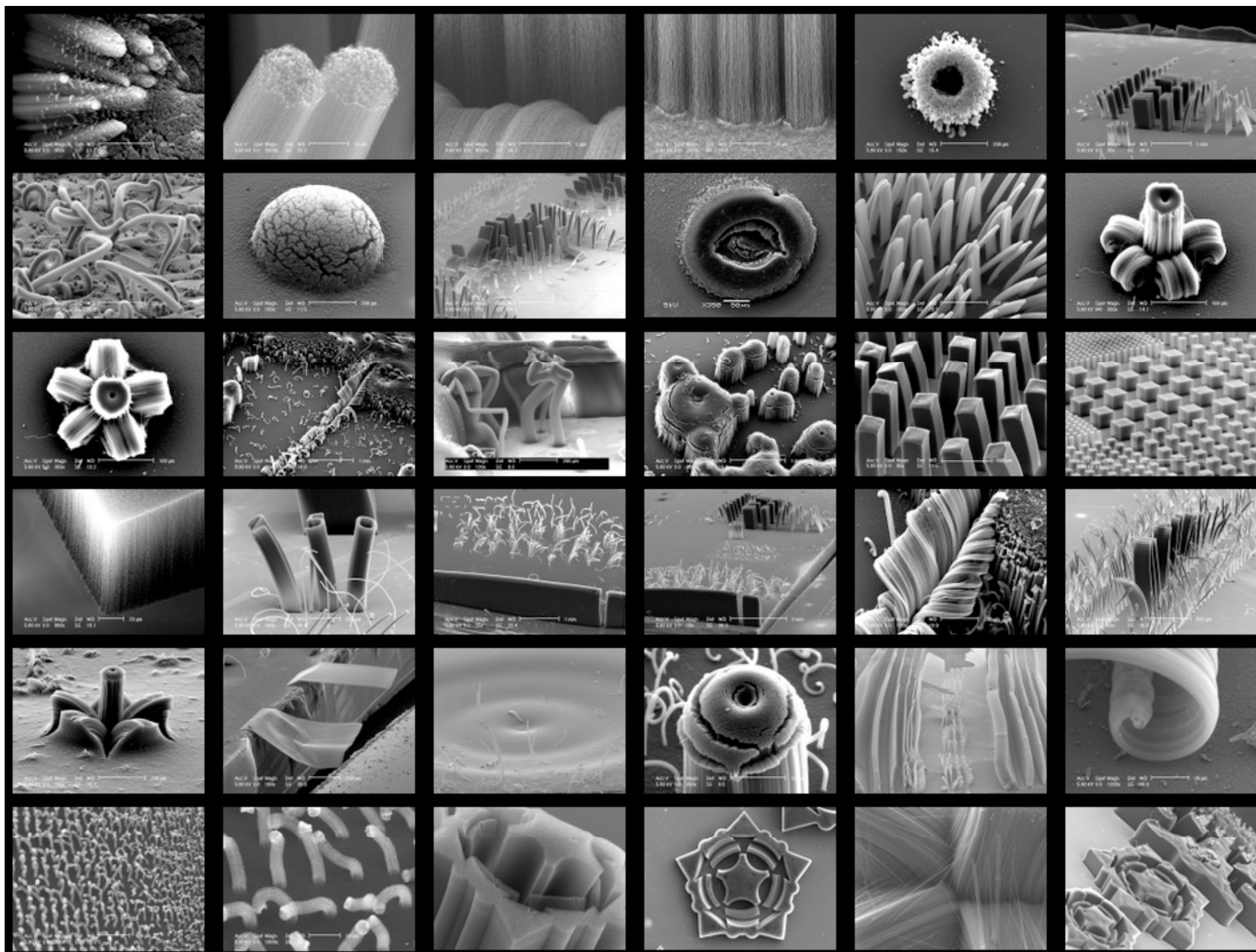


Cortesía J Restrepo UdeA

What is a Nanometer?



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- A stack of *three* silicon atoms is a nanometer high. This is approximately the thickness of the inversion layer – the conducting electron region of a transistor.





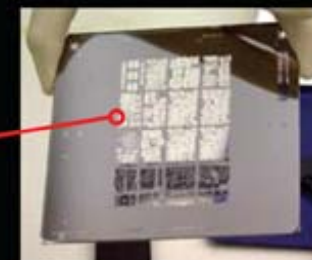
- (1) Se convierte la imagen a una de líneas.
- (2) Se encoje y se imprime sobre un substrato de vidrio (máscara) usando un sistema láser.
- (3) Se ilumina con luz ultravioleta a través de la máscara una película delgada de polímero sobre un wafer de Si (Fotolitografía).
- (4) Se recubre el wafer con una película delgada de nanopartículas catalíticas que funcionan como semillas para el crecimiento de los nanotubos.
- (5) Se remueve el polímero remanente y quedan las semillas en las formas de los nanobamas.
- (6) Se crecen los CNTs colocando el wafer en un horno a alta temperatura y llenándolo con un gas rico en carbono.
- (7) Se toman las fotografías de las estructuras mediante microscopía electrónica SEM.



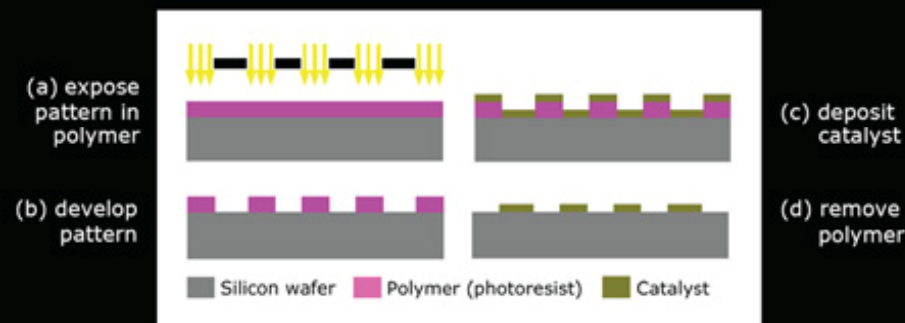
(0) image



(1) line drawing



(2) mask



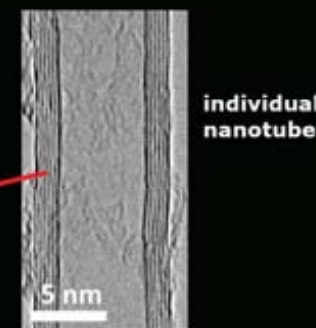
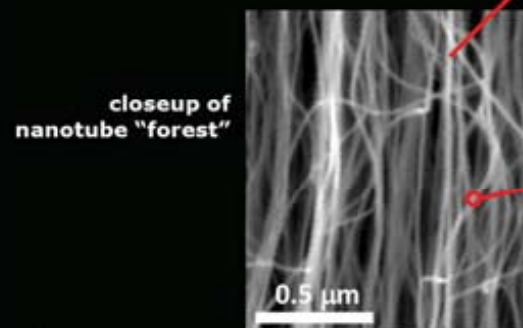
(3,4,5) photolithography and catalyst patterning



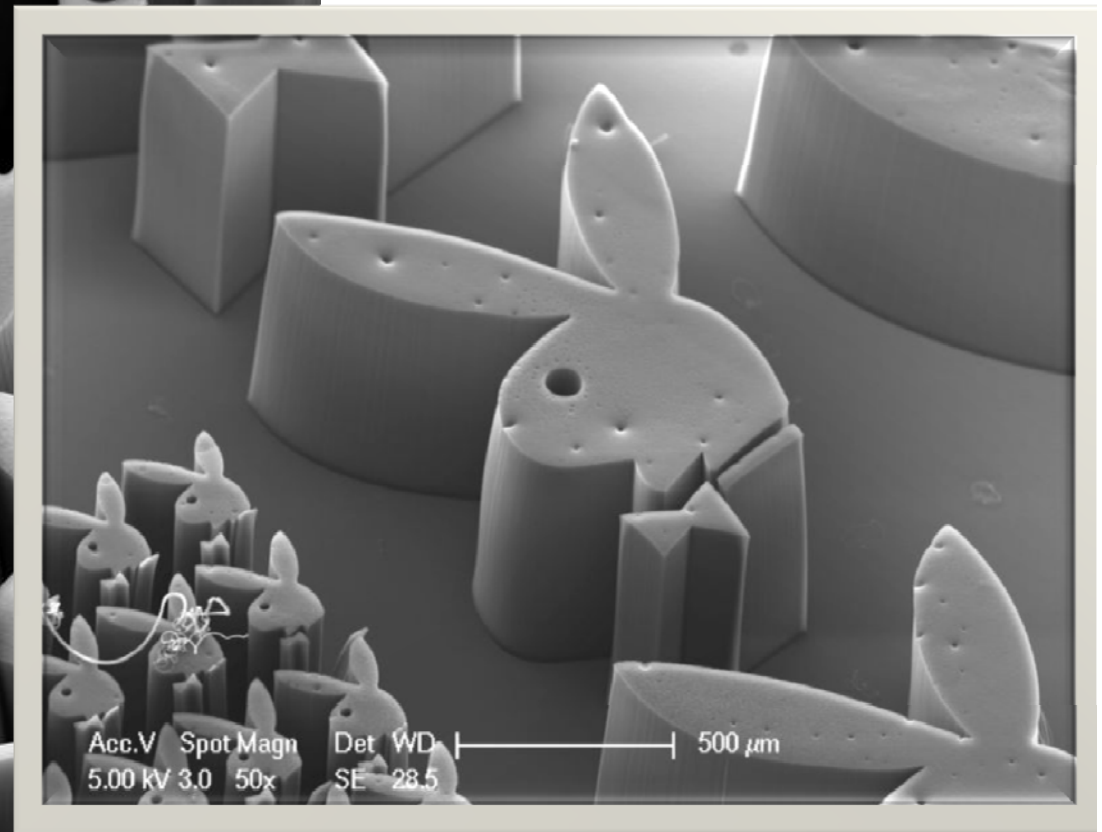
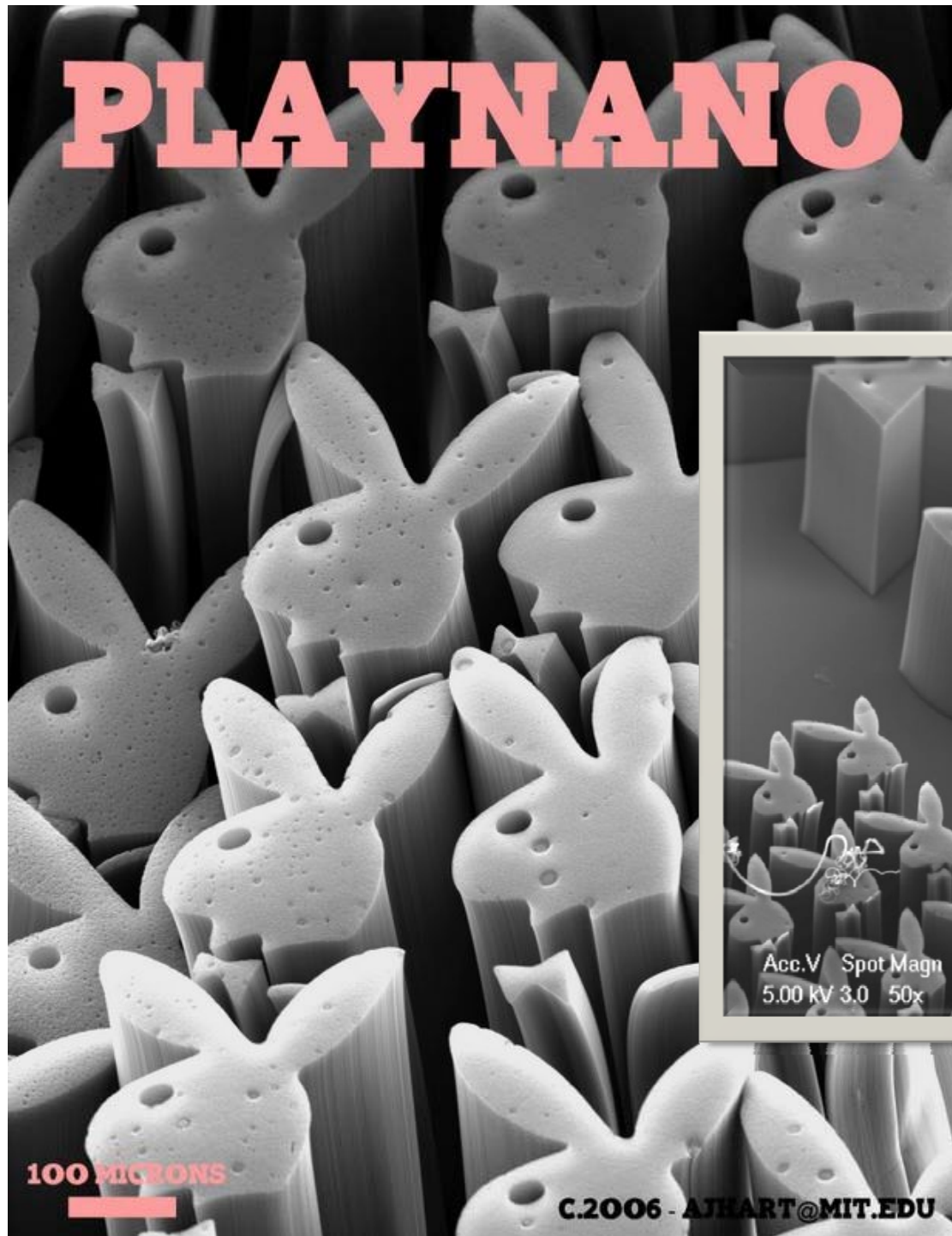
(6) grow nanotubes



(7) take pictures



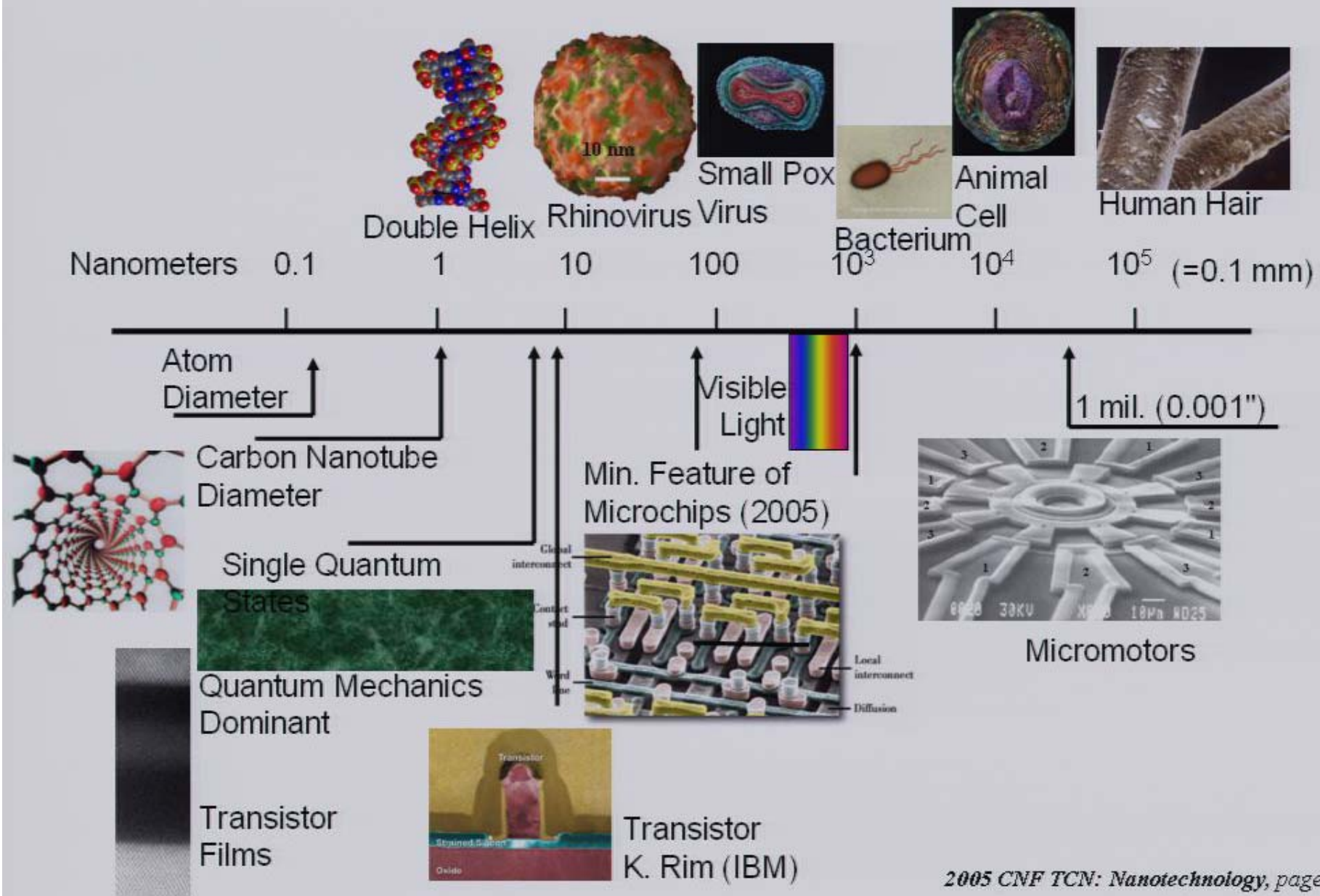
PLAYNANO



100 MICRONS

C.2006 - AJHART@MIT.EDU

Nanostructure Size Scales



The Scale of Things – Nanometers and More



Things Natural

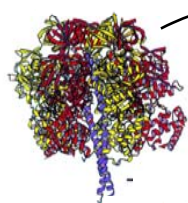
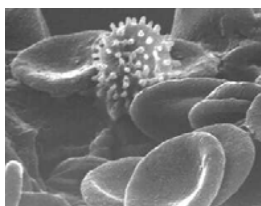


Dust mite
200 μm

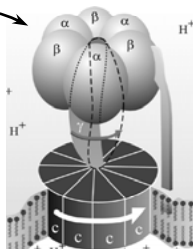


Human hair
~ 60-120 μm wide

Red blood cells
with white cell
~ 2-5 μm



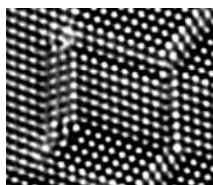
~10 nm diameter



ATP synthase



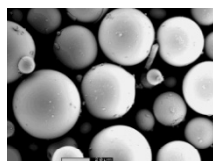
DNA
~2-1/2 nm diameter



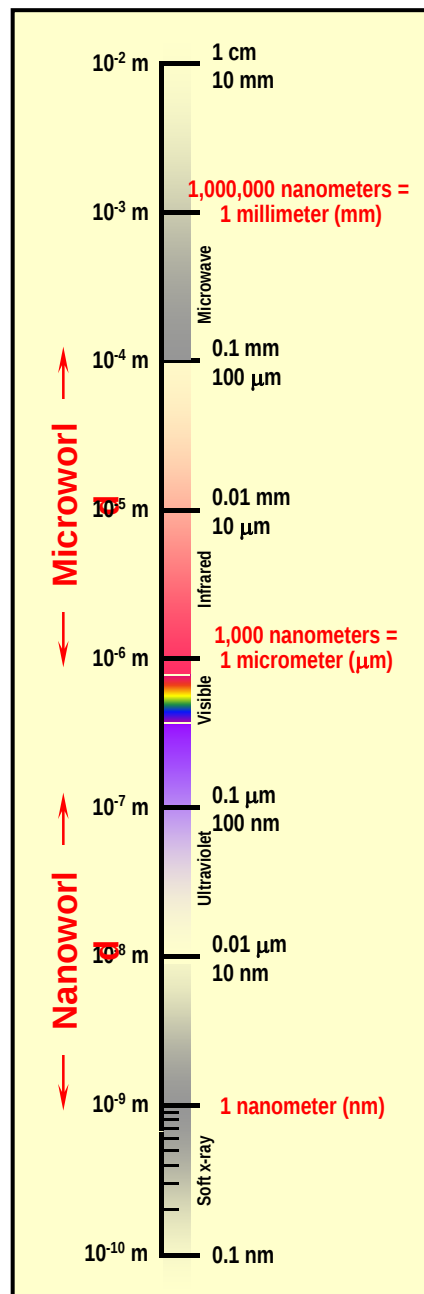
Atoms of silicon
spacing ~tenths of nm



Ant
~ 5 mm



Fly ash
~ 10-20 μm



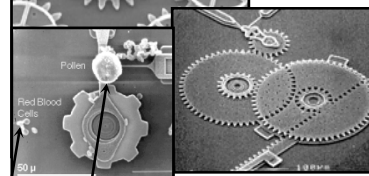
Things Manmade



Head of a pin
1-2 mm

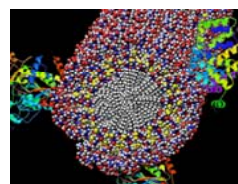


MicroElectroMechanical (MEMS) devices
10 -100 μm wide

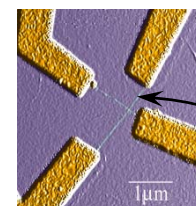


Pollen grain
Red blood cells

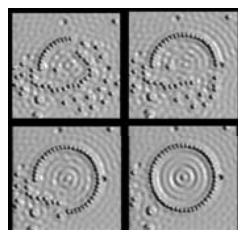
Zone plate x-ray "lens"
Outer ring spacing ~35 nm



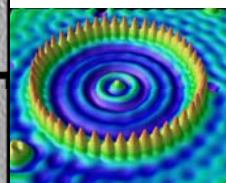
Self-assembled,
Nature-inspired structure
Many 10s of nm



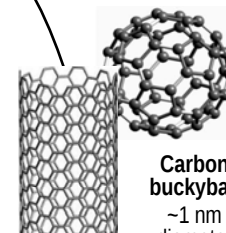
Nanotube electrode



Quantum corral of 48 iron atoms on copper surface
positioned one at a time with an STM tip
Corral diameter 14 nm

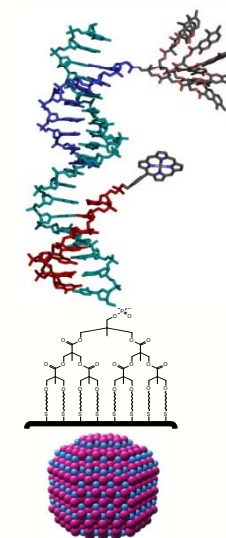


Carbon nanotube
~1.3 nm diameter



Carbon buckyball
~1 nm diameter

The Challenge



Fabricate and combine
nanoscale building
blocks to make useful
devices, e.g., a
photosynthetic reaction
center with integral
semiconductor storage.

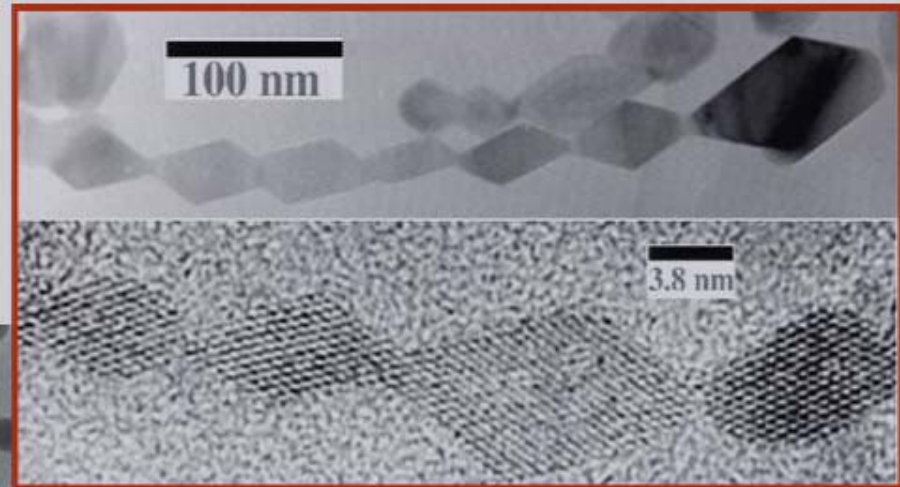
Is Nanotechnology Something New?

- Nanoscale components have been in use for thousands of years.
- Materials have been engineered at the nanoscale for many years.

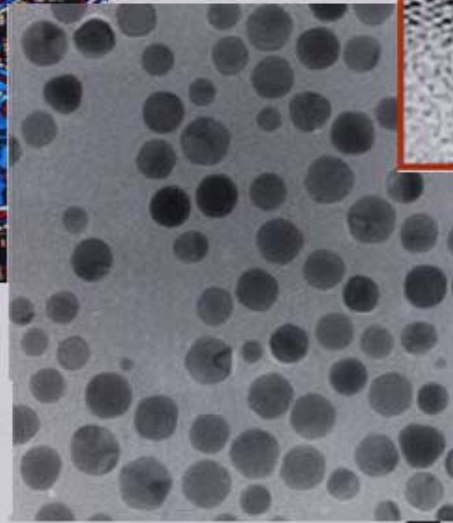


Stained Glass

Nanoscale gold particles in glass give red color

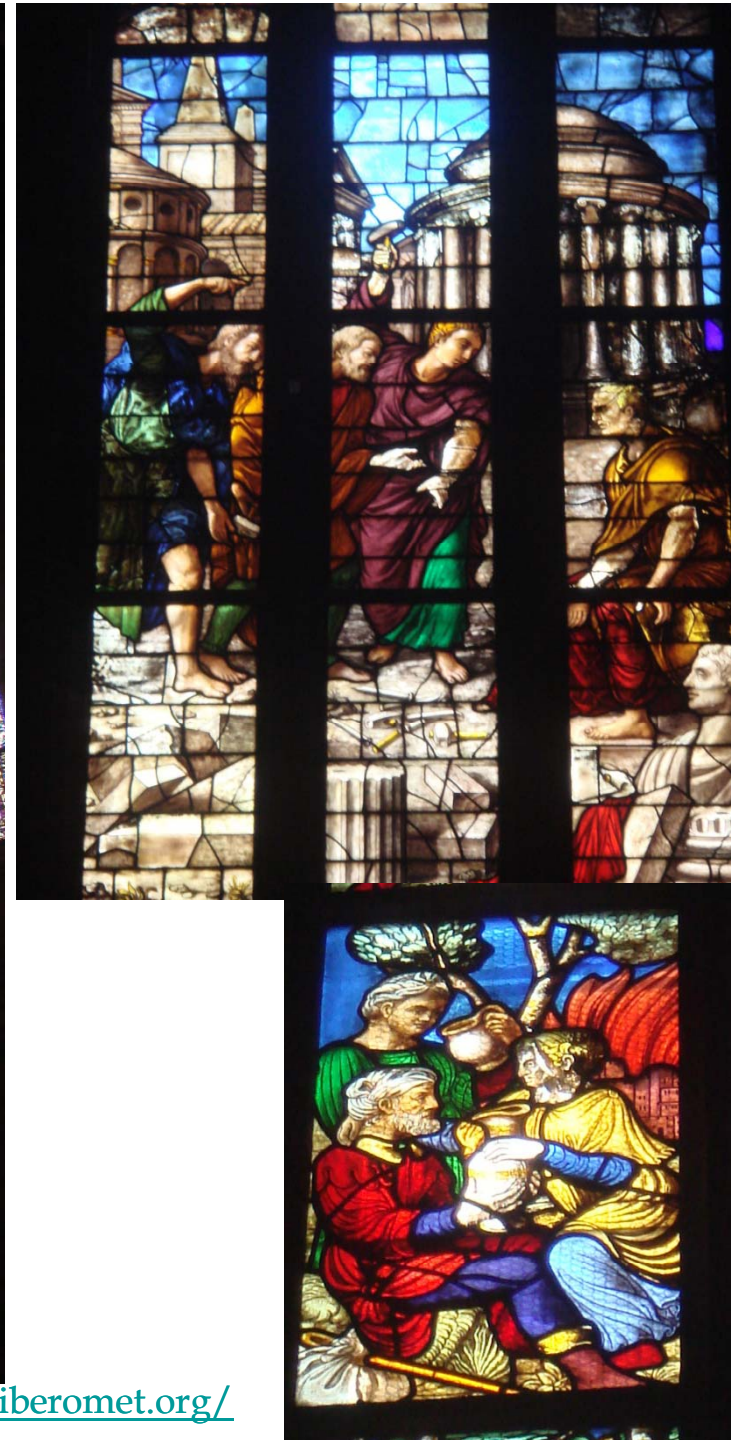


Grain size and grain boundaries have a strong effect on the *properties of materials*



10nm

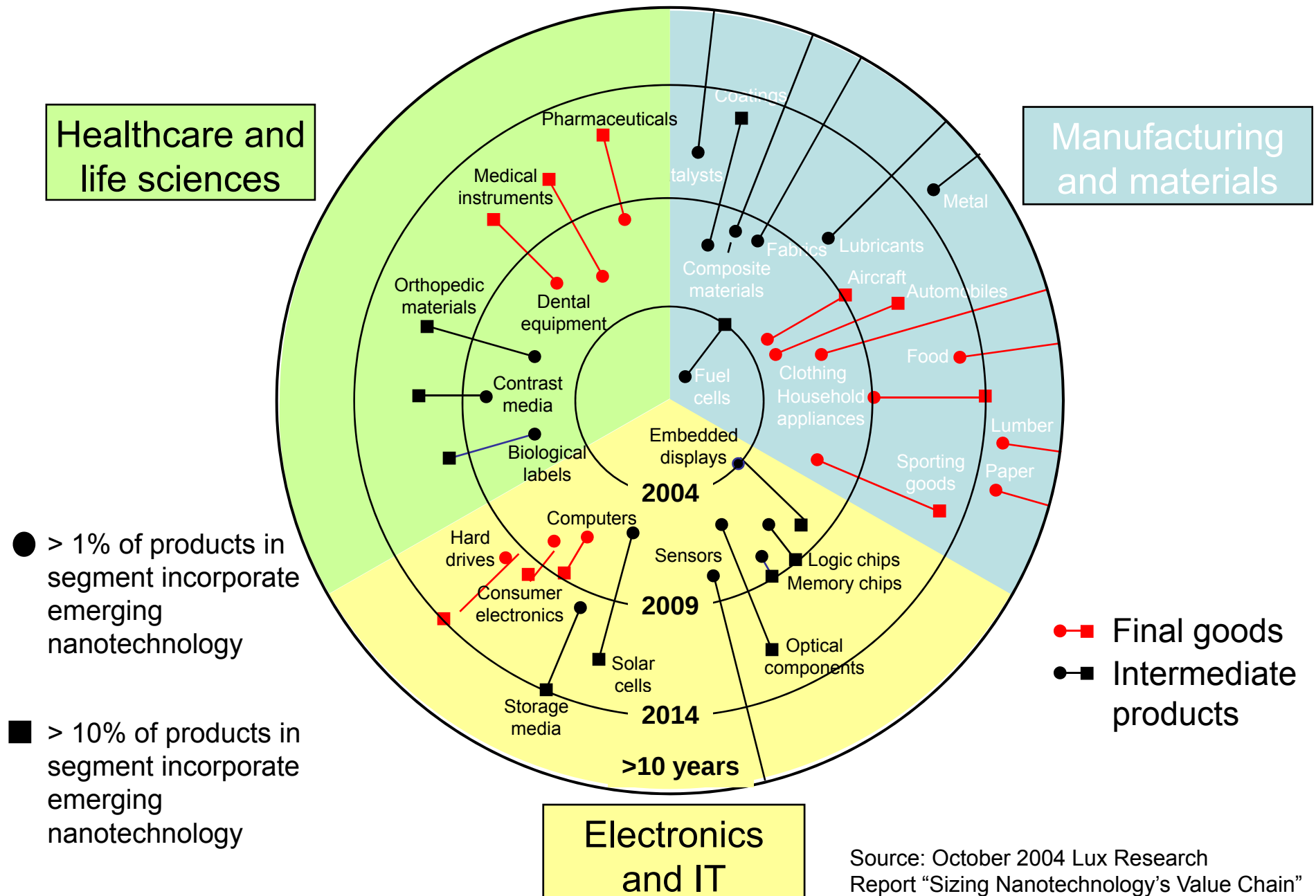
Pasado



Quantum effects on windows since
Greeks, Egyptian and middle age

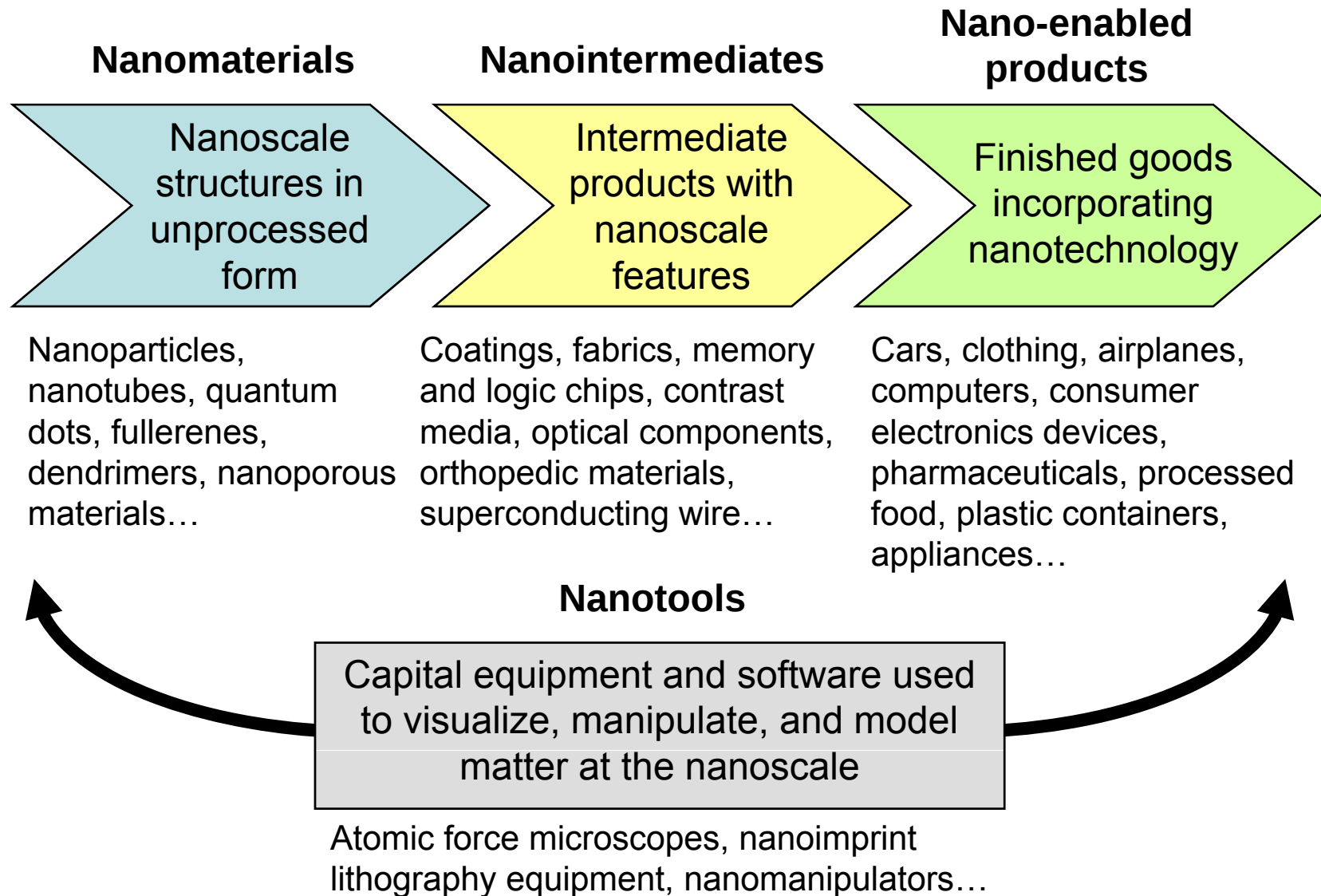
Cortesía M Sacilotti oct. 13-17 2008 Cartagena-Colombia <http://www.iberomet.org/>

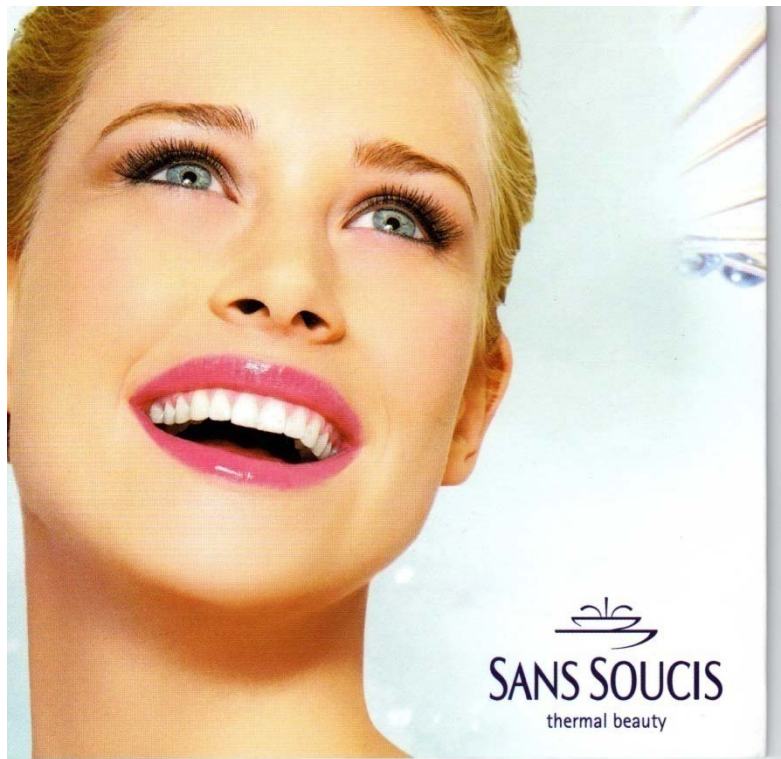
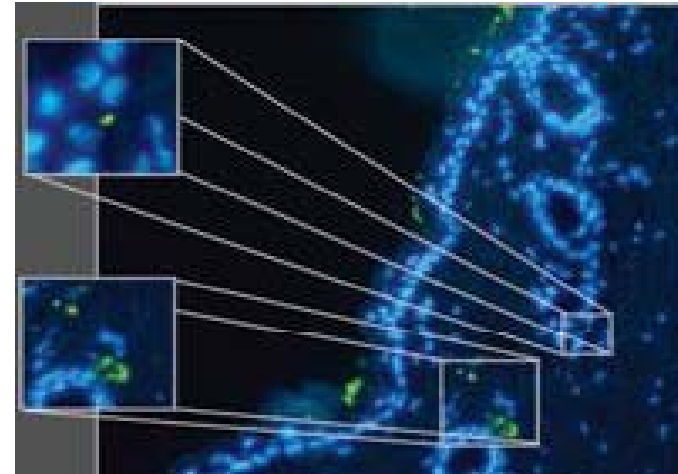
Potential and impact of Nanotechnology



Source: October 2004 Lux Research
Report "Sizing Nanotechnology's Value Chain"

The nanotechnology value chain





www.sanssoucisusa.com/

Skin penetration evidenced

Study of the penetration of nanoparticles known as quantum dots that fluoresce under some conditions, making them easier to see and track compared to other nanoparticles. The scientists looked at the distribution of quantum dots in mice whose skin had been exposed to about the same amount of ultraviolet light as might cause a slight sunburn on a person.

Do cosmetics, including mineral make-up, contain dangerous *nanoparticles*?

J. Mortensen, Oberdrster, P. Pentland, A. DeLouise Nano Lett., 2008, 8 (9)

Nanoparticulate
additives = 10%
better fuel economy

Nanocomposite body
moldings = 20%
lighter

Nanocoating = 3x
scratch resistance;
40% longer lifetime



Nanocomposite air
barriers = 2x better air
retention

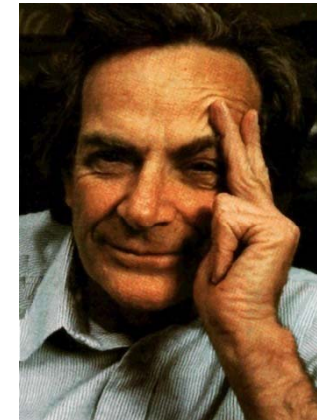
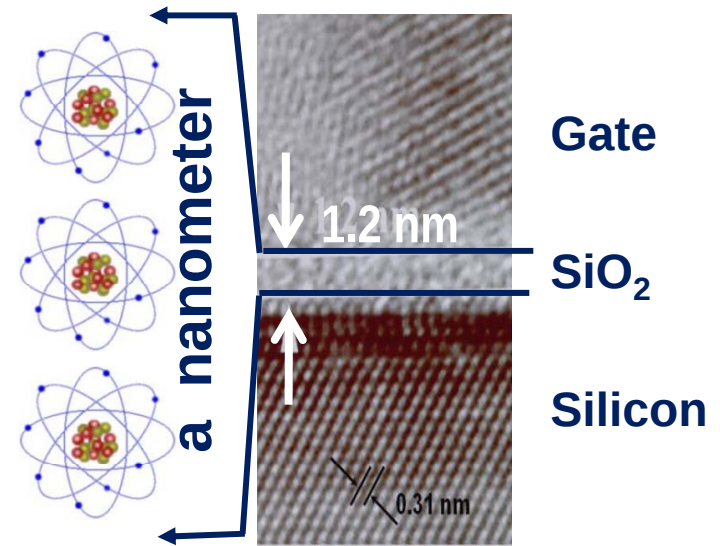
Nanoscale catalysts =
20% reduction in
emissions

Nanotechnology and Novel Materials

Explore & exploit unique phenomena and effects at atomic, molecular, and supra-molecular dimensions to create materials, devices, and systems with fundamentally novel properties and functions. **Nanoscale** gathers multidisciplinary approaches: Physics, Chemistry, Biology, Mathematics, Materials Sciences, and TICs, all of great benefit to humanity.

Applications are exciting; scientific & engineering potential is vast.

Nanotechnology represent an open disposition by policy makers to exploit its full potential for the benefit of society.



Feynman, 1959 *There's Plenty of Room at the Bottom*

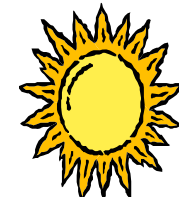
Motivaciones para el estudio de materiales a escala nano/micrométrica (Ga, Al, In)N

presente



Nasa satellite picture

20%
total light
economy



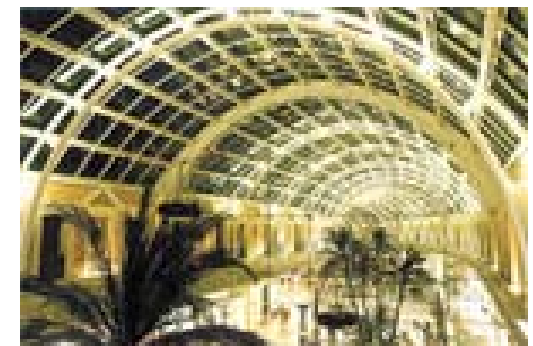
Light?
may be
LED is one
of the
solutions...



Presente



All ligthed by
LED



General lighting

(Ga, Al, In)N material's applications

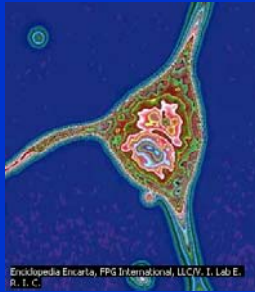
SIZE MATTER

Atomic nuclei $\sim 10^{-15}$ meters = 10^{-6} nanometers

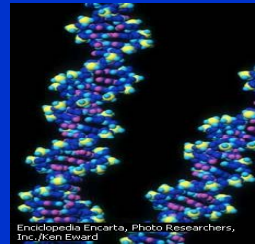
Atoms $\sim 10^{-10}$ meters = 0.1 nanometers

Nanoscale ~ 1 to 100 nanometers

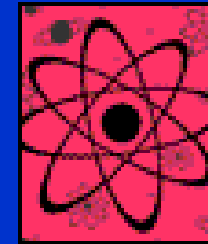
Everyday world ~ 1 meter = 10^9 nanometers



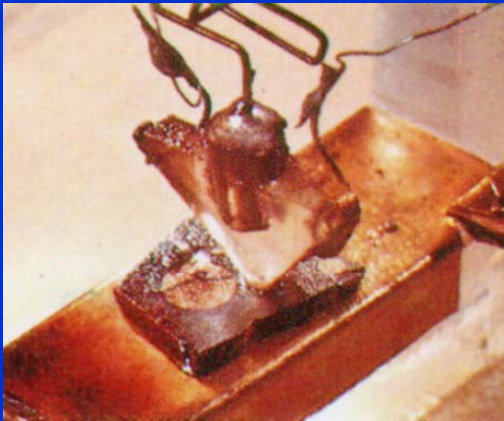
Célula ~ 1000 nm



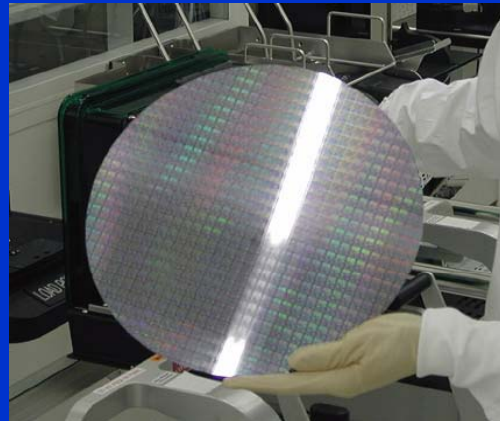
DNA ~ 2.5 nm



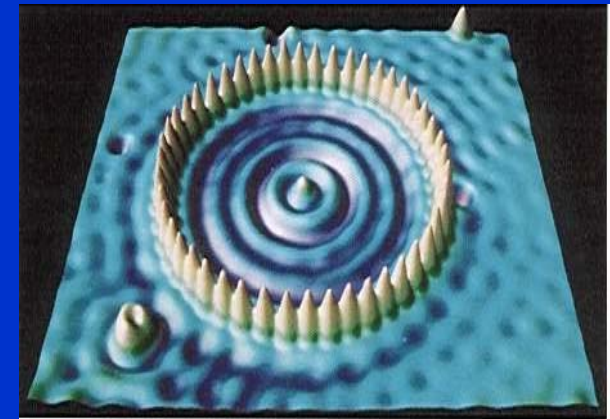
Atoms < 1 nm



Bell Labs, 1947: mm

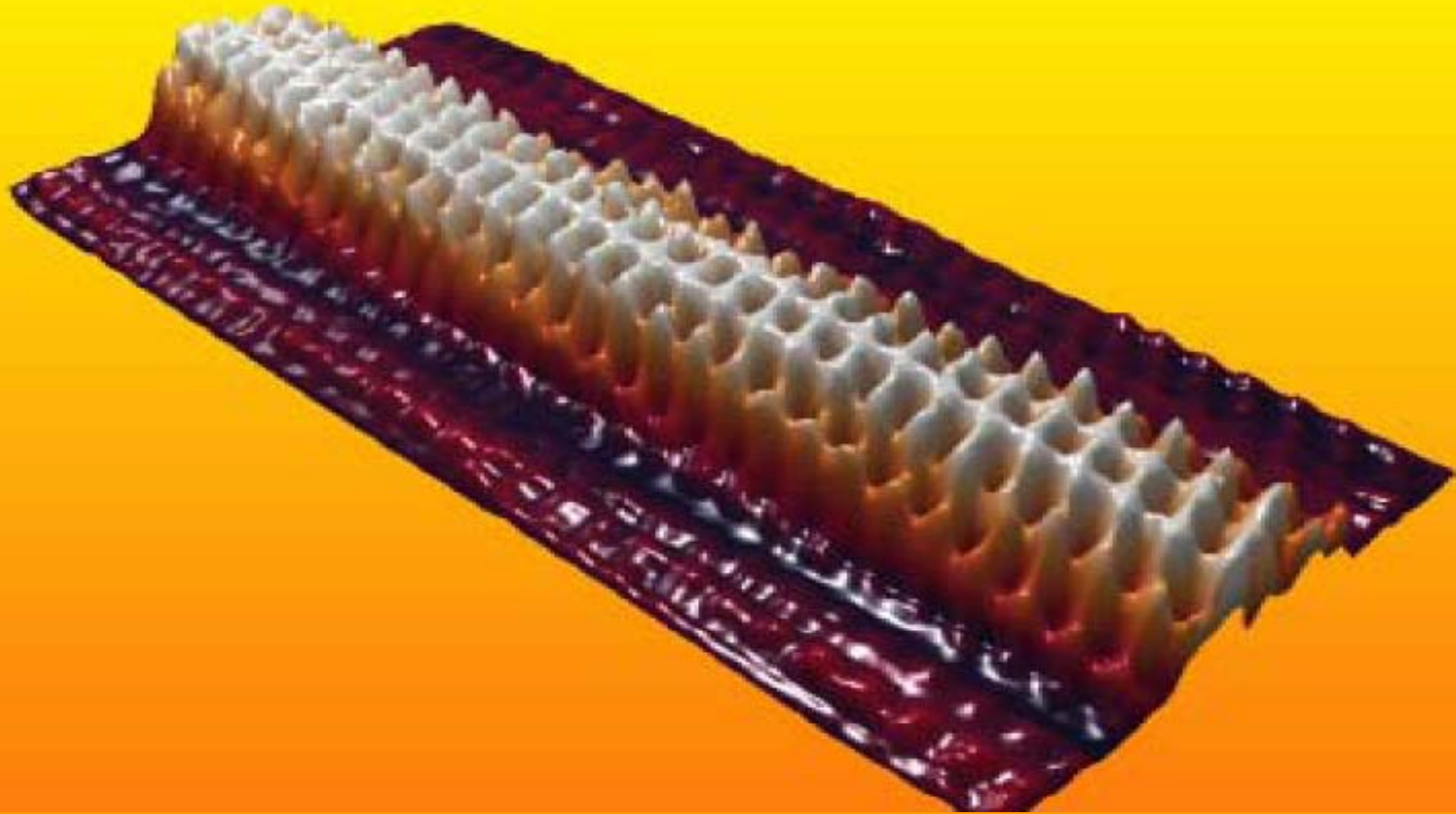


Intel 2004: μm



IBM 2002: nm

A scanning tunneling microscope image of a Single-Walled Carbon Nanotube
A symbol of the origins of Nanoscience & Nanotechnology



Propiedades de un material son de pendientes del tamaño y dimensión

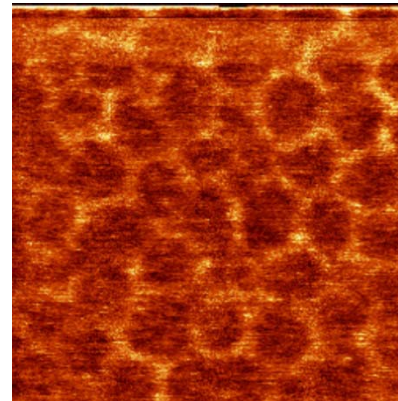
- Una propiedad describe como un material se comporta bajo ciertas condiciones
- Tipo se propiedades
 - Ópticas (color, transparencia)
 - Eléctricas (conductividad)
 - Físicas (Dureza, punto de fusión etc.)
 - Químicas (reactividad tasas de reacción)
- La propiedades son usualmente medidas mirando un gran conglomerado de átomos o moléculas ($\sim 10^{23}$)



- El oro tiene un color amarillo en bloque
- Nano partículas de oro aparecen de color rojo
 - Los electrones están confinados y no pueden moverse como en el bloque
 - Debido a este confinamiento los electrones reaccionan de una manera muy diferente con la luz.



“Bulk” gold looks yellow



12 nanometer gold particles look red

Propiedades ópticas del : Zinc Oxide (ZnO)

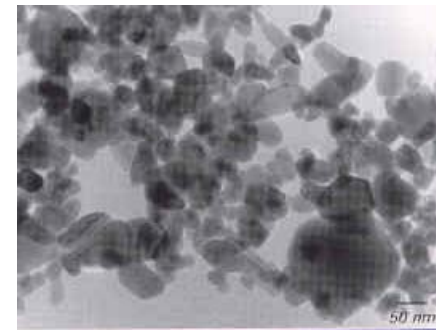
- Partículas macroscópicas de ZnO
 - Bloquen la luz UV
 - Dispersan la luz visible
 - Apariencia blanca
- Nano partículas de ZnO
 - Bloquen la luz UV
 - Su tamaño menor que la longitud de la luz visible que no dispersan la luz
 - Aparecen transparentes



“Traditional” ZnO
sunscreen is white

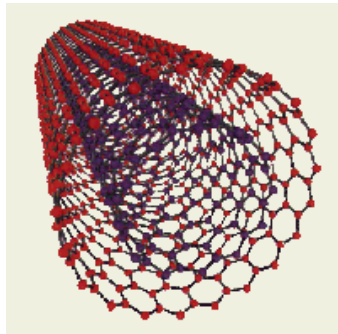


Nanoscale ZnO
sunscreen is clear



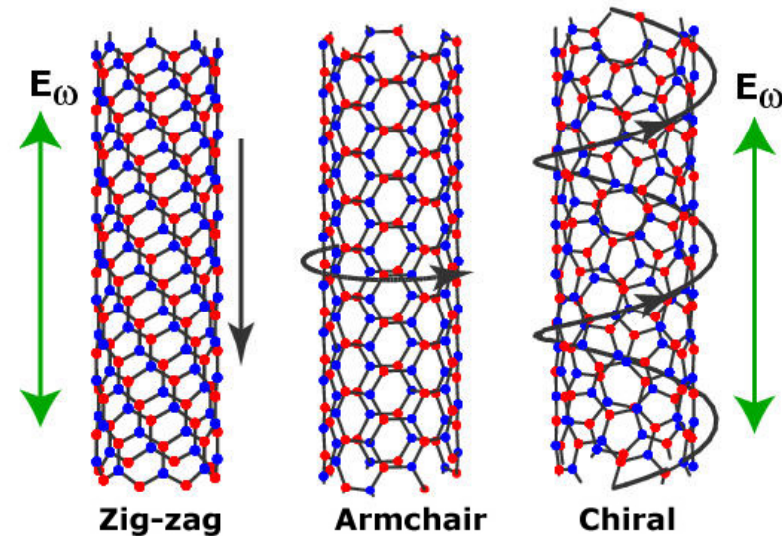
Zinc oxide nanoparticles

- Las propiedades eléctricas de CNT cambian con el diámetro la forma de “arrollamiento” y el numero de paredes pudiendo ser conductores, o semiconductores.

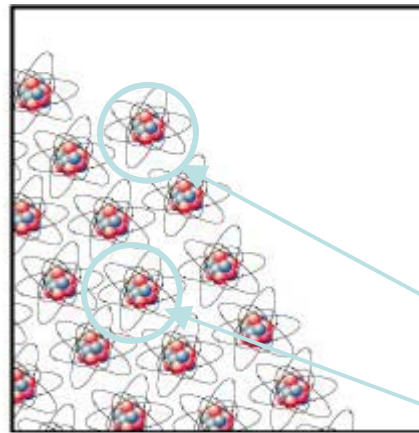
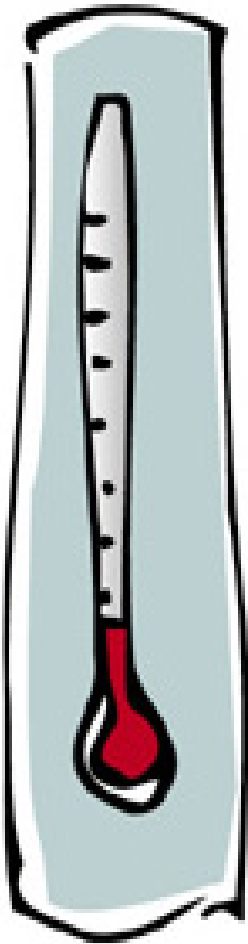


Multi-walled

Electric current
varies by tube
structure



Punto de fusión Temperatura a la cual los átomos o moléculas en una sustancia adquieren suficiente energía para superar las fuerzas intermoleculares que las mantienen “fijas” en un sólido.



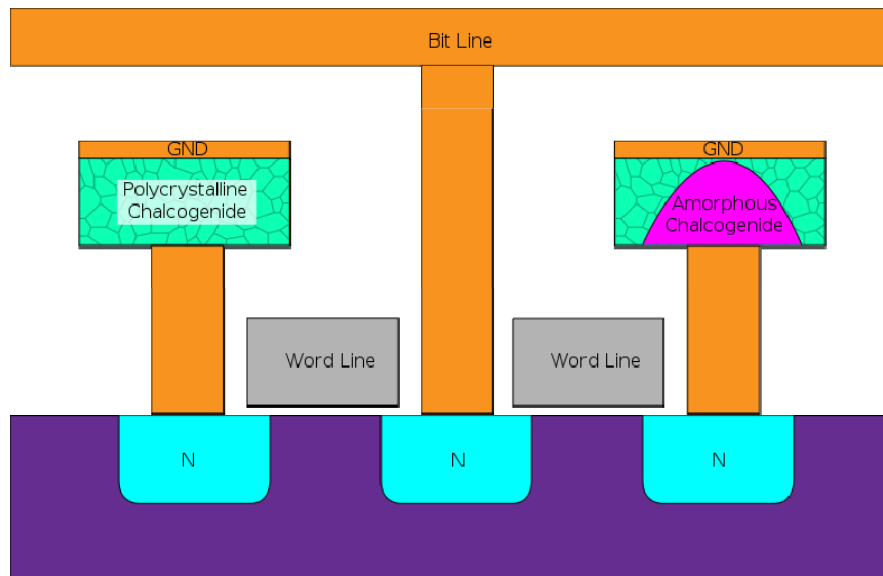
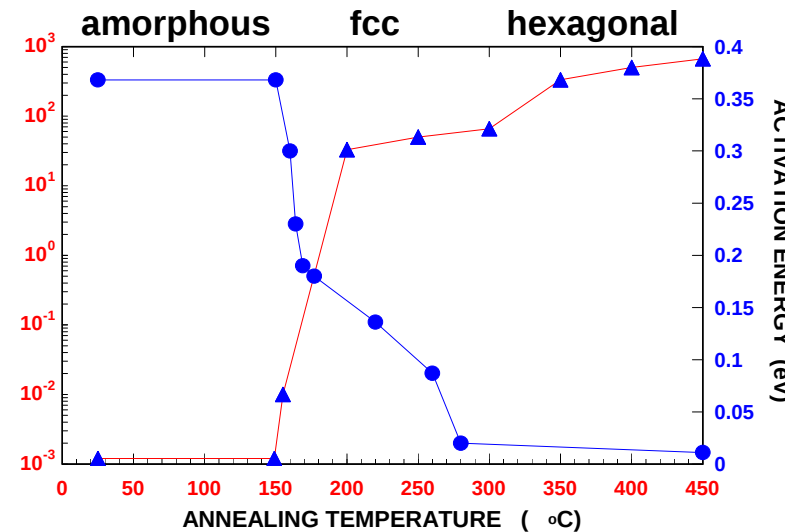
- Los átomos en la superficie requieren menos energía para “liberarse” debido a que están en contacto con menos átomos

El Punto de fusión depende del tamaño

In contact with 3 atoms

In contact with 7 atoms

Phase-Change Memory PRAM uses the unique behavior of chalcogenide glass, which can be "switched" between two states, crystalline and amorphous, with the application of heat.



Samsung' unveiled a 512Mb multi chip package featuring PRAM , which is due to be available for use in mobile handsets later this quarter (May 6 2010)

A cross-section of two PRAM memory cells. One cell is in low resistance crystalline state, the other in high resistance amorphous state.

<http://www.telecoms.com/20183/samsung>

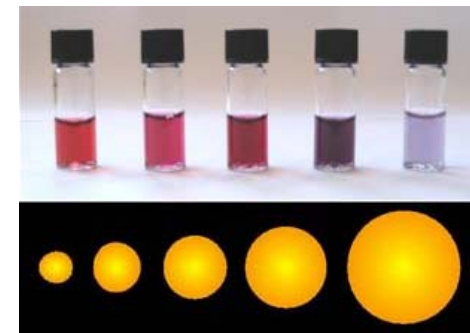
Efectos Cuánticos

- La mecánica clásica usada para entender la materia a escala macroscópica falla para..
 - Objetos a nanoscala
- La mecánica cuántica describe los fenómenos que no se entienden clásicamente ...
 - Probabilidad (mejor que la certeza) de que un electrón sea encontrado en un solido.



Macrogold

Nanogold



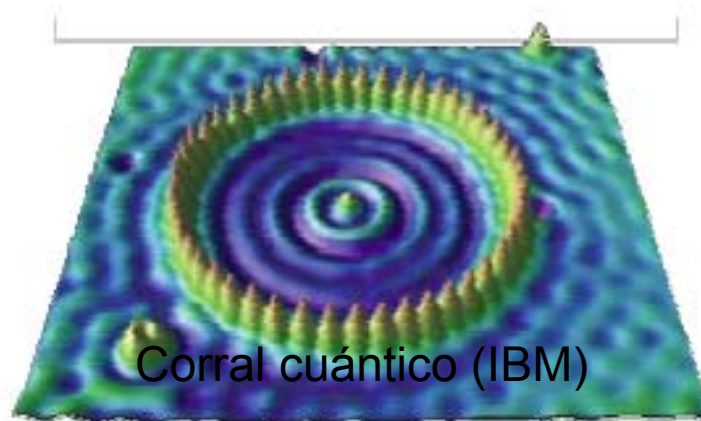
Por qué “Nano” es diferente?

Aspectos intrínsecos a la naturaleza cuántica de la materia:

Condensado de Bose-Einstein, transiciones conductor-aislante, confinamiento de cargas, QUANTUM DOTS, etc.

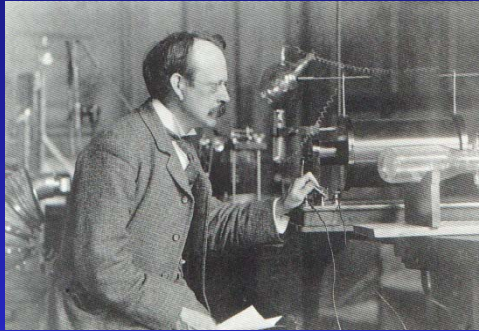
Aspectos intrínsecos a la aspectos (clásicos) estructurales y de escala:

Incremento de relación superficie/volumen, temperatura de fusión, transiciones de fase, modos vibracionales, etc.



Corral cuántico (IBM)

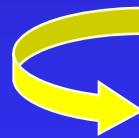
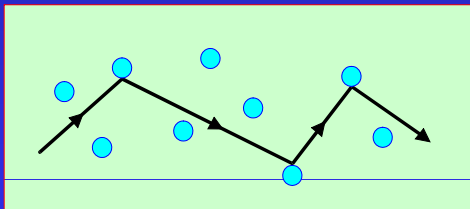
Los últimos años de la Era Clásica



1897 – Descubrimiento del electrón por J.J. Thomson

1900 – **Modelo de Drude para electrones en metales**

- Gas de electrones libres $n \sim 10^{22} \text{ cm}^{-3}$
- Interacción e-red despreciable
- Interacción e-e despreciable
- Colisiones con los iones
- $P(dt) = dt/\tau$

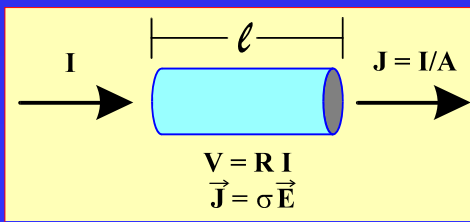


$$\sigma = ne^2\tau/m$$

$$\sigma/\kappa = 3/2 (k/e)^2 T$$

Ley de Ohm

Wiedemann-Franz



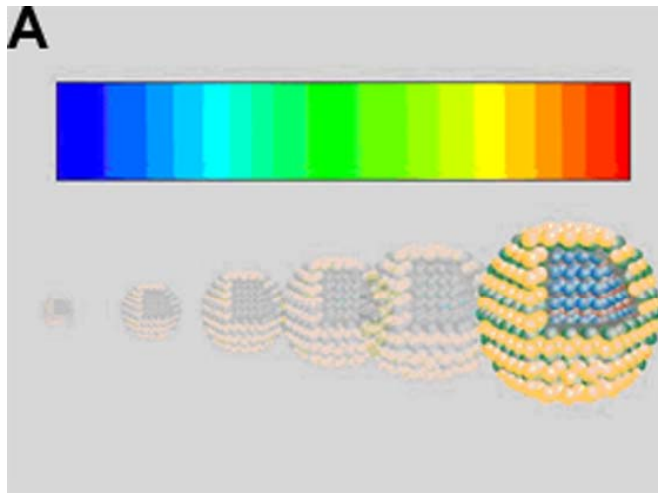
Fallas

- C_v independiente de T
- χ dependiente de T
- ρ Independiente de T

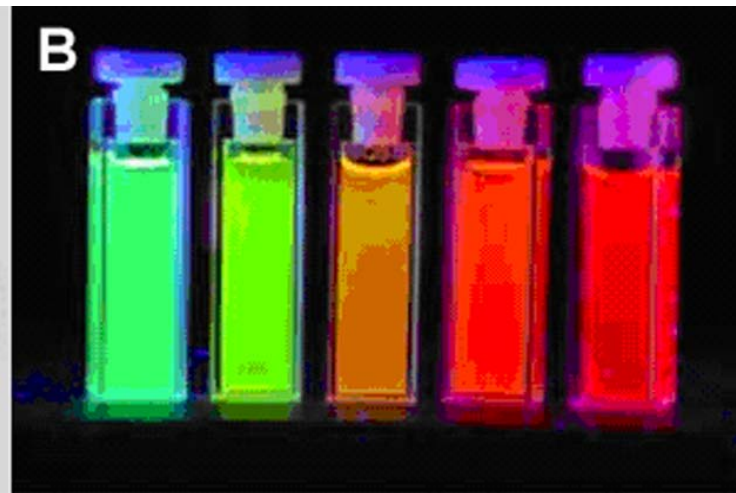
Quantum Mechanics

- Particle in a box

$$E_1 = \frac{\hbar^2 \pi^2}{2mL^2}$$



(Courtesy of Dylan M. Spencer)



(Source: Philips)

ALGUNOS CONCEPTOS Y CANTIDADES

- *An electron:*

$$E = (\hbar k)^2 / (2m_e); \quad P = \hbar k; \quad \lambda_e = h / (2m_e E)^{1/2}; \quad 1\text{eV} \rightarrow 12.3 \text{ \AA}.$$

(de Broglie electron)

- *A photon:*

$$E = h\nu; \quad P = E/c; \quad \lambda_{\text{photon}} = (hc)/E; \quad 1\text{eV} \rightarrow 1.24 \text{ \mu m}.$$

- *A photon (the energy quanta of lattice vibrations):*

$$E = \hbar\omega; \quad P = \hbar q; \quad \omega_{\text{phonon}} = c_s/q \quad (c_s = \text{the sound velocity})$$

Plank constant: $h = 6.626 \times 10^{-34} \text{ J-s} = 4.1357 \times 10^{-15} \text{ eV-s}$

$$\hbar = h / (2\pi) = 6.5822 \times 10^{-16} \text{ eV-s}$$

ALGUNOS CONCEPTOS Y CANTIDADES

- *Wave function:* $\Phi(\mathbf{r}, t) = \psi(\mathbf{r})f(t) = A \cdot \exp[-(\mathbf{k} \cdot \mathbf{r} - \omega t)]$
 $|\Phi(\mathbf{r}, t)|^2$: the probability of finding an electron at point $\mathbf{r}$ and time t .

- *The Schrödinger wave equation,*

$$\left[-\frac{\hbar^2}{2m}\nabla^2 + U(\vec{r})\right]\Phi(\vec{r}, t) = i\hbar \frac{\partial \Phi(\vec{r}, t)}{\partial t}.$$

- *The time-independent Schrödinger wave equation,*

$$\hat{H}\psi(\vec{r}) = E\psi(\vec{r}), \quad \text{where} \quad \hat{H} = -\frac{\hbar^2}{2m}\nabla^2\psi(\vec{r}) + U(\vec{r})$$

- *Uncertainty principle:*

$$\Delta P \Delta x > \hbar/2; \quad \Delta E \Delta t > \hbar/2.$$

Primeros Impactos de la Mecánica Cuántica en la FMC



Modelo de Sommerfeld para electrones en metales

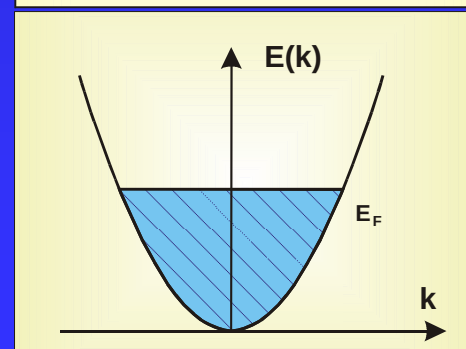
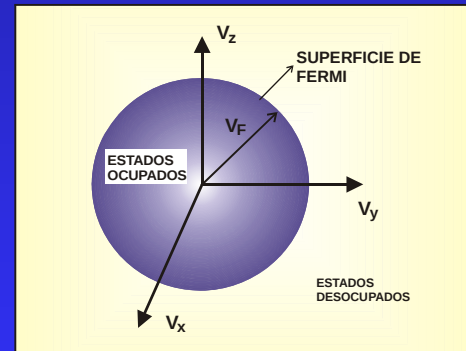
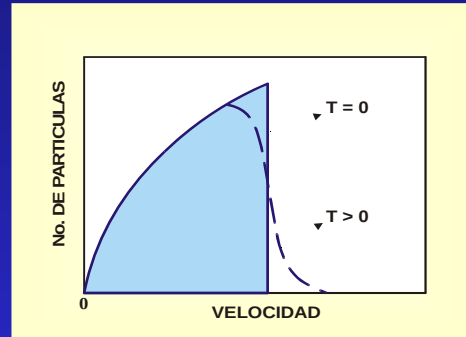
➤ Estadística de Fermi-Dirac a e

$$f(E_k) = \frac{1}{e^{\frac{(E_k - \mu)}{k_B T}} + 1}$$

$$\Psi(\vec{r}) = \frac{1}{\sqrt{V}} e^{i\vec{k} \cdot \vec{r}} \quad E(\vec{k}) = \frac{\hbar^2 k^2}{2m}$$

- E_F nivel más energético a $T=0$
- Superficie de Fermi esférica
- $C_v \sim T$
- χ independiente de T

❑ ¿Metales aislantes?



ELECTRONES

Electrones Libres:

In a free space, the potential $U = 0$,

$$-\frac{\hbar^2}{2m} \nabla^2 \psi(\vec{r}) = E \psi(\vec{r})$$

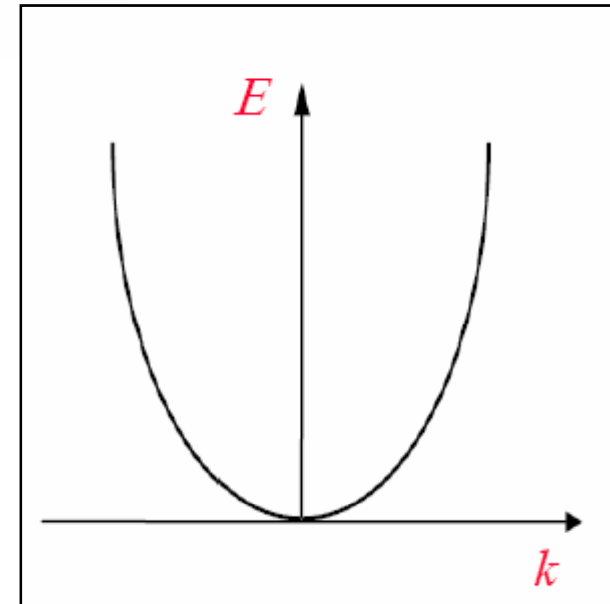
Solución de la función de onda

$$\psi(\vec{r}) = \frac{1}{\sqrt{L^3}} \exp(\pm i \vec{k} \cdot \vec{r}),$$

Donde $k = (2m_e E / \hbar^2)^{1/2}$. es el vector de onda.

Ej:

$$E = (\hbar k)^2 / (2m_e).$$

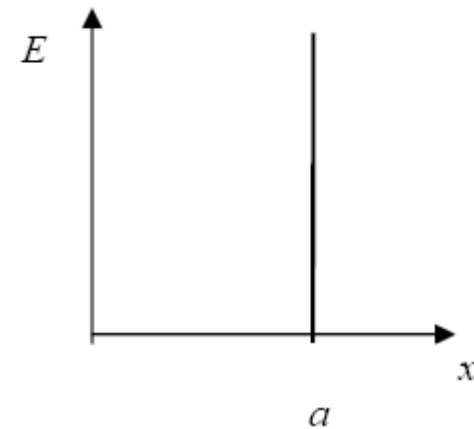


Los electrones libres tienen un comportamiento parabólico continuo de la energía con respecto al valor de K

ELECTRONES

Electrones en un pozo de potencial infinito 1-D

$$U(x) \begin{cases} \infty & x < 0 \\ 0 & 0 < x < a \\ \infty & x > a \end{cases}$$



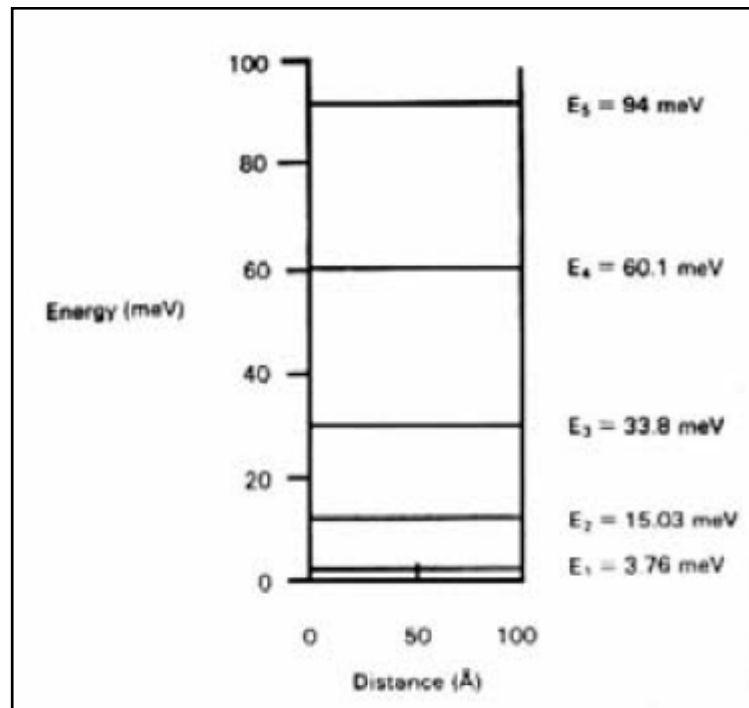
La ecuación de onda de Schrodinger
Puede ser escrita como:

$$\frac{d^2 \psi(x)}{dx^2} + k_x^2 \psi(x) = 0 \quad \text{Donde: } k_x = (2m_e E / \hbar^2)^{1/2}.$$

ELECTRONES

Solución: E tiene valores discretos de energía $E = E_n = \frac{\pi^2 \hbar^2 n^2}{2m_e a^2}$.

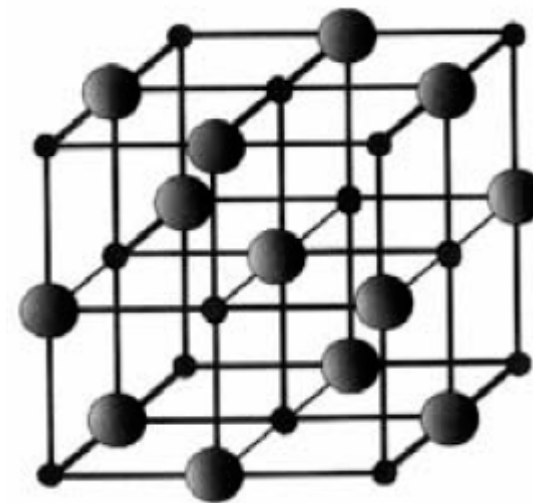
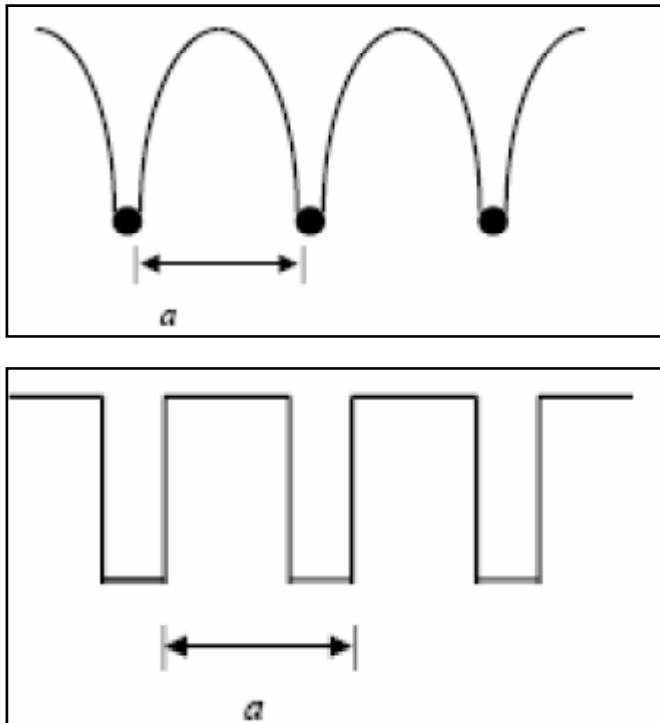
Ej:



Los electrones en un pozo de potencial de tamaño limitado forman niveles de energía discretos

ATOMOS

CADENAS DE ATOMOS, REDES & ELECTRONES EN UN POTENCIAL PERIODICO

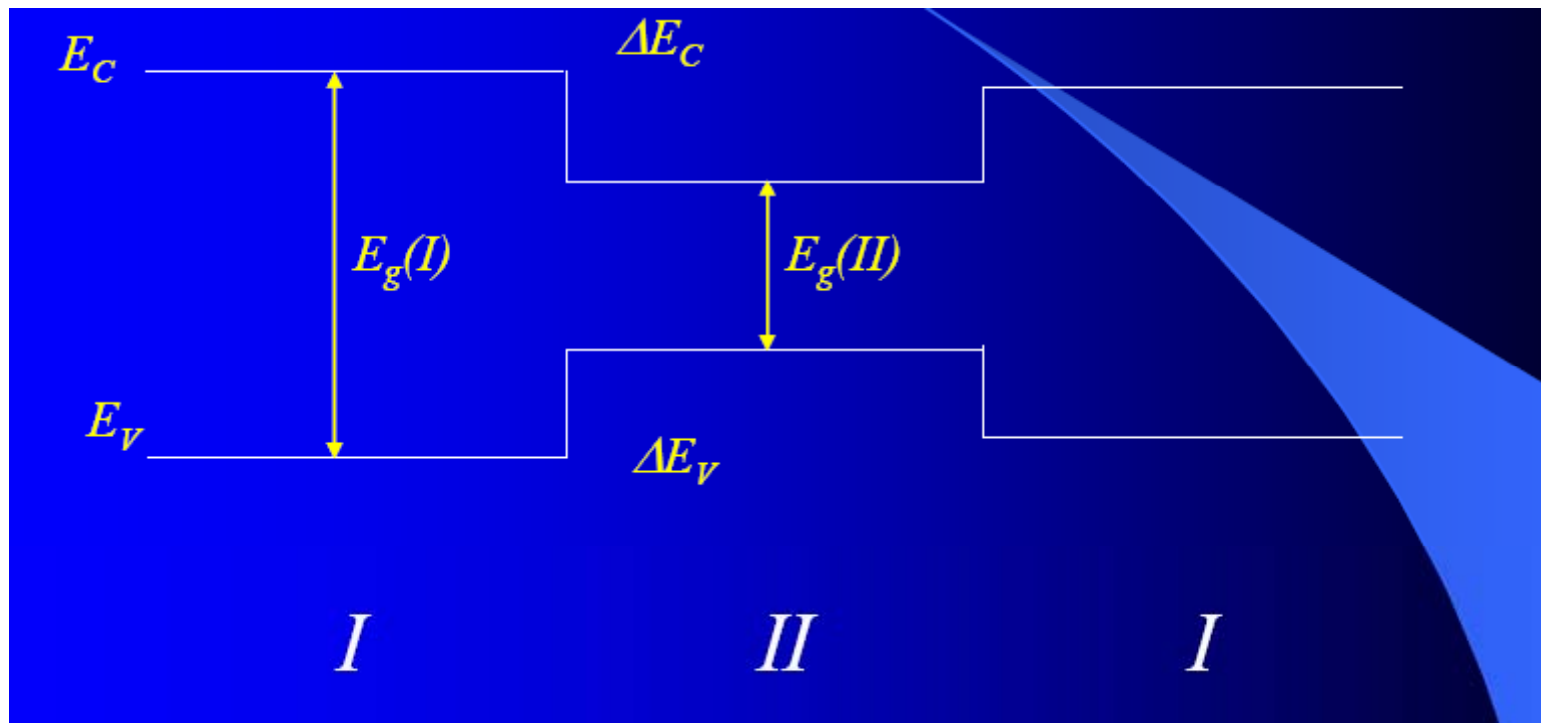


Red Cristalina

Resultando en un gap de energía prohibido

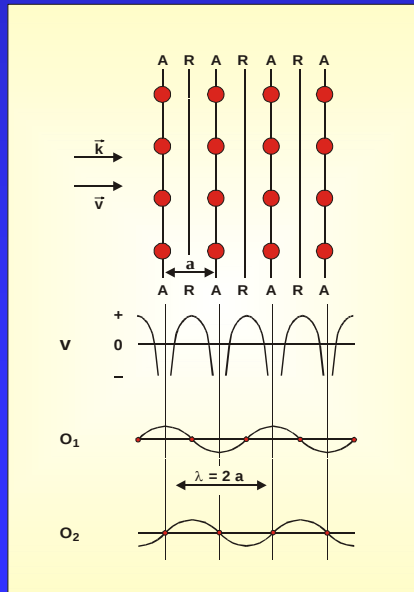
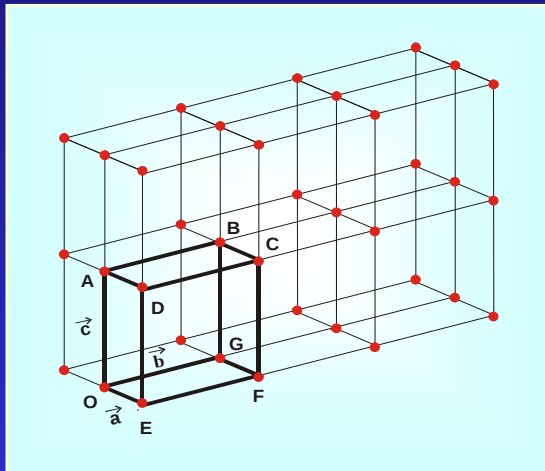
BANDAS DE ENERGIA

HETEROESTRUCTURAS SEMICONDUCTORAS & POZOS CUANTICO



La diferencia de la banda gap

$$\Delta E_g(I) = E_g(I) - E_g(II) = \Delta E_C + \Delta E_V$$



Teorema de Bloch

$$\vec{T}_n = n_1 \vec{a} + n_2 \vec{b} + n_3 \vec{c} \quad \text{Simetría de Traslación}$$

$$U(\vec{r}) = U(\vec{r} + \vec{T}) \quad \Rightarrow \quad H(\vec{r}) = H(\vec{r} + \vec{T})$$



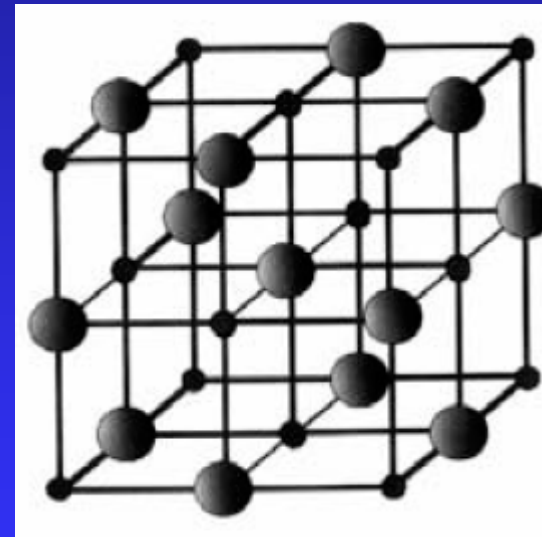
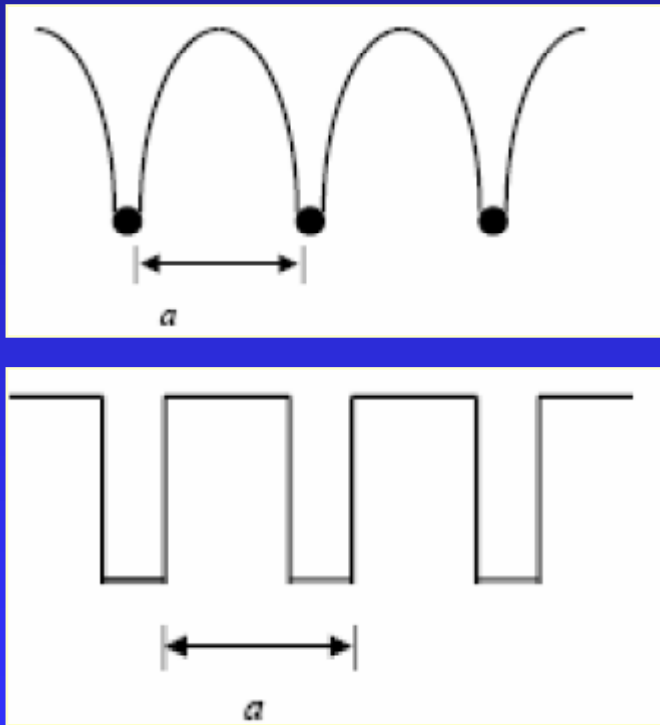
$$\Psi(\vec{r}) = u_k(\vec{r}) e^{i\vec{k} \cdot \vec{r}} \quad \text{Función de Bloch}$$

$$u_k(\vec{r}) = u_k(\vec{r} + \vec{T})$$

$$\Psi_k(\vec{r} + \vec{T}) = e^{i\vec{k} \cdot \vec{T}} \Psi_k(\vec{r})$$

ATOMOS

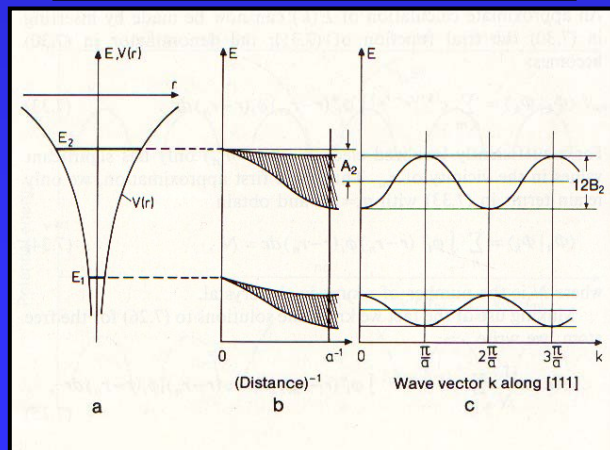
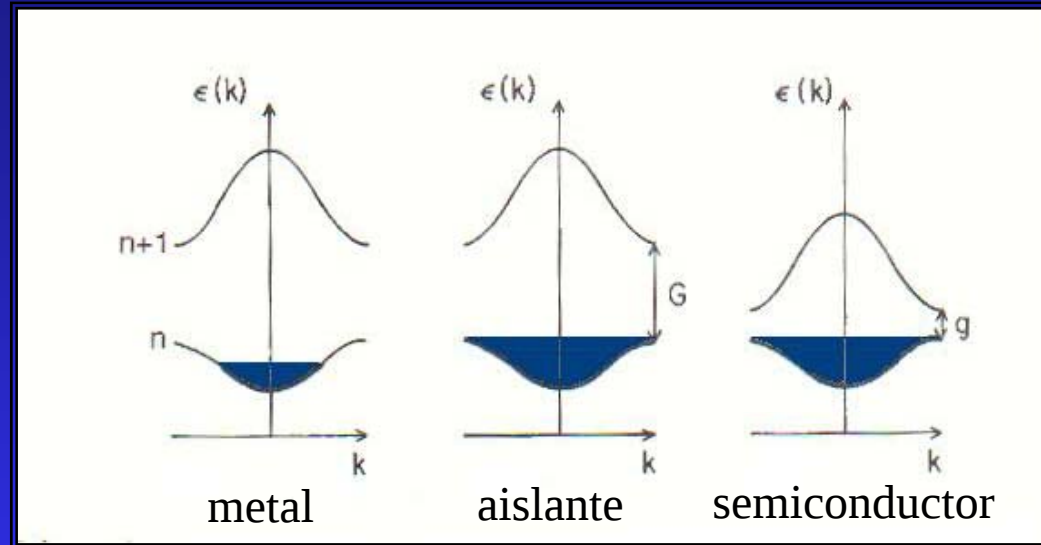
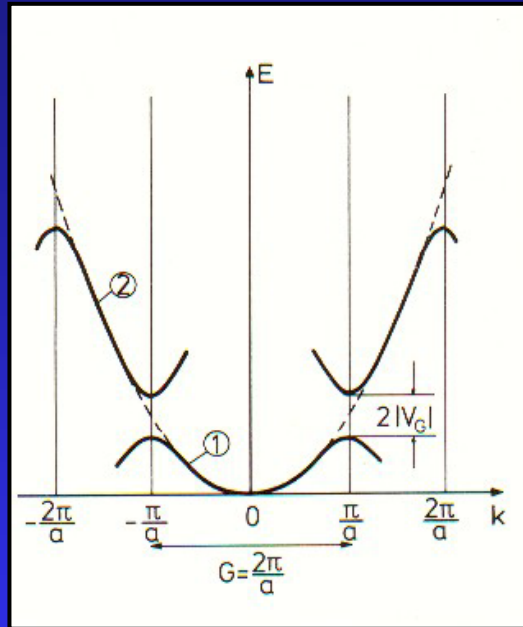
CADENAS DE ATOMOS, REDES & ELECTRONES EN UN POTENCIAL PERIODICO



Red Cristalina

Resultando en un gap de energía prohibido

El Paradigma de la Estructura de Bandas



Modelo de electrón casi libre $\rightarrow E_G \sim V_G$

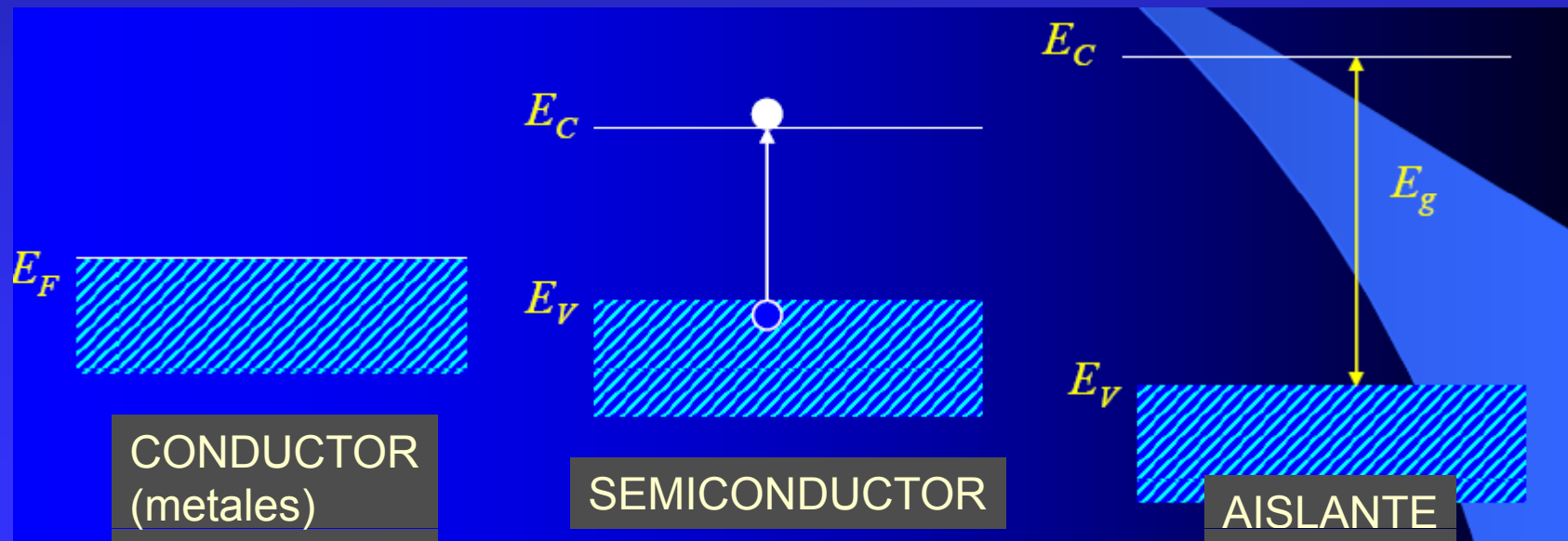
Modelo de enlace fuerte

ancho de banda $\sim$ Integral de translapación

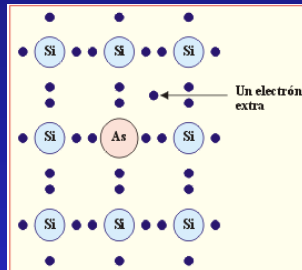
BANDAS DE ENERGIA

ESTRUCTURA DE BANDAS

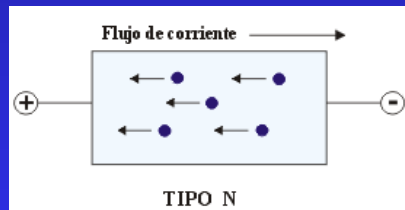
E_F : Energía del nivel de Fermi
 E_V : Energía mínima de la banda de valencia.
 E_C : Energía mínima de la banda de conducción.
 E_g : Energía asociada con la banda prohibida (gap)



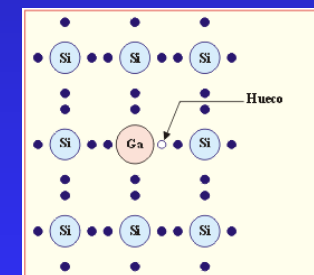
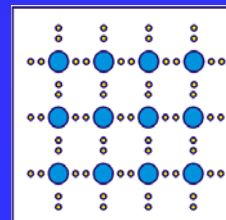
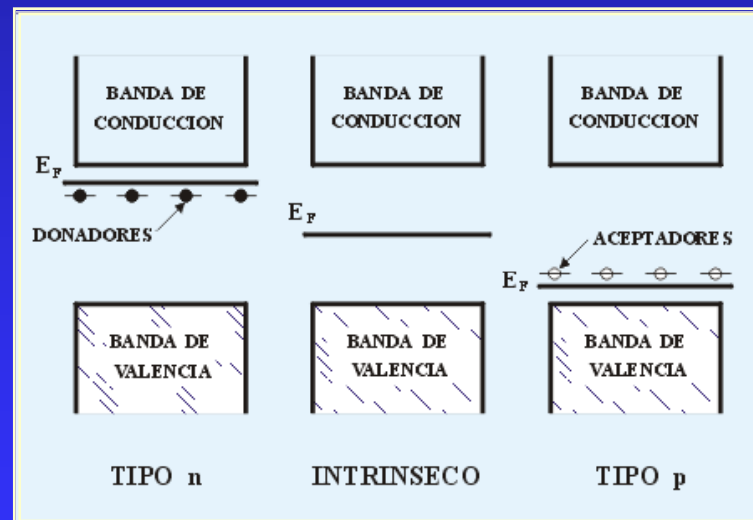
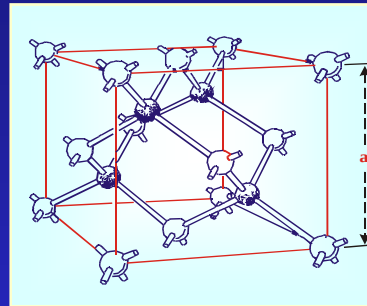
Materiales Semiconductores



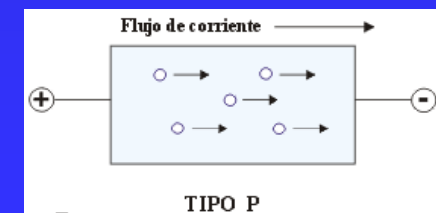
Si Tipo n



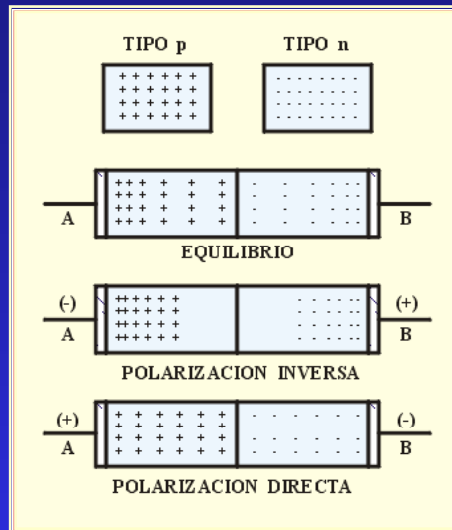
Si



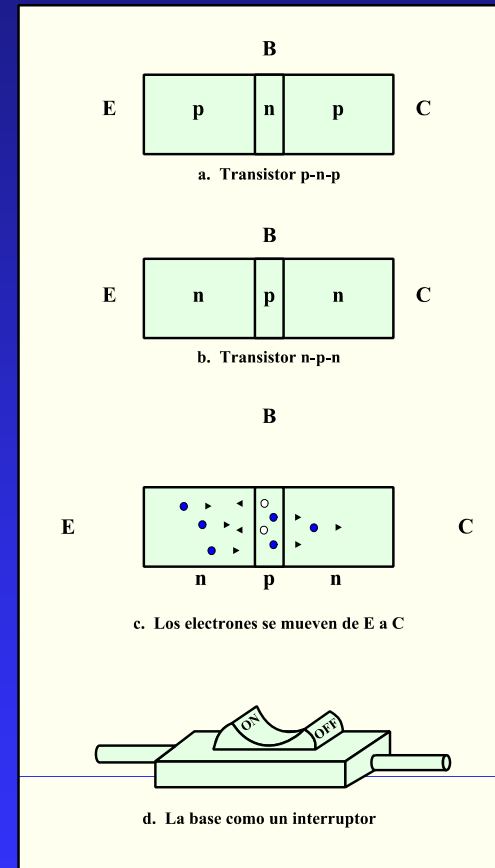
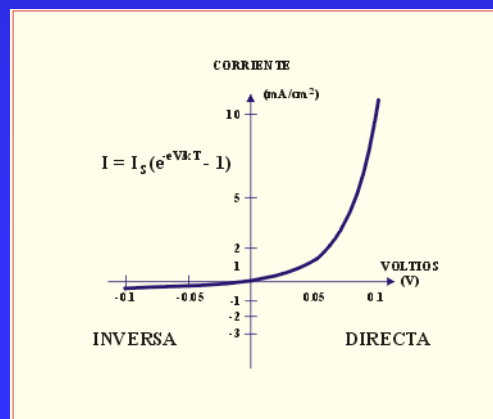
Si Tipo p



Dispositivos Semiconductores

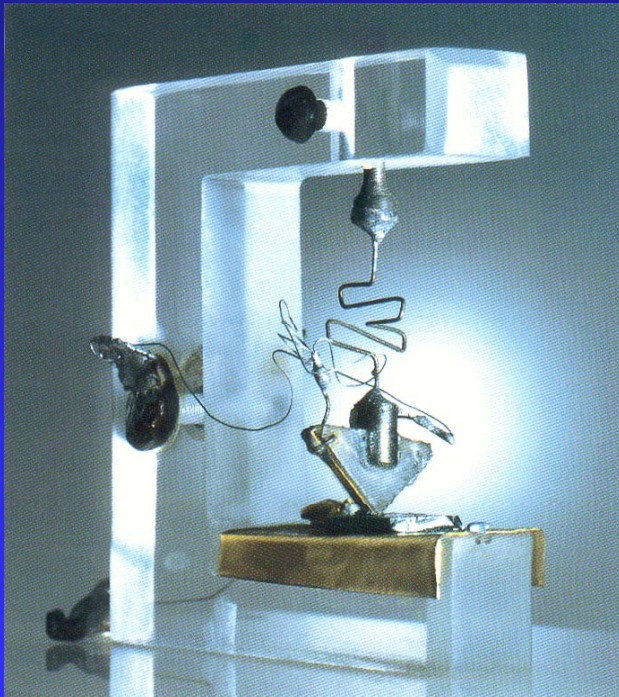


Diodo

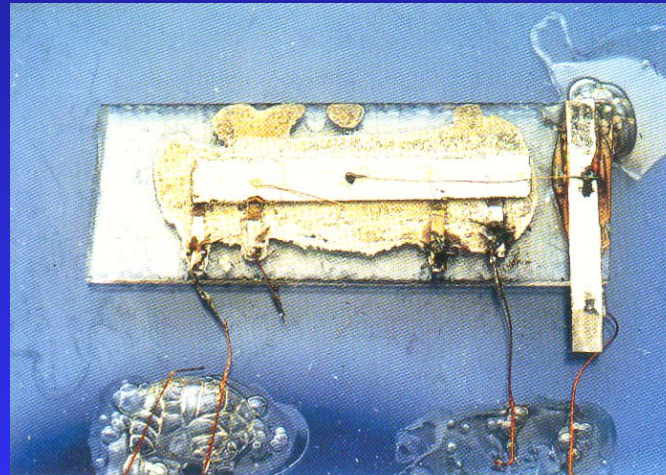


Transistor

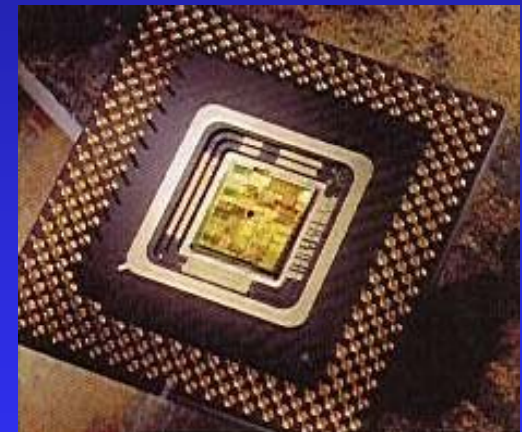
Dispositivos Semiconductores



Transistor:
Bardeen, Shockley, Brattain
Bell Labs. 1947



Circuito Integrado:
Kilby.
Texas Instruments. 1958



Chip Pentium :
Intel Corporation.
2000

Interacción e – fonón: Resistividad

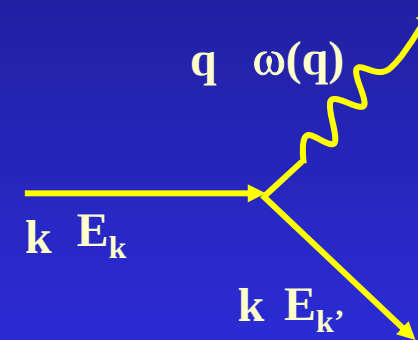
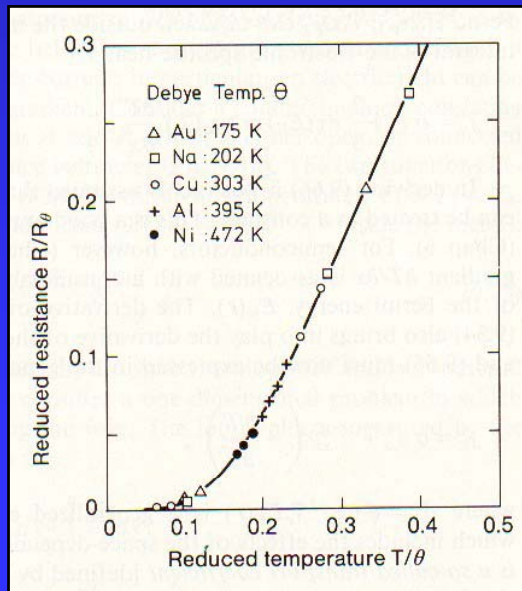


Aproximación adiabática $\mu_e \gg \mu_i$

Oscilaciones de la red cuantizadas: fonones

$$H = \sum_l \frac{M_l}{2} \dot{u}_l^2 + \Phi(u_1, u_2, \dots, u_N)$$

Relación de Bloch-Grüneisen



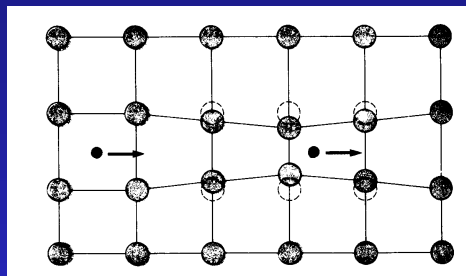
$$\rho = \frac{m^*}{ne^2} \frac{1}{\tau}$$

$$\rho_{ph}(T) = A(T/\Theta)^5 \int_0^{\Theta/T} \frac{x^5 dx}{(e^x - 1)(1 - e^{-x})}$$

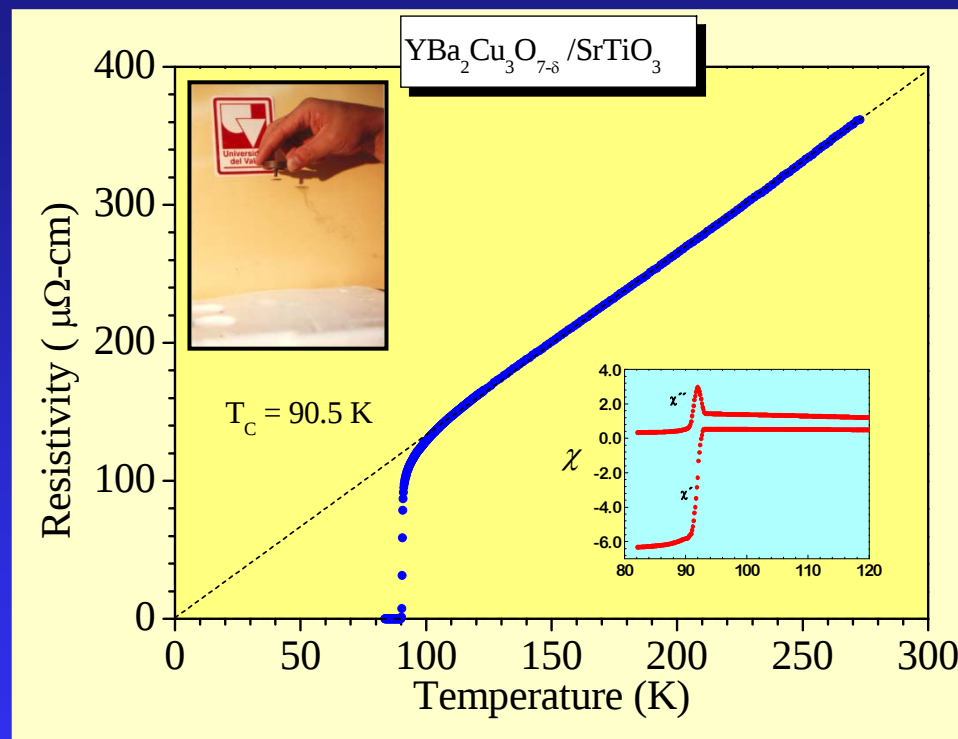
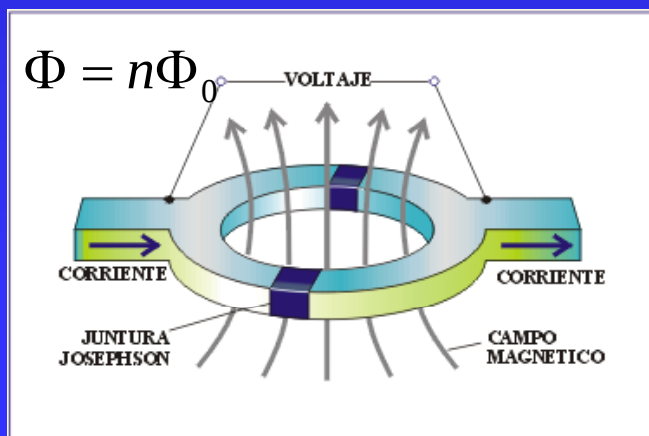
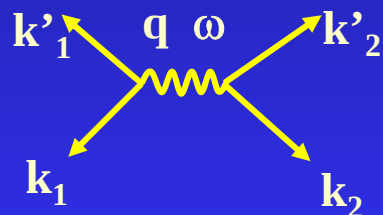
Interacción e – e : Superconductividad



Teoría BCS



Par de Cooper

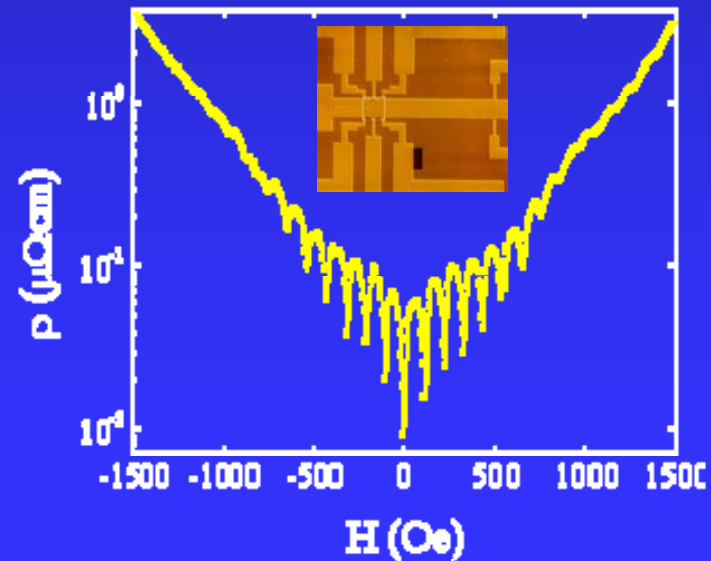
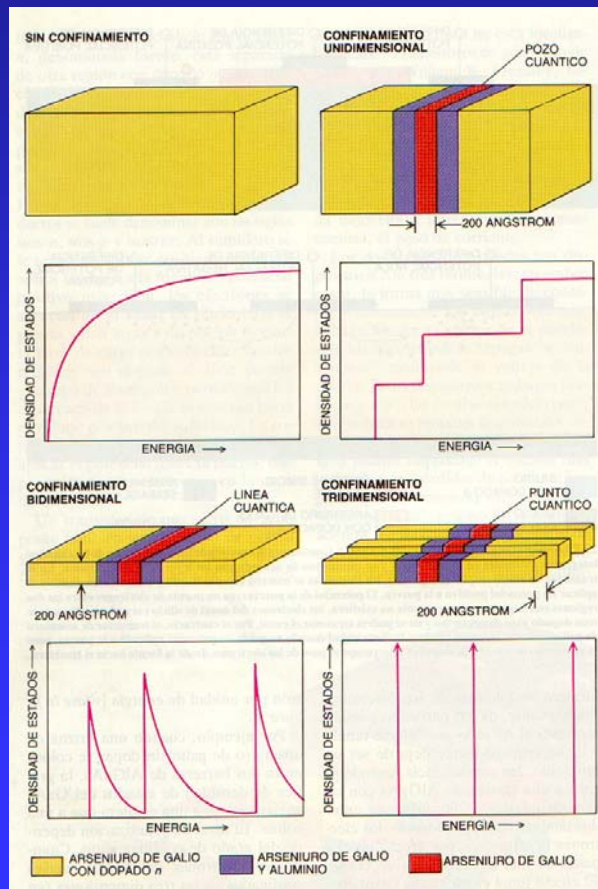


$$\Phi_0 = \frac{h}{2e} = 2.067 \times 10^{-15} \frac{T}{m^2}$$

Confinamiento Cuántico

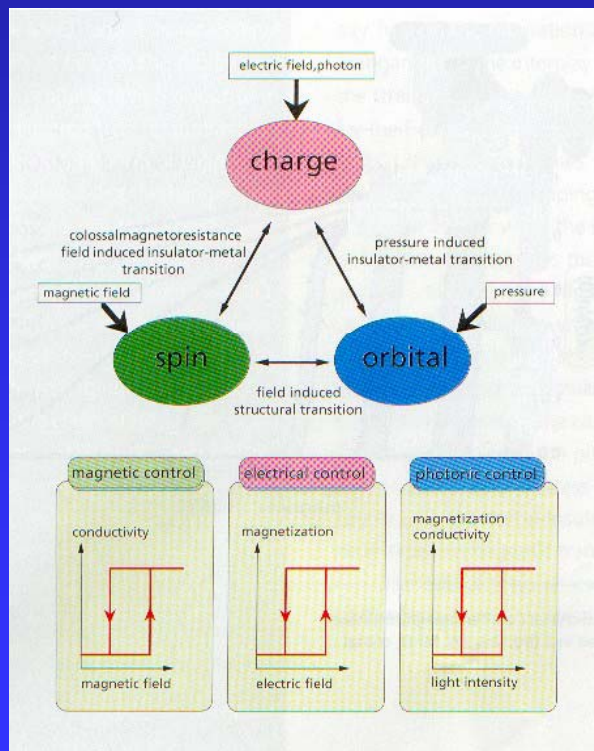


Física de baja dimensionalidad

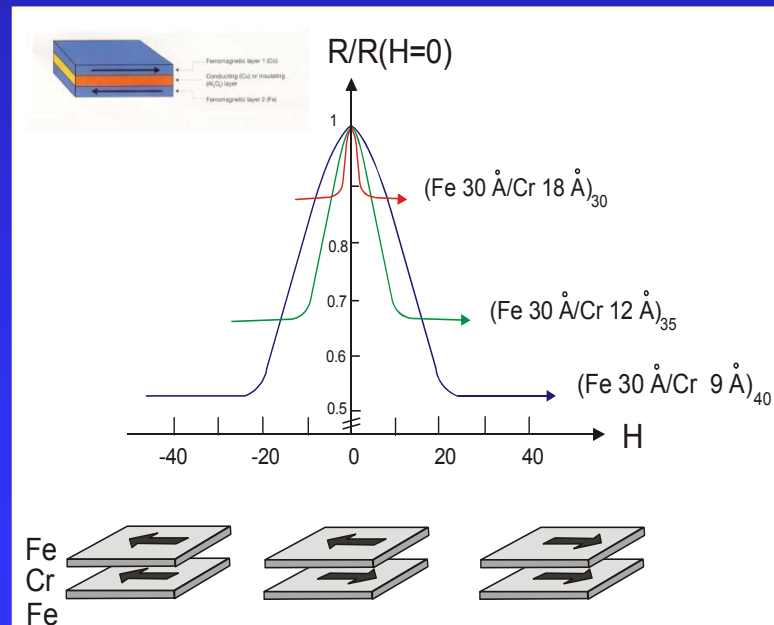




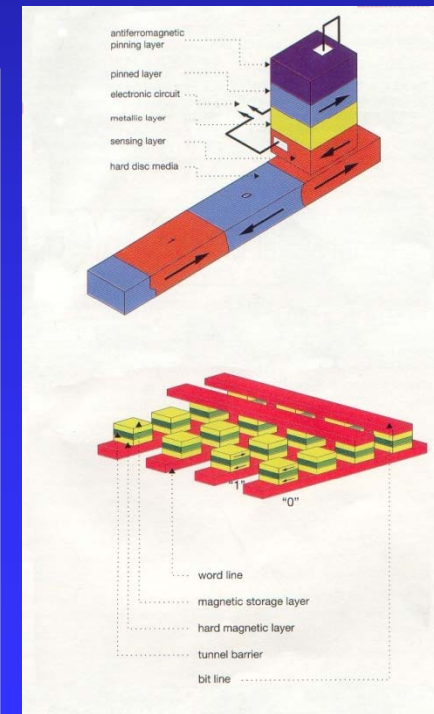
e:carga+spin



GMR

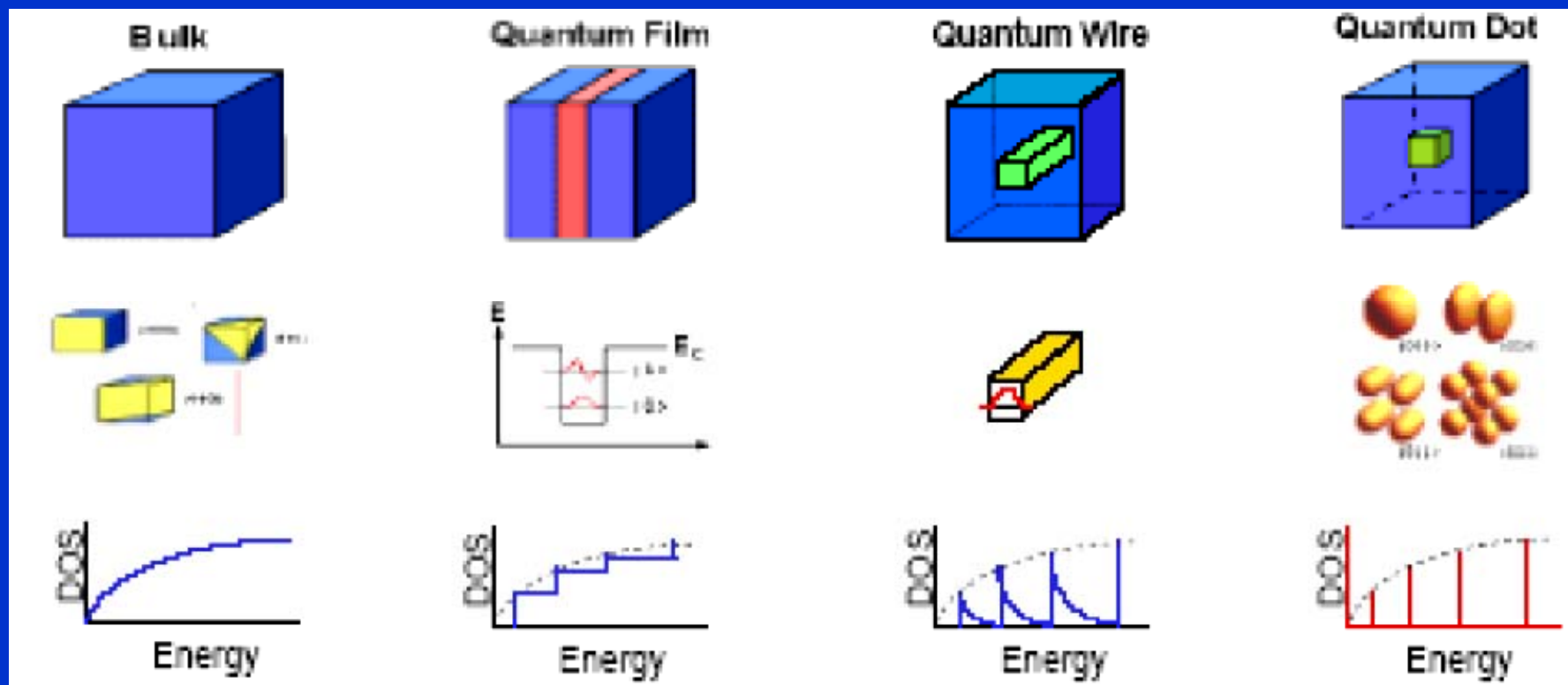


Dispositivos GMR



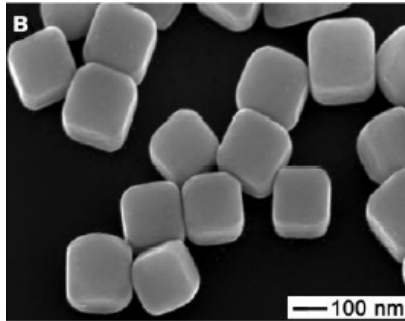
Efectos cuánticos de dimensionalidad

Cambios de los niveles de energía y al densidad electrónica
Cambiando de esta forma también las propiedades eléctricas, electrónicas, fónicas y magnéticas

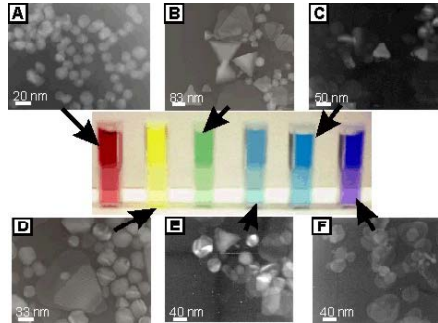


Nanostructures

Noble Metal Nanoparticles

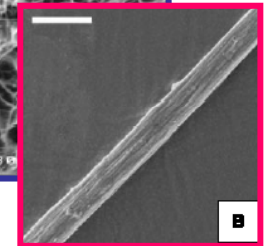
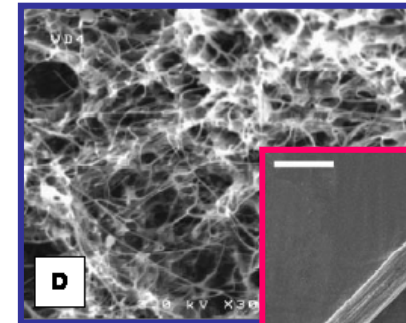
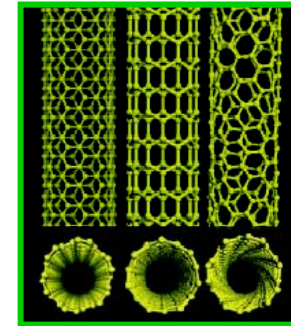


Sun, Y.; Xia, Y. *Science* **2002**, 298, 2176.



Courtesy of the Van Duyne group

Carbon Nanotubes



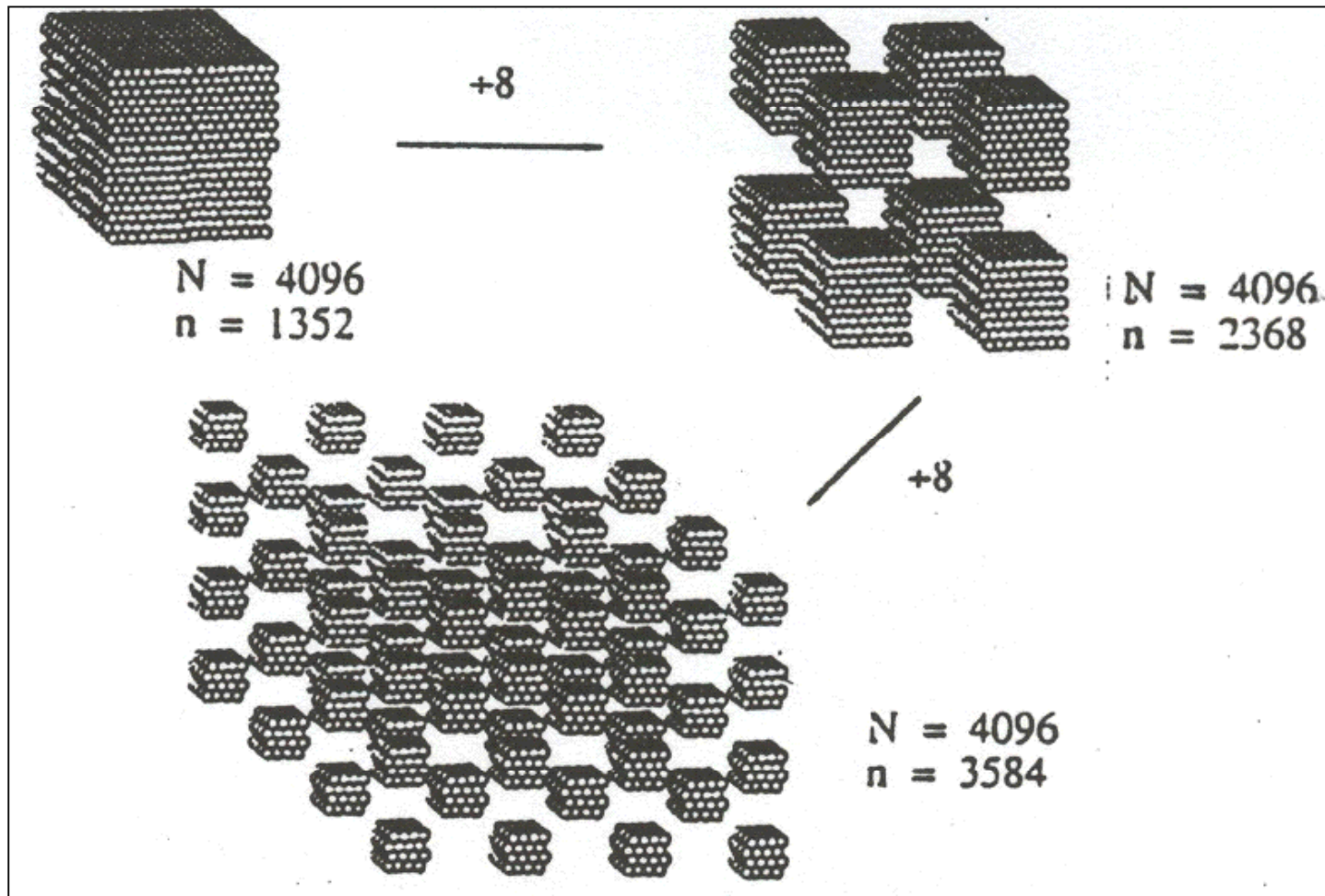
Baughman, R. H.; Zakhidov, A. A.; de Heer, W. A. *Science* **2002**, 297, 787

Vigolo, B.; Penicuaud, A.; Coulon, C.; Sauder, C.; Pailler, R.; Journé, C.; Bernier, P.; Poulin, P. *Science* **2000**, 290, 1331

CdSe Quantum Dots



Courtesy of Liza Babayon



Relación entre átomos en el volumen y sobre la superficie

TAMAÑO DE LA MATERIA

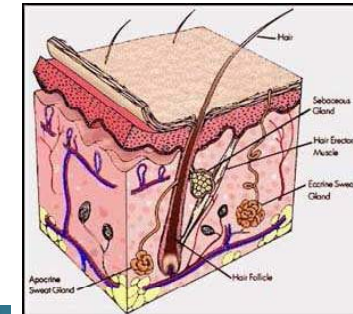
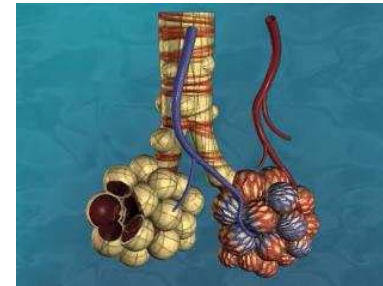
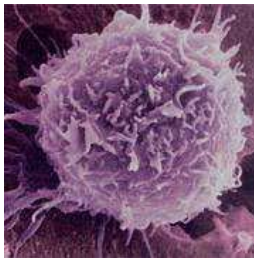
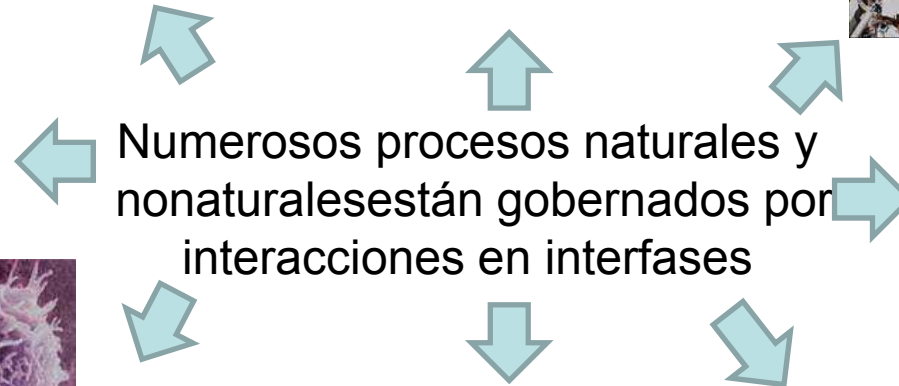
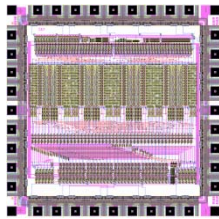
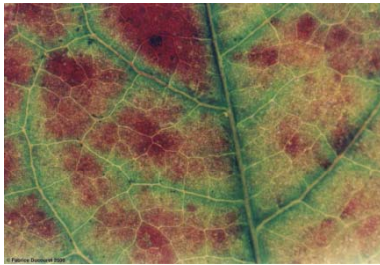
LOS EFECTOS SUPERFICIALES

Cuando la razón superficie / bulk atómico es grande, entonces se presentan efecto en las propiedades mecánicas y químicas

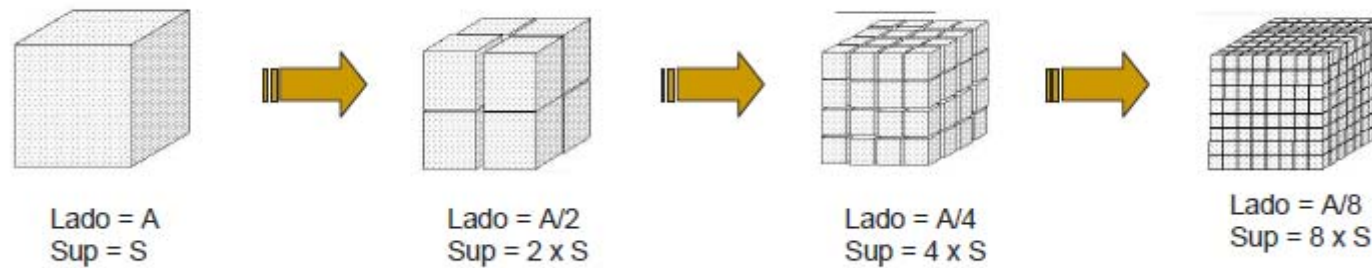
Numero de átomos en el interior y en la superficie en la estructura BBC

Number of unit cells in the cube	Surface (S) atoms	Interior (I) atoms	Ratio (S/I)
1	8	1	8
8 (2x2x2)	26	9	2.9
27 (3x3x3)	56	35	1.6
64 (4x4x4)	98	91	1.1
125 (5x5x5)	152	189	0.8
216 (6x6x6)	218	341	0.6
...			
1,000,000 (100x100x100)	60,002	1,970,299	0.03

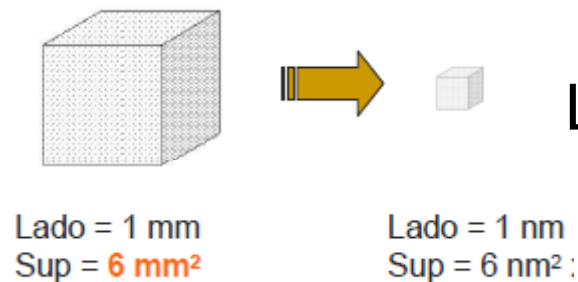
Los sistemas se vinculan a través de su superficie (interfases)



Efecto de la superficie:

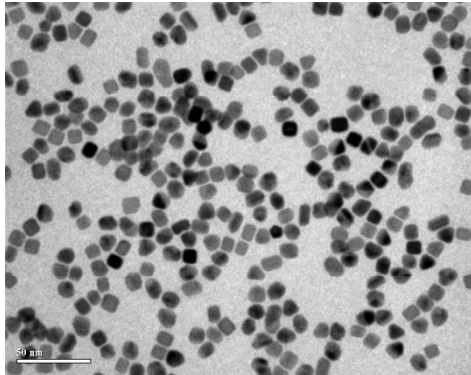


(1 mm = 1.000.000 nm)

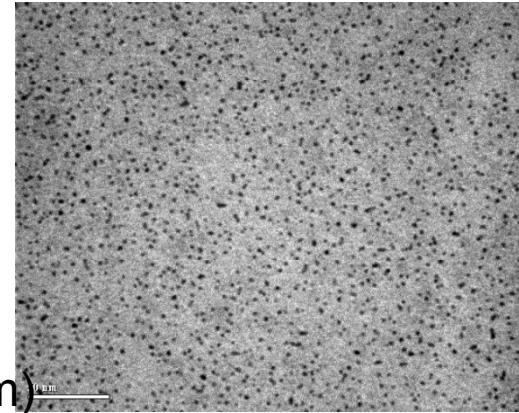


La superficie se amplificó 1 millón de veces

Efecto de la superficie:



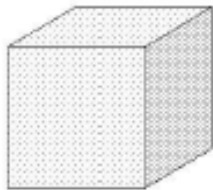
Nanopartículas
cúbicas
de Pt de 9 nm de
arista



Nanopartículas esféricas
de Pt de 2 nm de
diámetro

(1 mm = 1.000.000 nm)

La superficie se amplificó 1 millón de veces

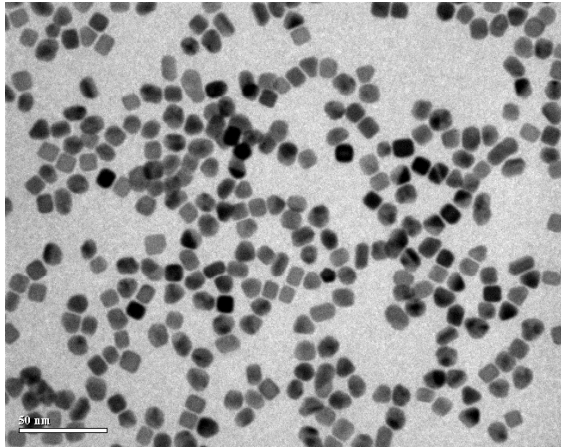


Lado = 1
mm
Sup = 6 mm²



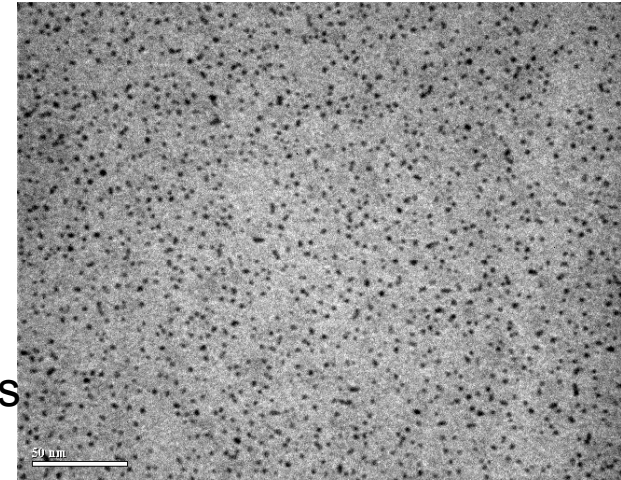
Lado = 1 nm
Sup = 6 nm² x (10⁶ x 10⁶ x 10⁶) = 6 x 10¹⁸
nm² = 6.000.000 mm²

Efecto de la superficie:



Nanopartículas
cúbicas
de Pt de 9 nm de
arista

Nanopartículas esféricas
de Pt de 2 nm de
diámetro



La interacción entre diferentes sistemas (o de un sistema con el medio) se da a través de su superficie.

La nano dimensión amplifica enormemente los efectos de superficie.

NANOPARTICULAS: *LADRILLOS FUNDAMENTALES DE LA NANOTECNOLOGIA*

Influencia del espesor de capa



5 nm Plata

21 nm Oro

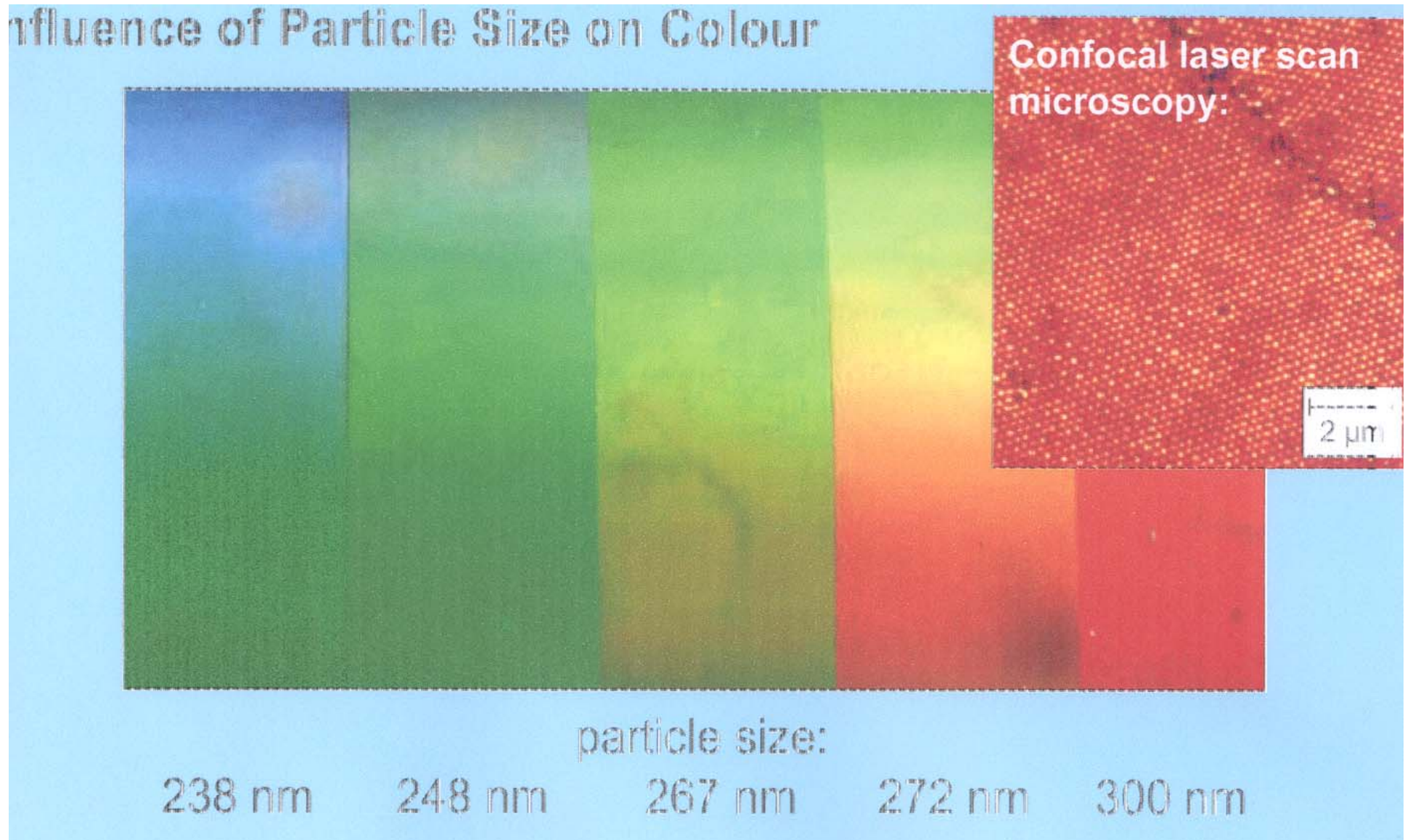
44 nm Violeta

122nm Rojo

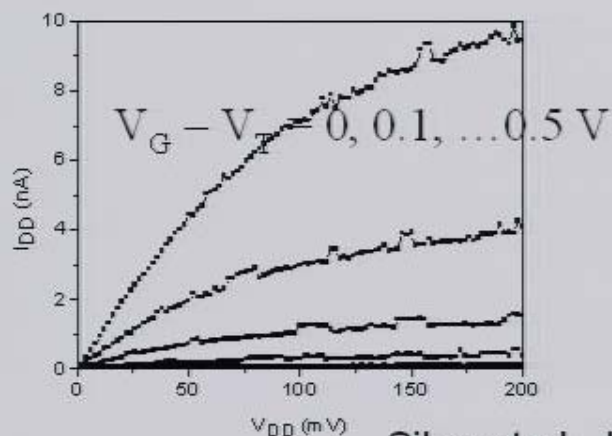
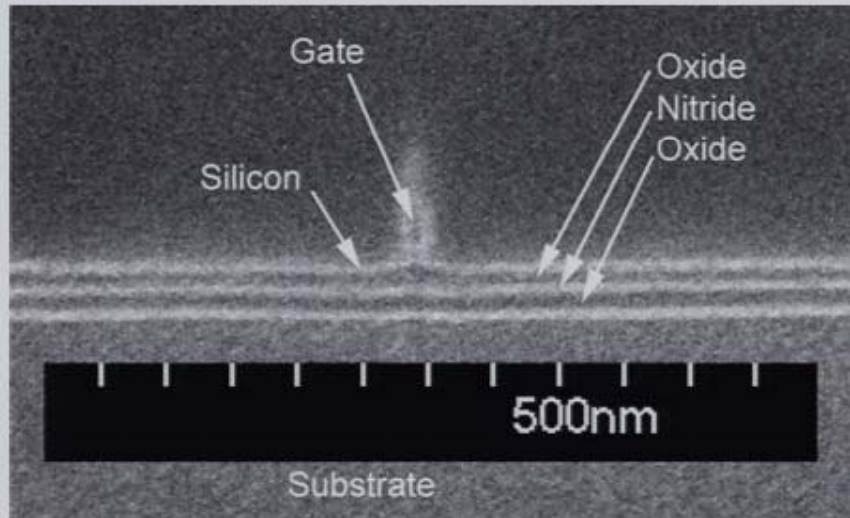
+ brillantes

y opacidad

Influencia del tamaño de partícula en el color

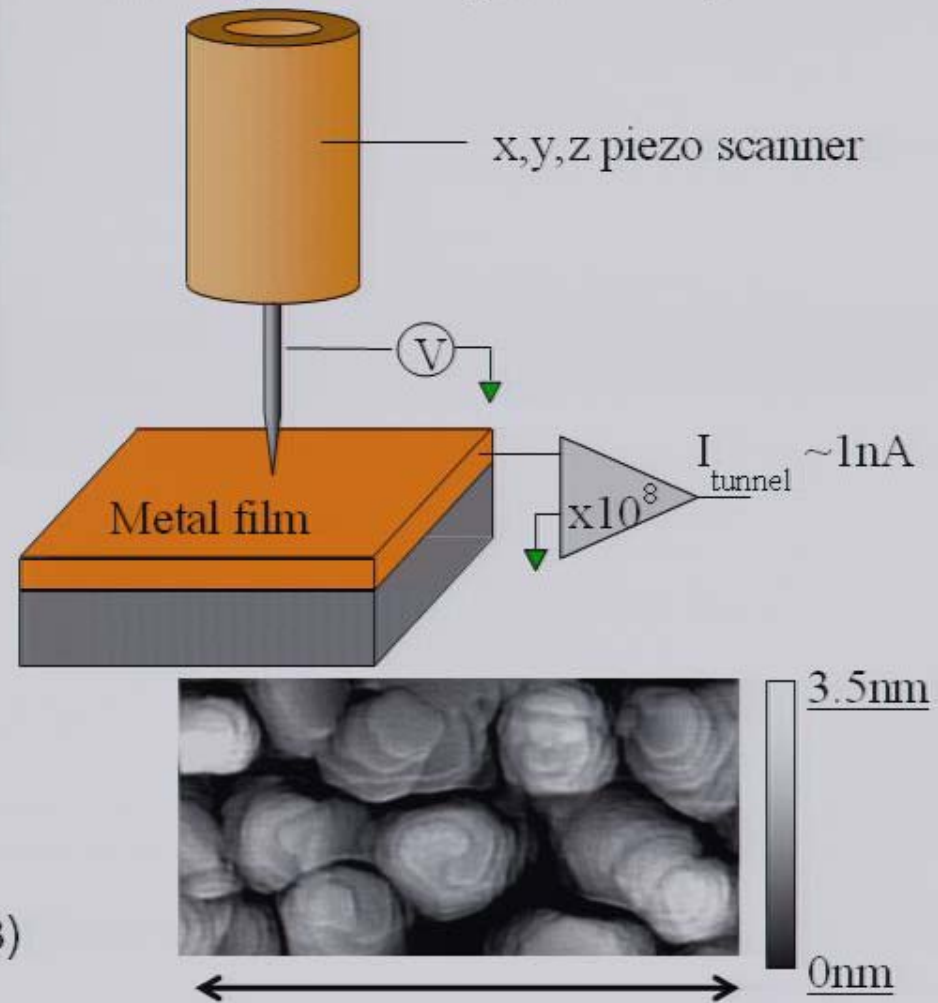


Nanoscale: Quantum Mechanical Effects



Silva et al., IEDM (2003)

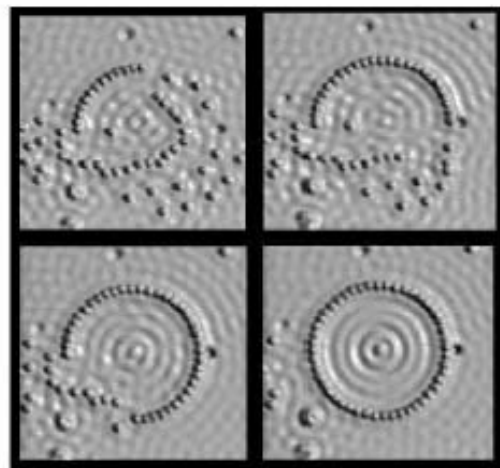
Scanning Tunneling Microscope



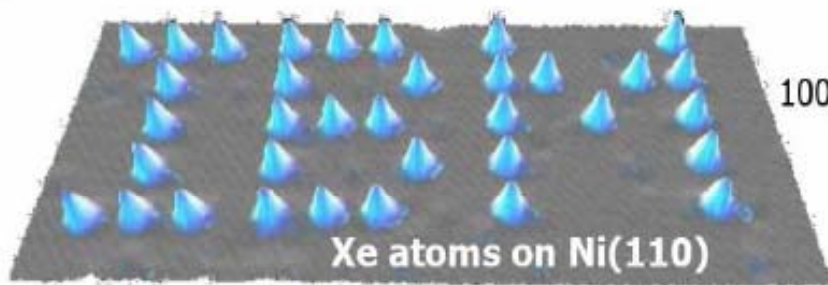
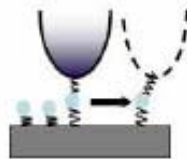
Fowler Nordheim tunneling makes Flash Memories possible
Tunneling makes scanning tunneling microscopes possible

Caracterización por imágenes

Manipulando átomos con STM

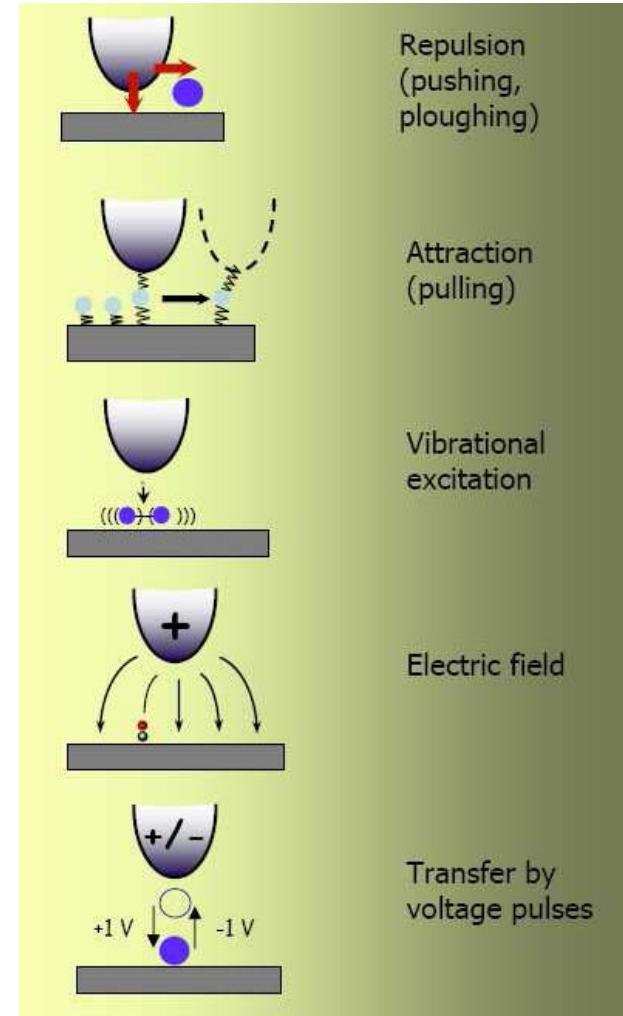


Building of a quantum
"corral" with Fe atoms on Cu



100,000 Gbit/sq.in

STM images courtesy of Don Eigler, IBM, San Jose



Repulsion
(pushing,
ploughing)

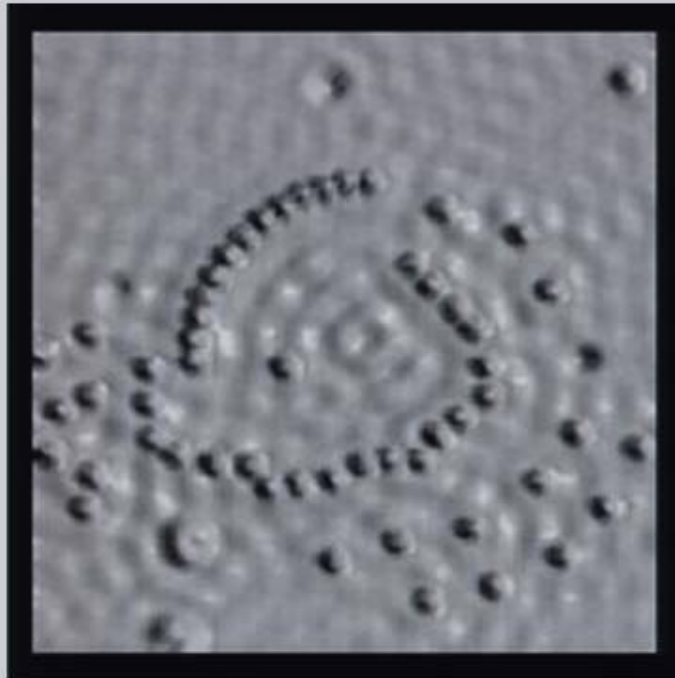
Attraction
(pulling)

Vibrational
excitation

Electric field

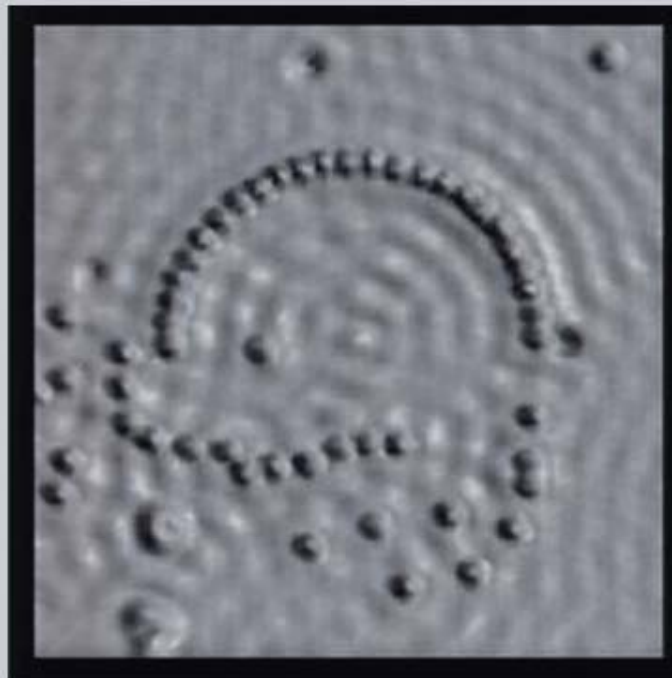
Transfer by
voltage pulses

Atom by Atom



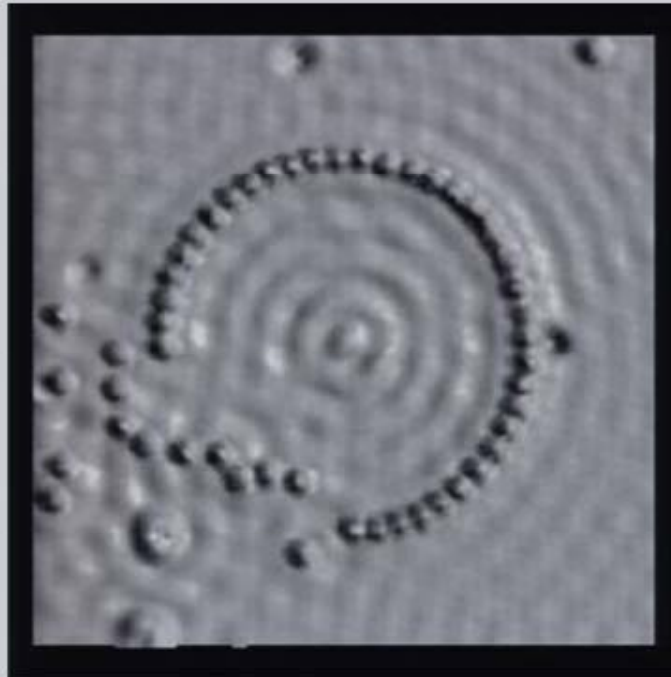
D. Eigler, IBM Almaden

Atom by Atom



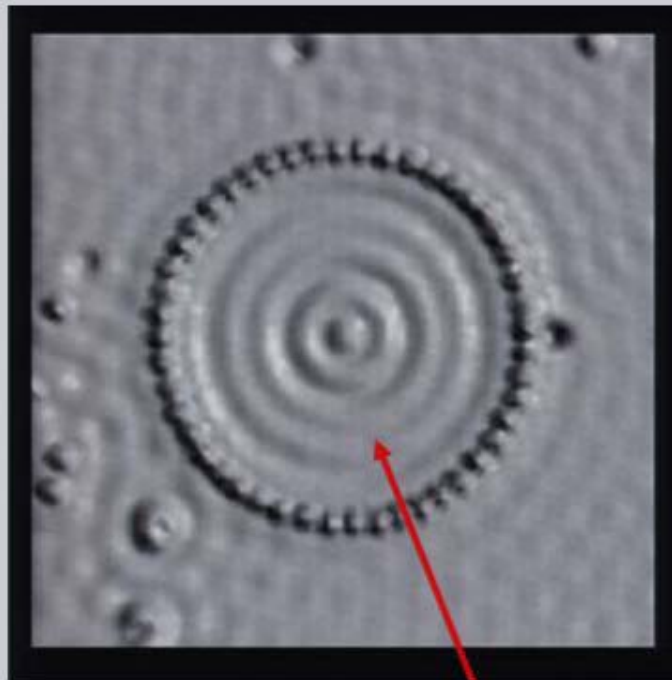
D. Eigler, IBM Almaden

Atom by Atom



D. Eigler, IBM Almaden

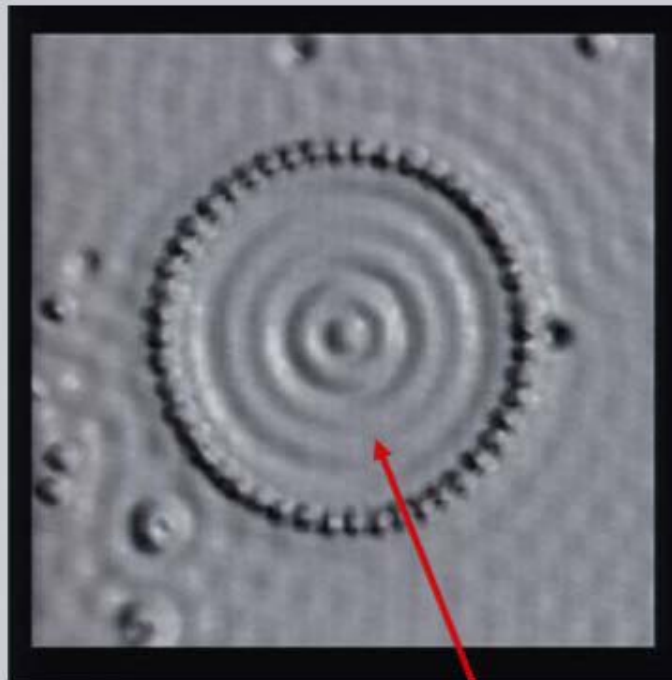
Atom by Atom



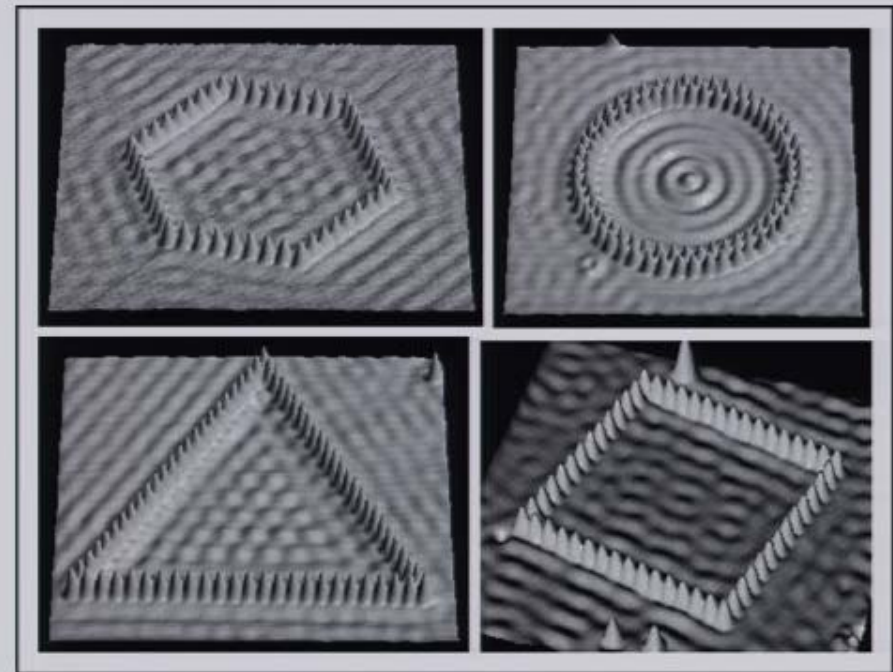
note waves

D. Eigler, IBM Almaden

Atom by Atom

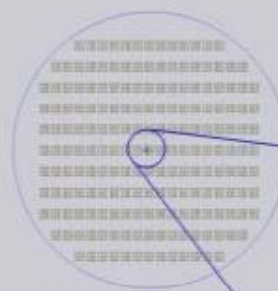


note waves

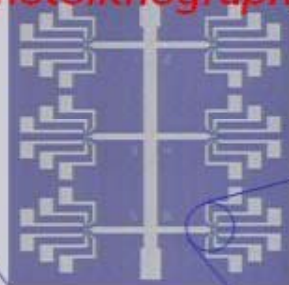


D. Eigler, IBM Almaden

Creating Single-Molecule Transistors



Gate areas and bonding contacts are defined via **photolithography**.



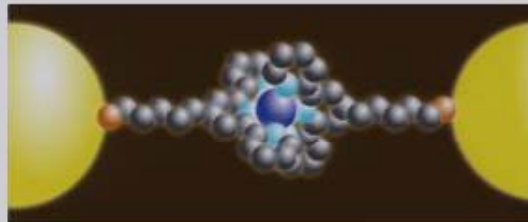
Nanowires are generated by **electron-beam lithography**.



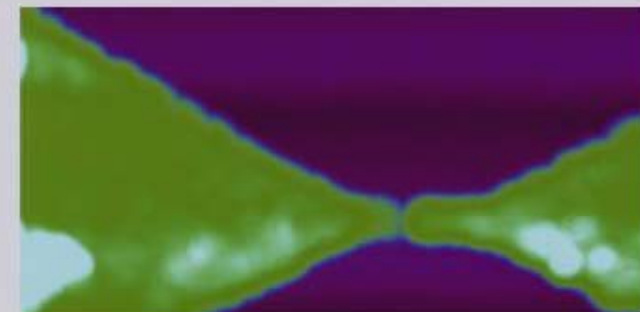
Deposit molecules on electrodes



Pass large currents: electromigration – Induced Gap formation.

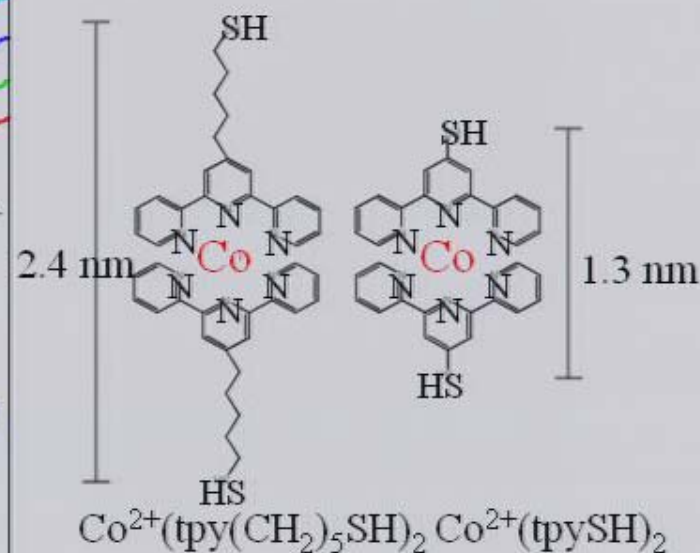
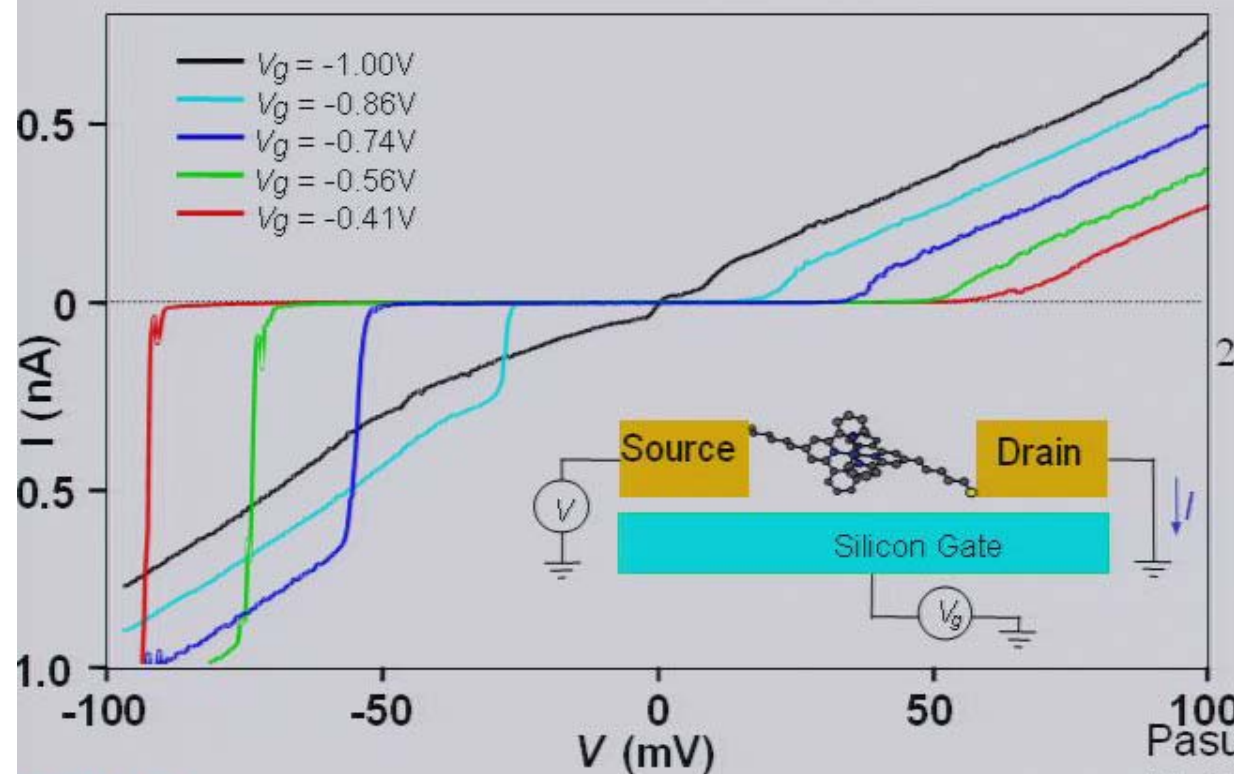


— 200 nm



Transistor Action

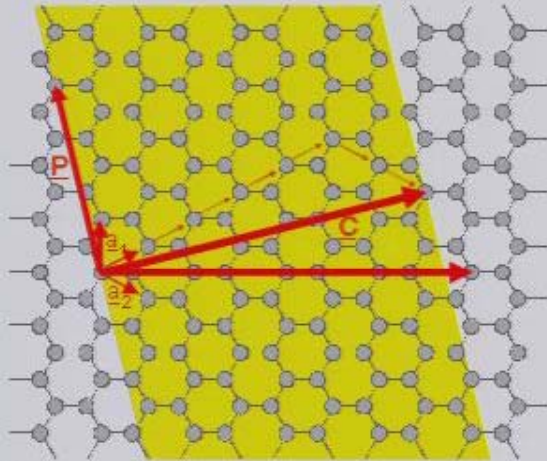
- Longer molecules: larger resistance
- Single molecule works as a single-electron transistor (though at low temperatures and no gain)



Pasupathy, Park, Goldsmith, Abruña, McEuen, Sethna, Ralph, Nature (2002)

2005 CNF TCN: Nanotechnology, page 12

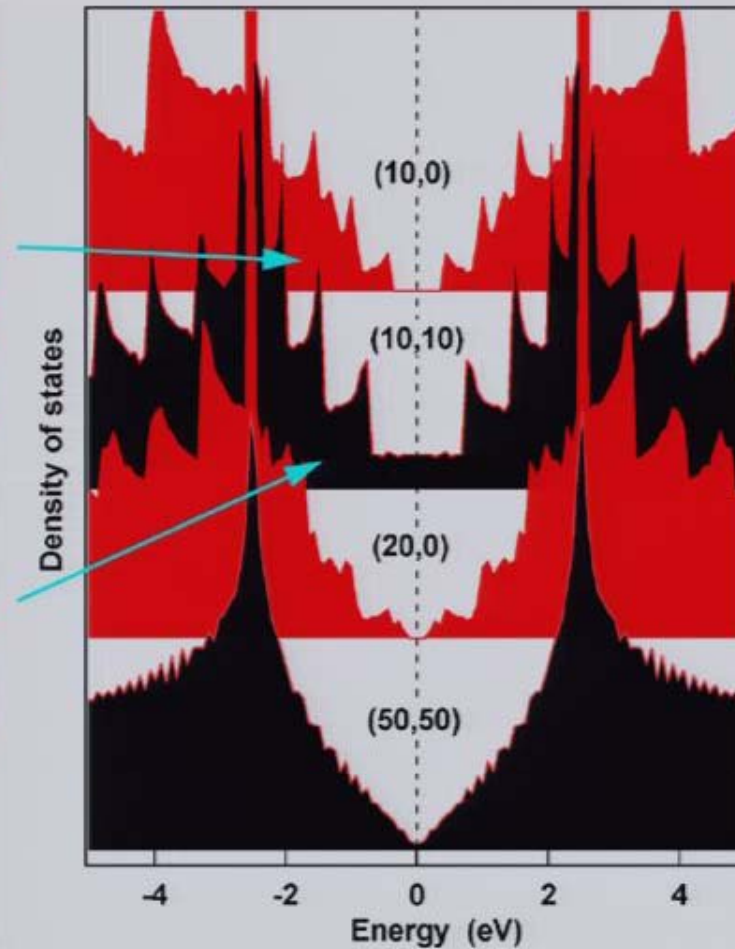
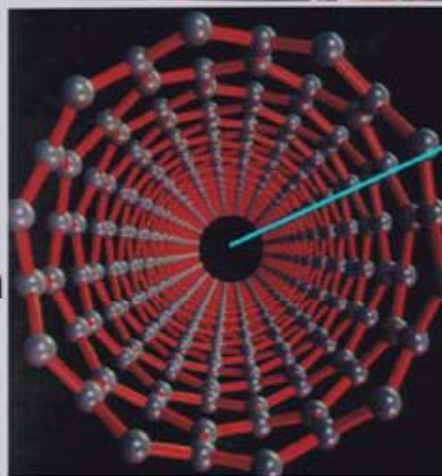
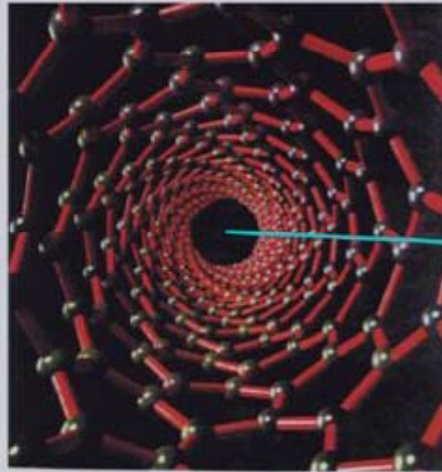
Carbon Nanotubes



A nanotube (n,m) is a folded graphite sheet. Single wall tubes are 1 nm diameter

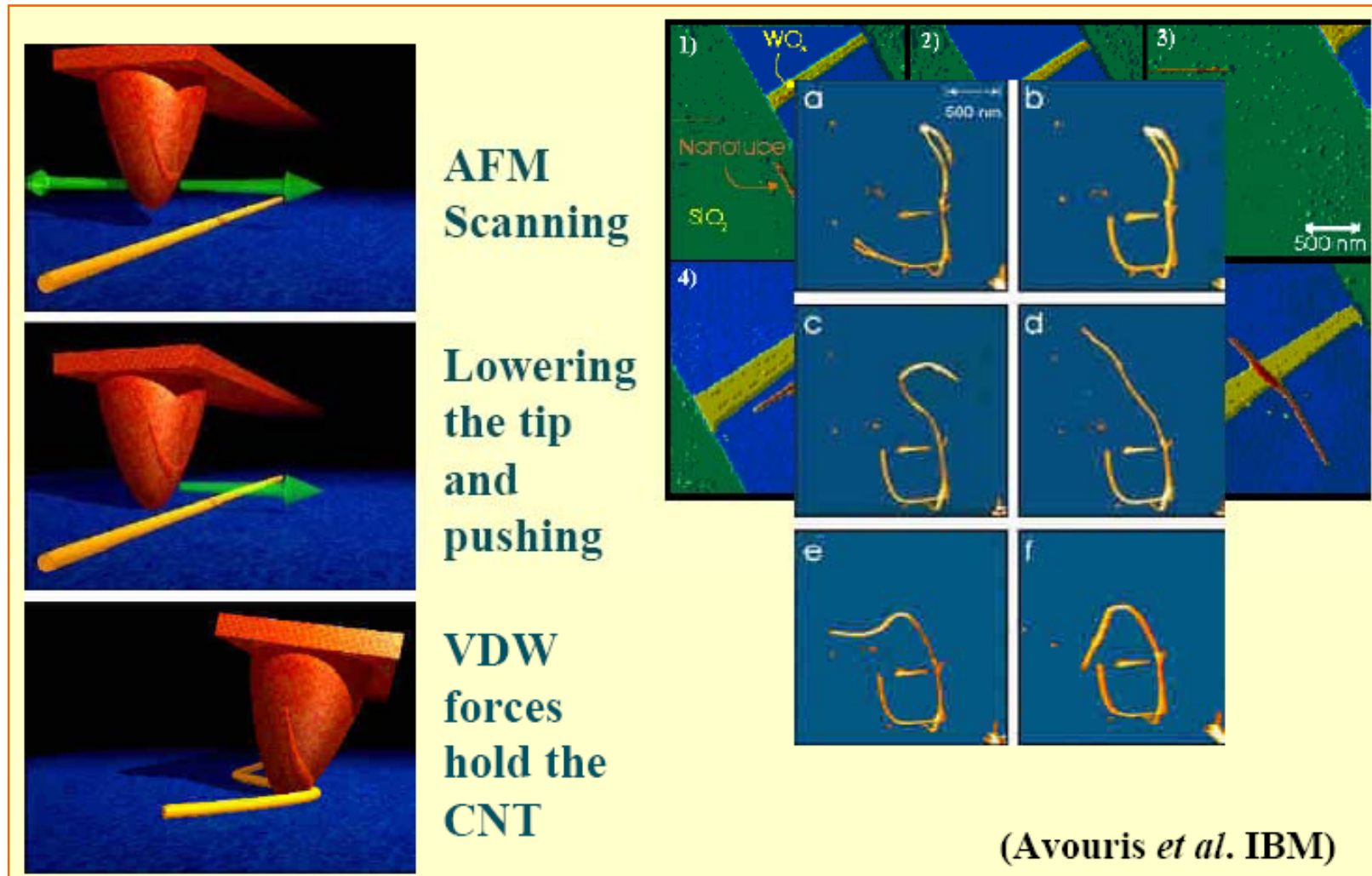
	Young's Modulus (GPa)	Tensile Strength (GPa)
SWNT	1054	150
Steel	208	0.4

Peak Thermal Conductivity: 4×10^4 W/m.K

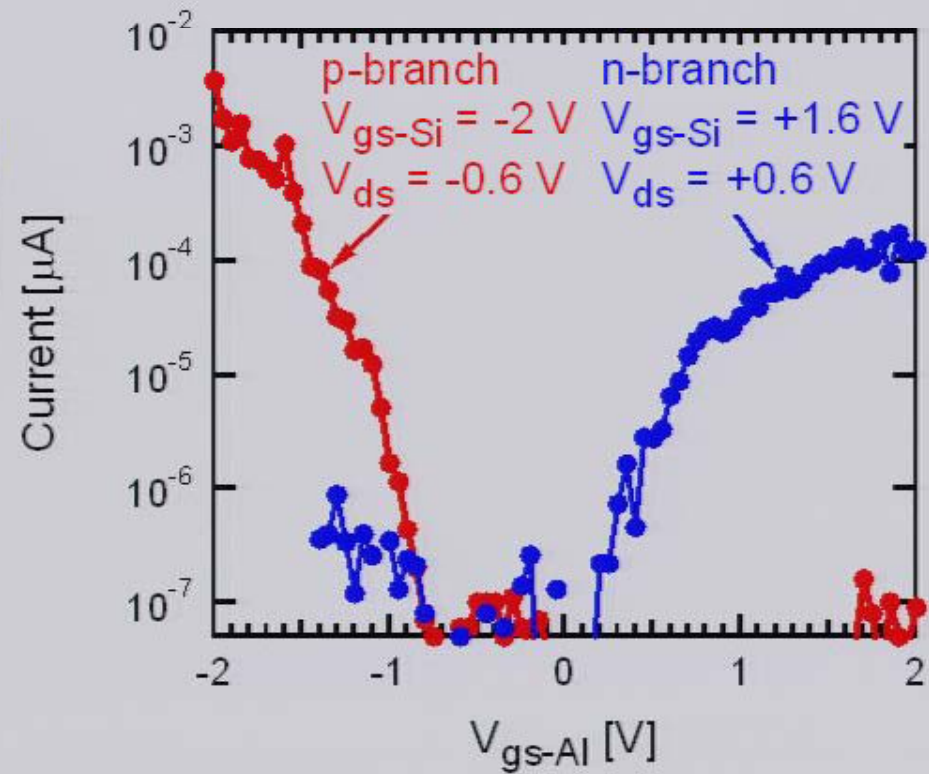
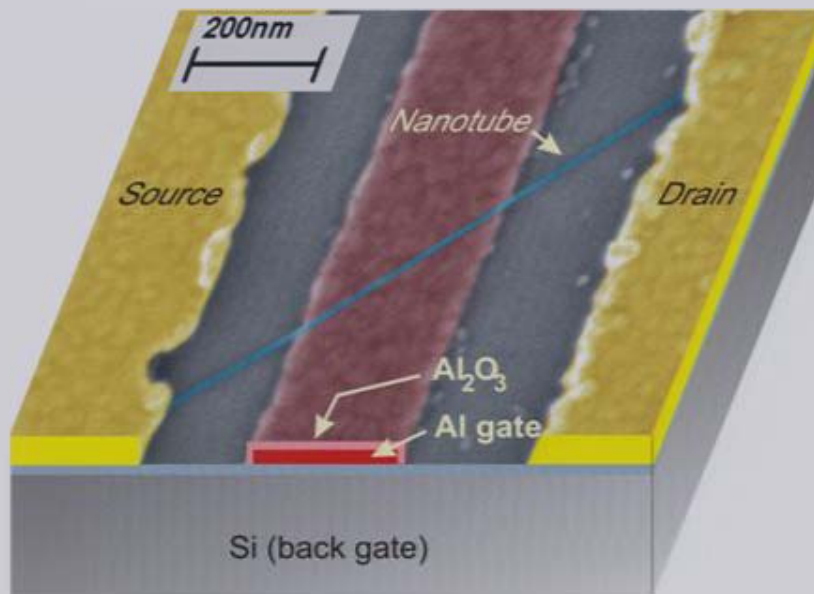


Semiconducting to metallic

Carbon Nanotube Manipulation

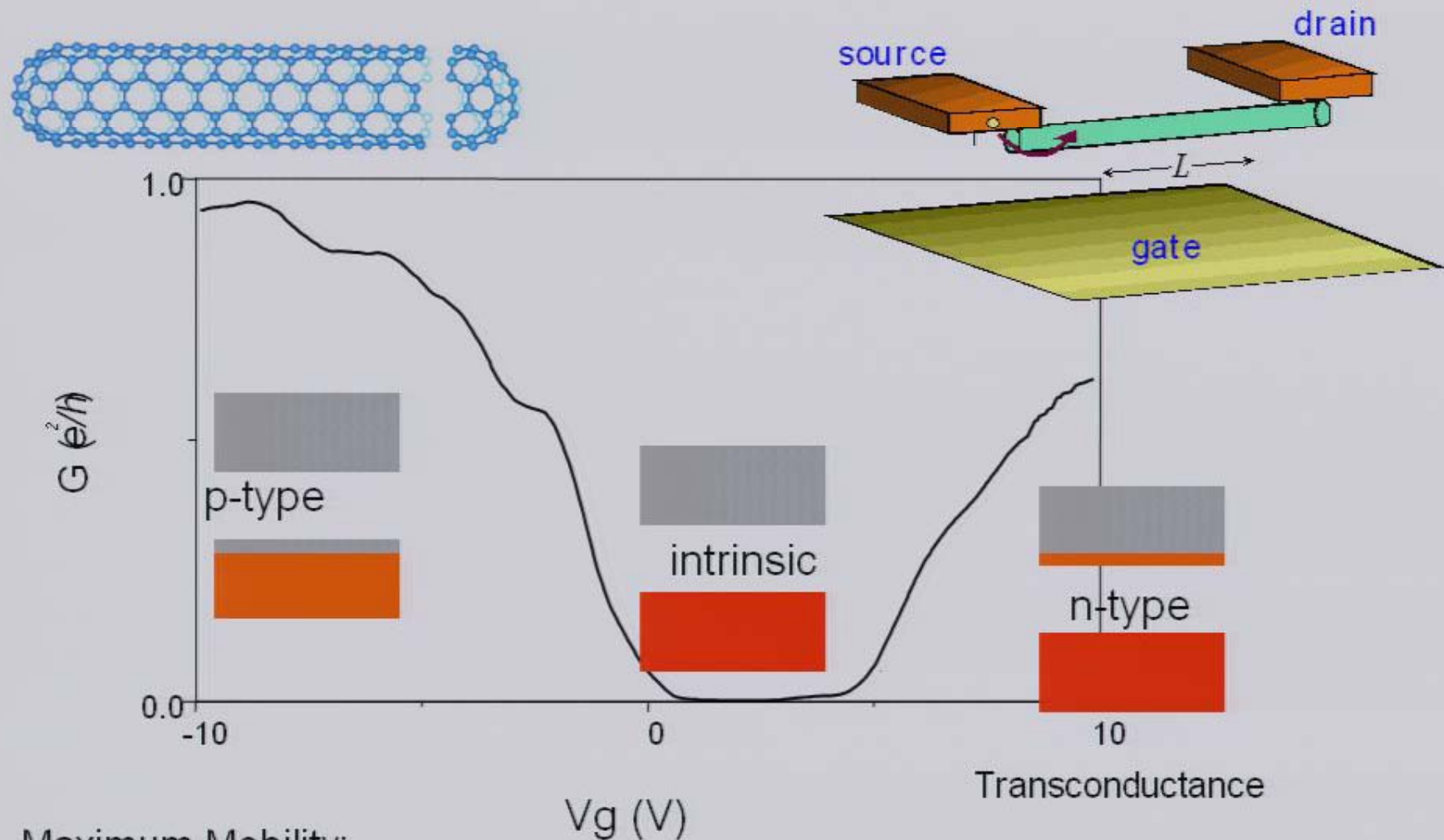


Carbon Nanotube Transistors



Y. M. Lin et al. (2005)

Ultimate Mobility of SWNT transistors

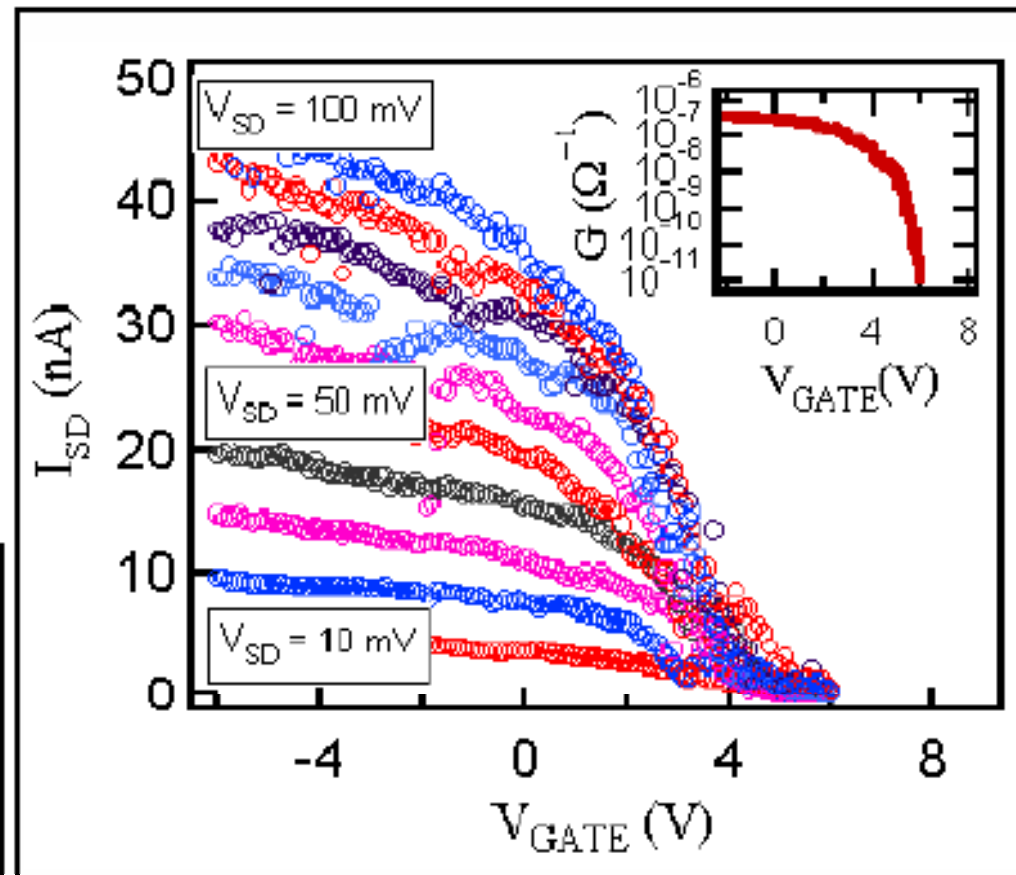
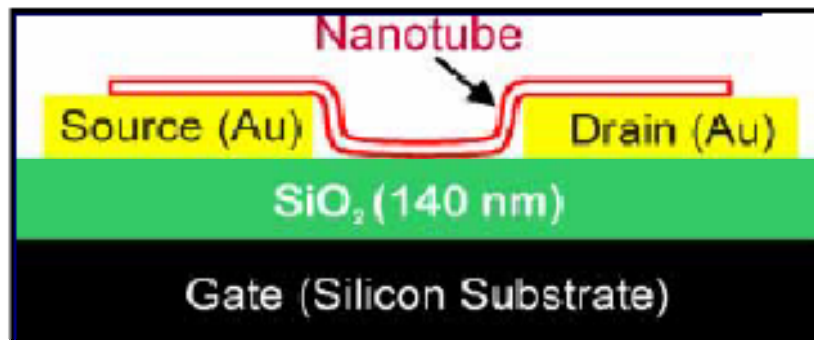
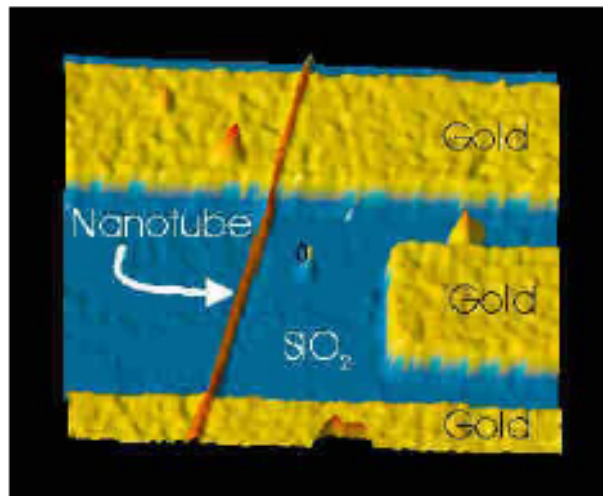


Maximum Mobility:
 $\mu = 10,000 - 20,000 \text{ cm}^2/\text{V-s}$

Limited by electron-
phonon scattering

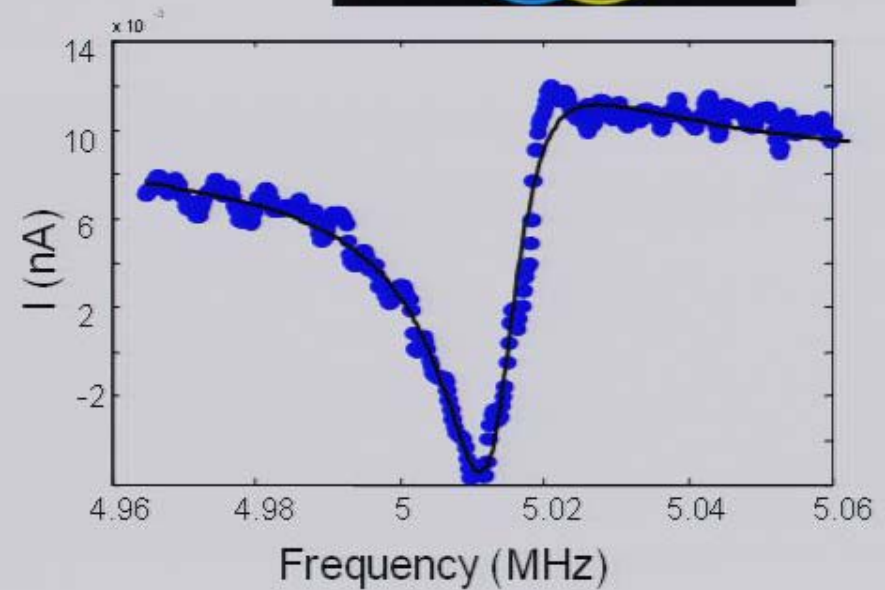
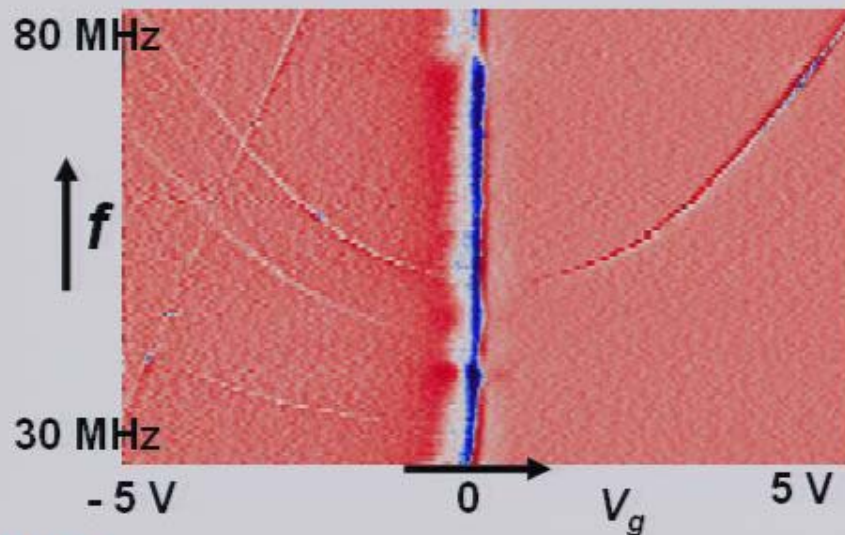
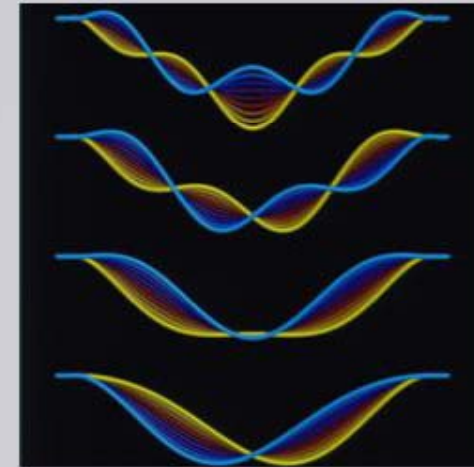
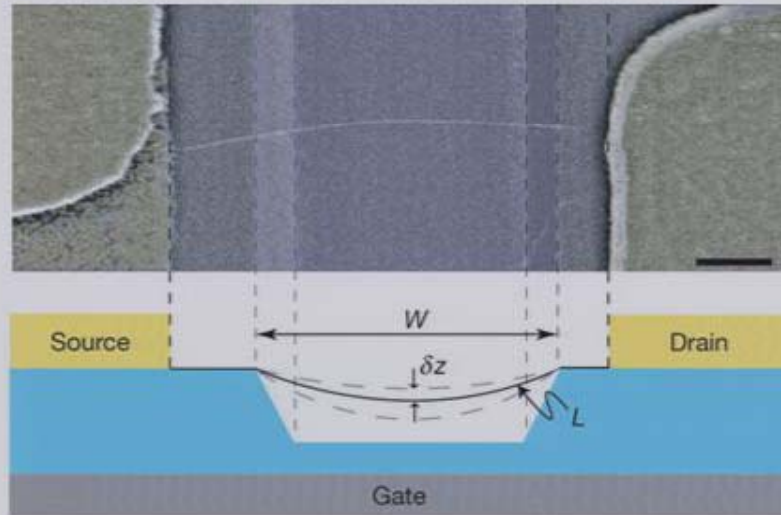
Zhao et al.,
unpublished

A Field-Effect Transistor Made from a Single-Wall Carbon Nanotube



(Avouriset al. IBM)

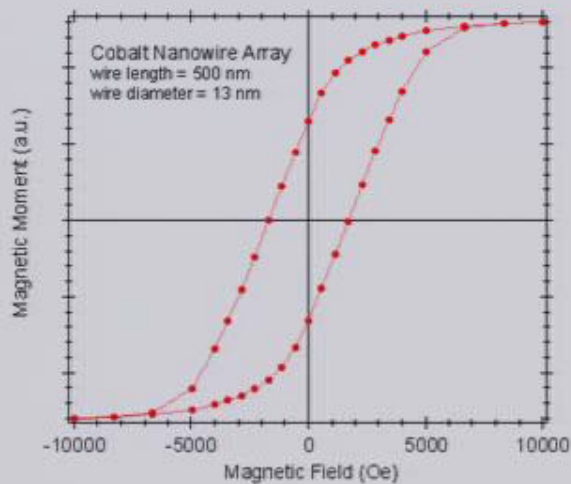
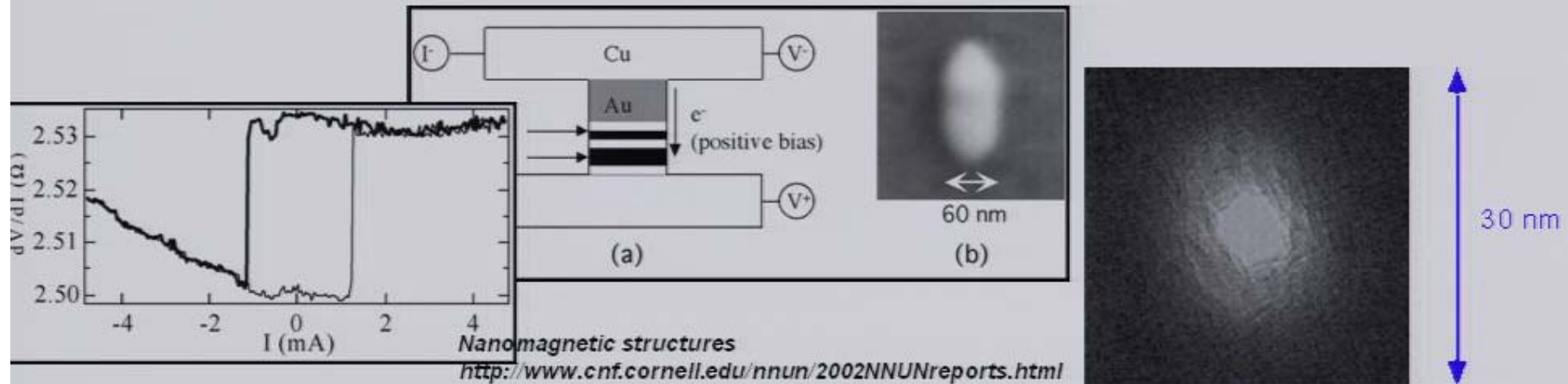
Nanotube Mechanical Oscillator



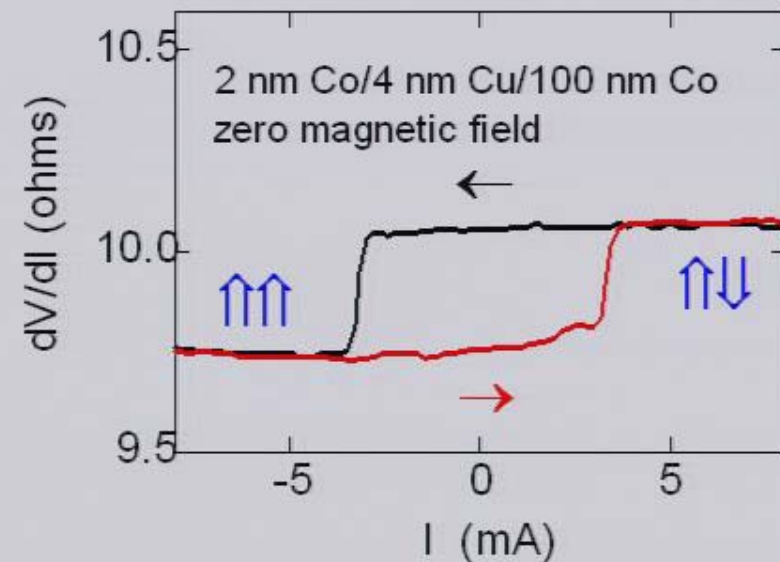
McEuen group, Nature (2004)

2005 CNF TCN: Nanotechnology, page 24

Nano-Magnetics



A. Ursache, et al., Proc. Mat. Res. Soc (2002)

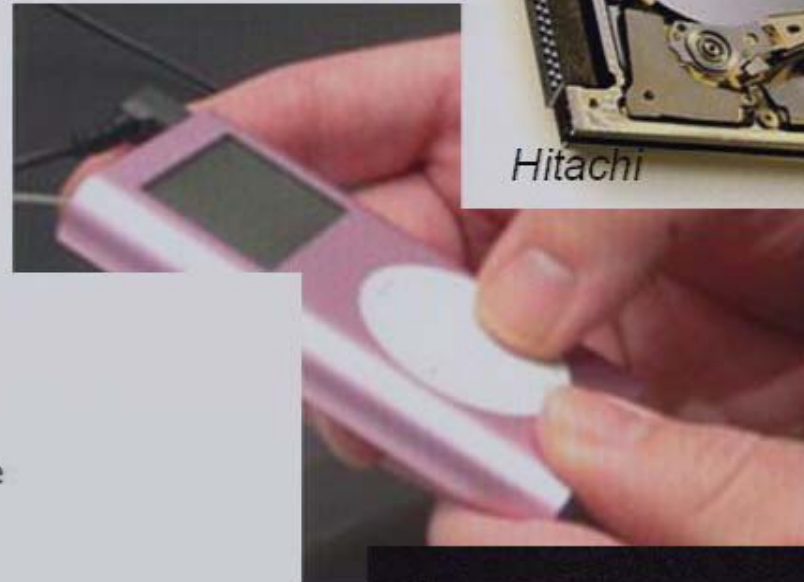
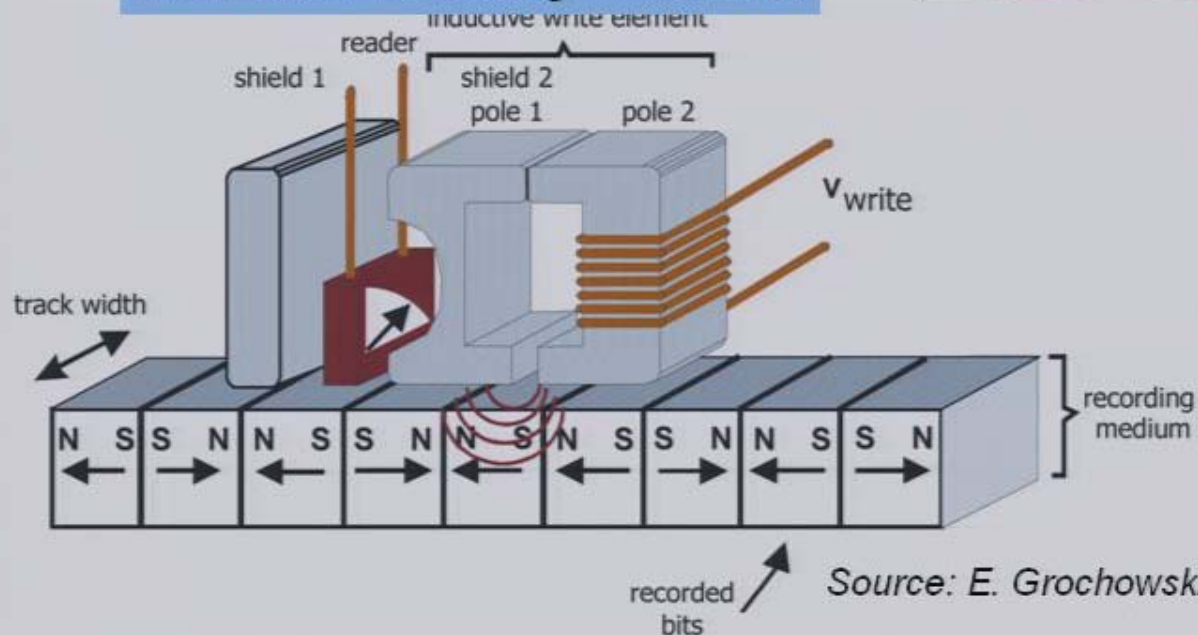


Ralph, Buhrman et al. (1999)
 2005 CNF TCN: Nanotechnology, page 18

Hard Drives

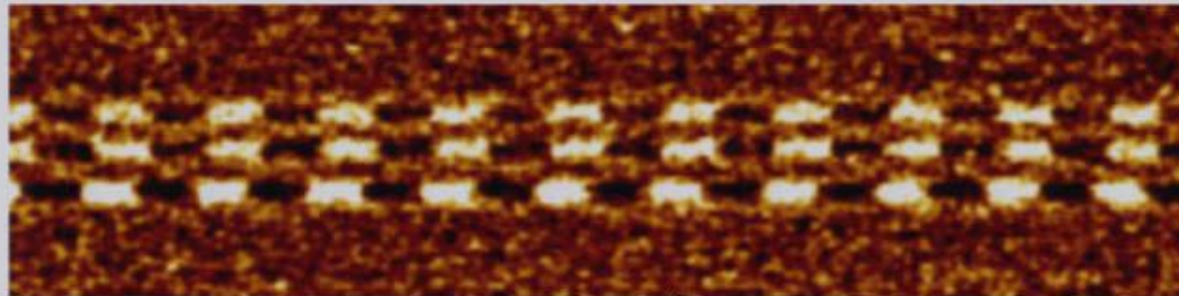
Hitachi (4 GB, 1 inch micro-drive) in iPod
Toshiba (4 GB, 0.85 inch micro-drive)

Ultra-sensitive read/write head
Small are magnetic storage
Horizontal recording -> Vertical

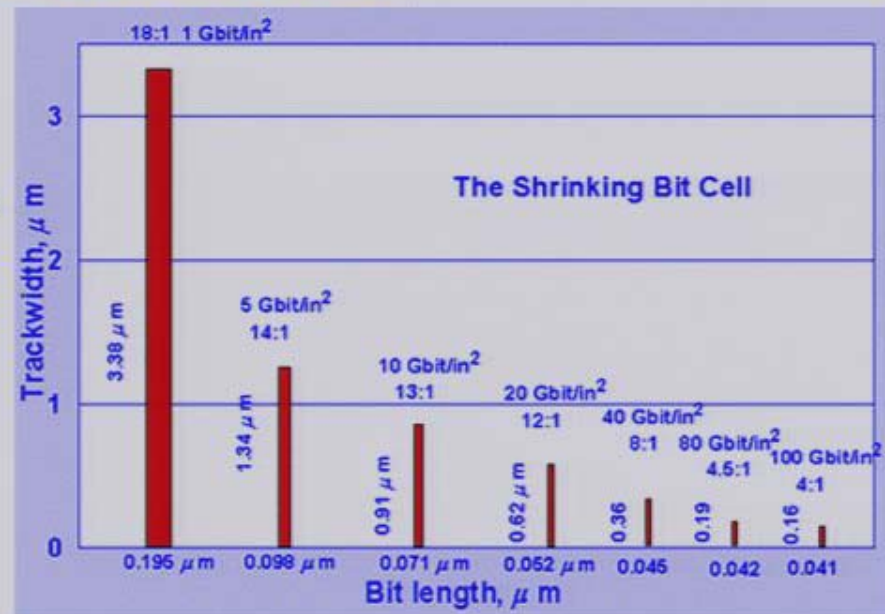
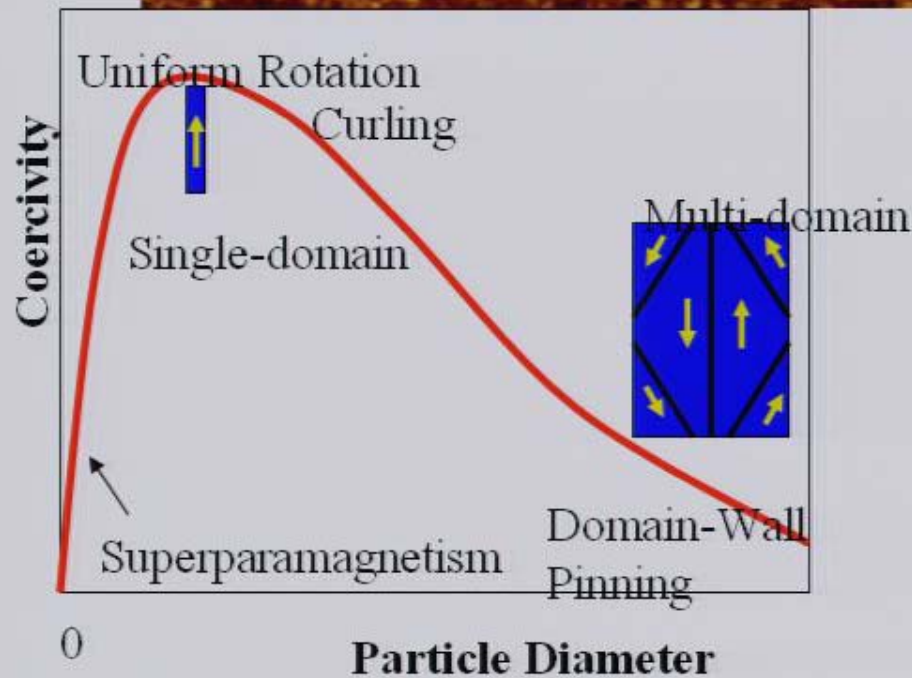


Toshiba

Magnetic Storage (Hard Disks)



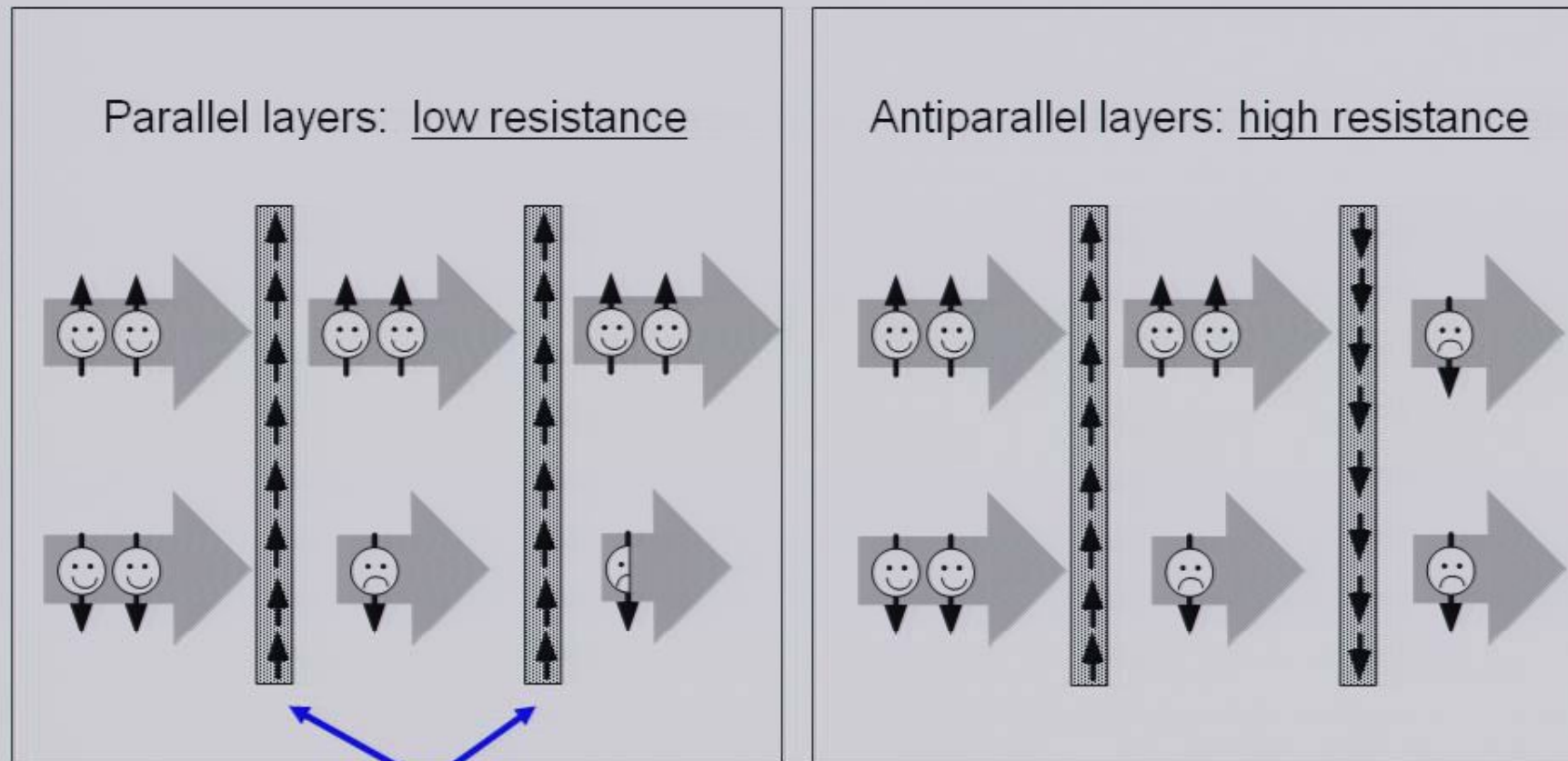
400 nm



Tuominen, Khizroev, etc.

“Spintronics”, or Nano-Magnetics

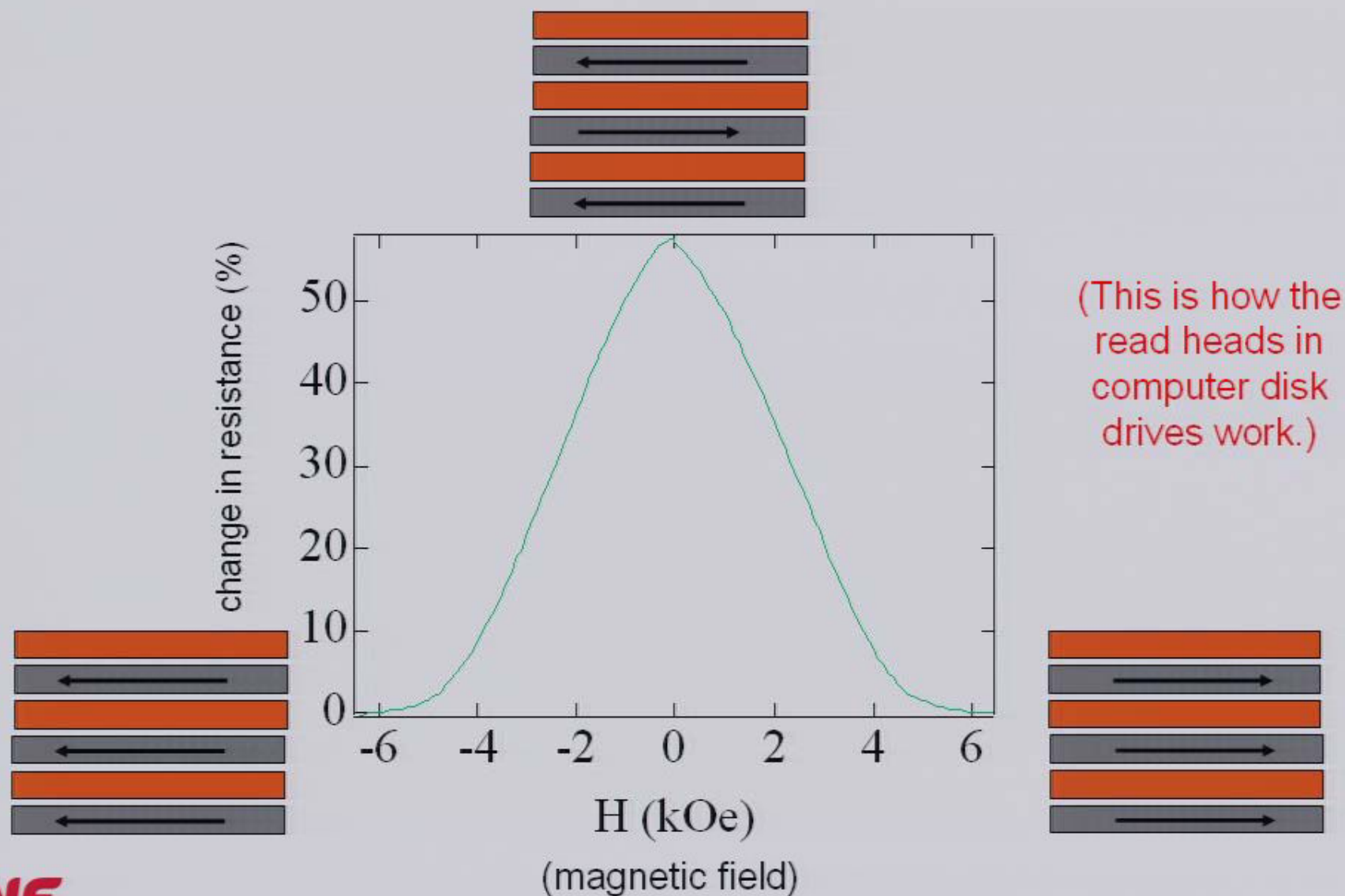
- Can get “giant” changes in resistance because magnetic layers filter spins.



Magnetic layers

Maximum spacing over which
the spins are not randomized ~ 50 nm

These Resistance Changes Allow Magnetic-Field Sensing



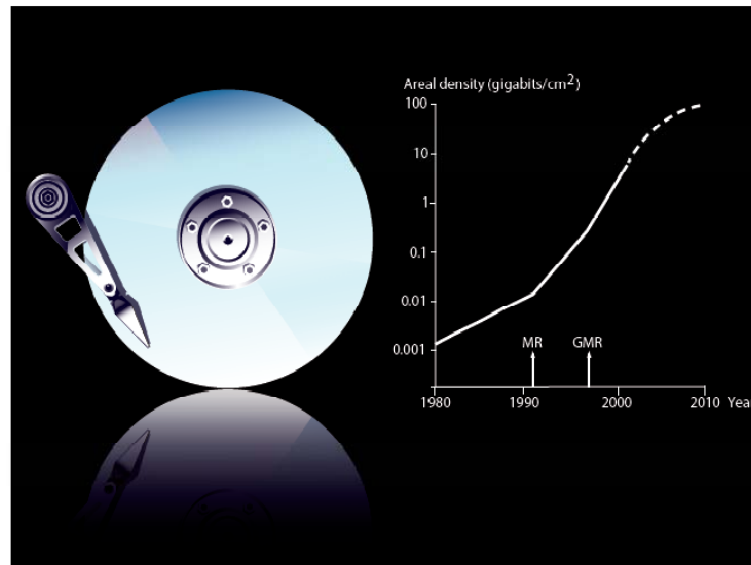
The Nobel Prize in Physics 2007

The discovery of Giant magnetoresistance

*This year's Nobel Prize in Physics is awarded to **ALBERT FERT** and **PETER GRÜNBERG** for their discovery of Giant Magnetoresistance. Applications of this phenomenon have revolutionized techniques for retrieving data from hard disks. The discovery also plays a major role in various magnetic sensors as well as for the development of a new generation of electronics. The use of Giant Magnetoresistance can be regarded as one of the first major applications of nanotechnology.*



Albert Fert
Unité Mixte de Physique
CNRS/THALES,
Université Paris-Sud,
Orsay, France,

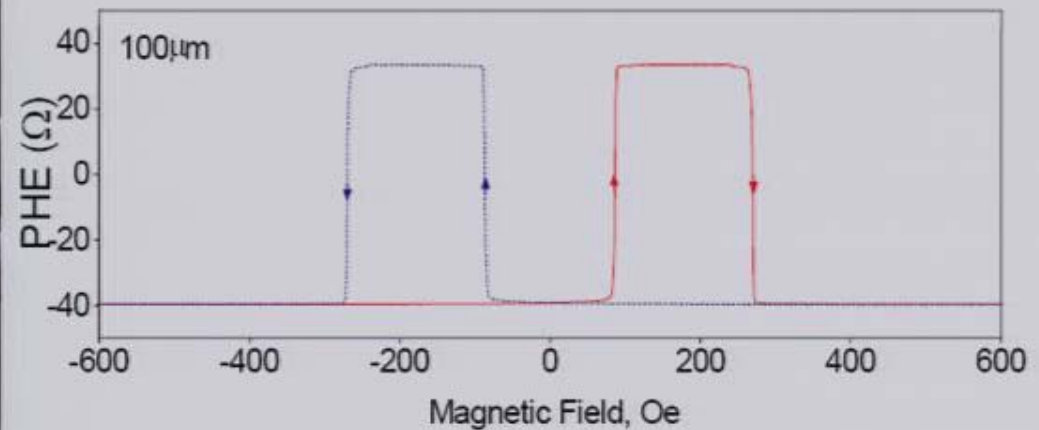
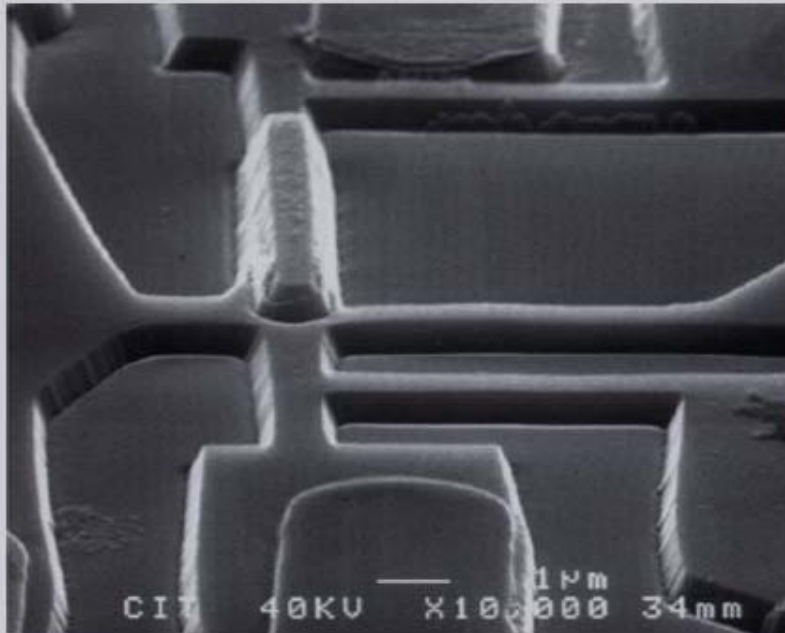


Diagrams showing the accelerating pace of miniaturization might give a false impression of simplicity – as if this development followed a law of nature. In actual fact, the ongoing IT-revolution depends on an intricate interplay between fundamental scientific progress and technical fine tuning. This is just what the Nobel Prize in Physics for the year 2007 is about.



Peter Grünberg
Forschungszentrum
Jülich, Germany,

Spintronics

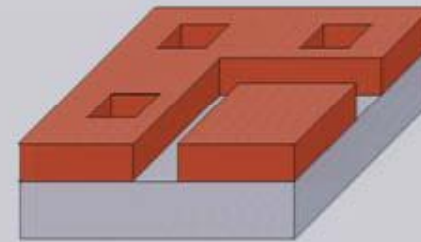
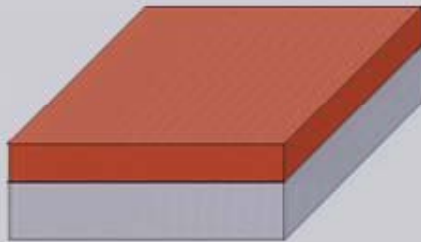


Awschalom et al., PRL (2003)

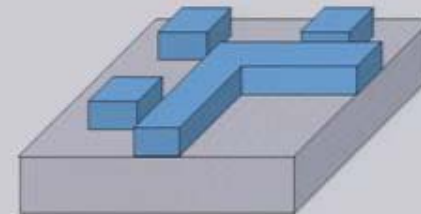
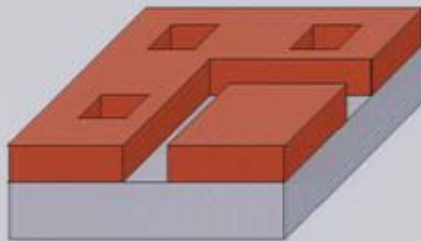
- Large spontaneous Hall effect in GeMnAs film that is 4 orders of magnitude larger than ferromagnetic films.
- Voltage control of domain walls

Top-Down

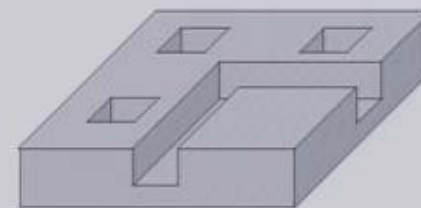
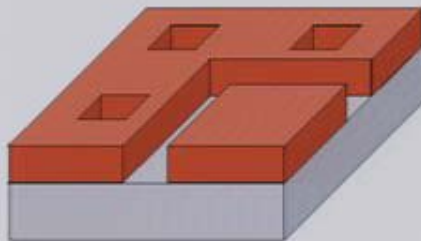
Lithography



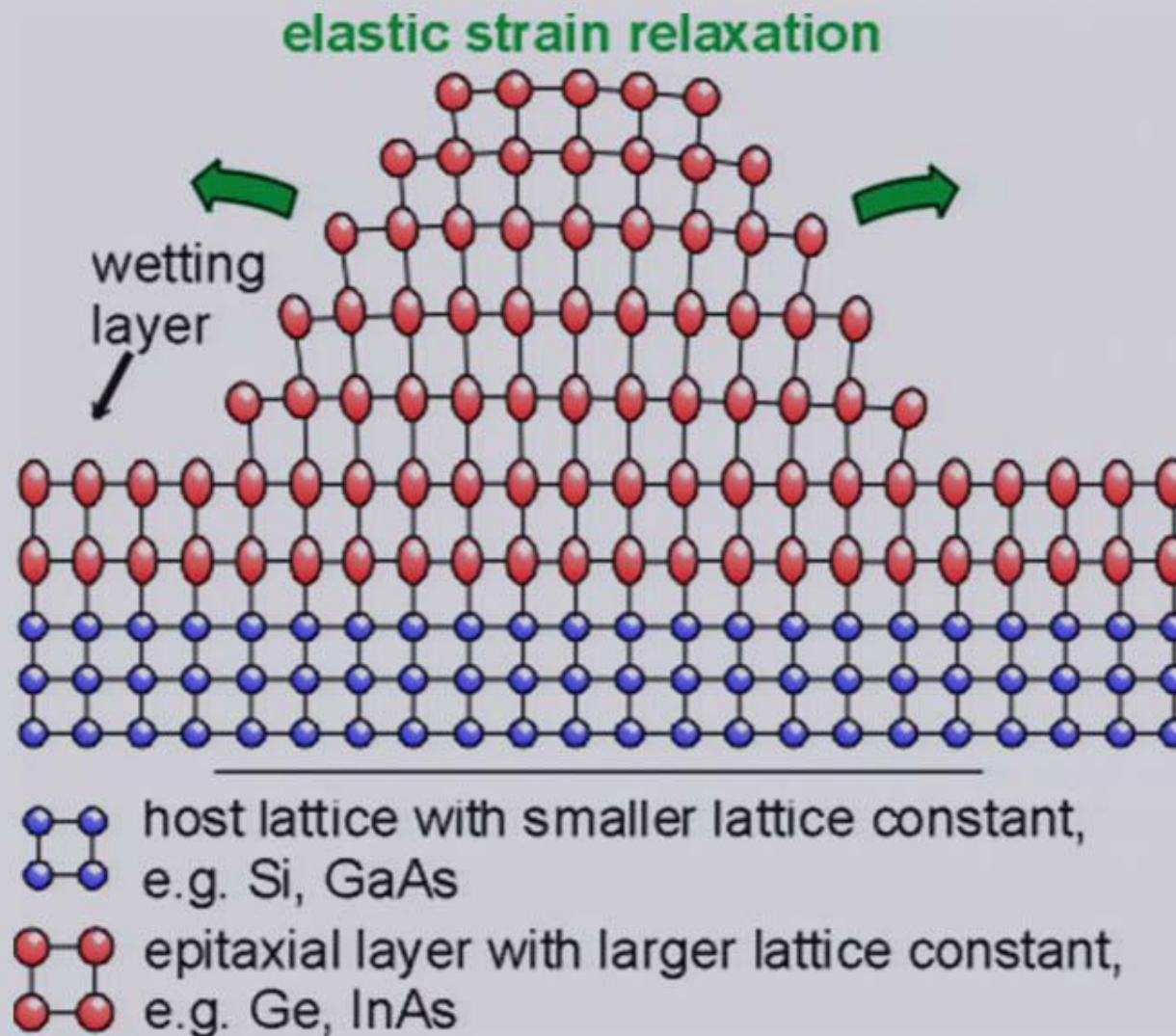
Deposition



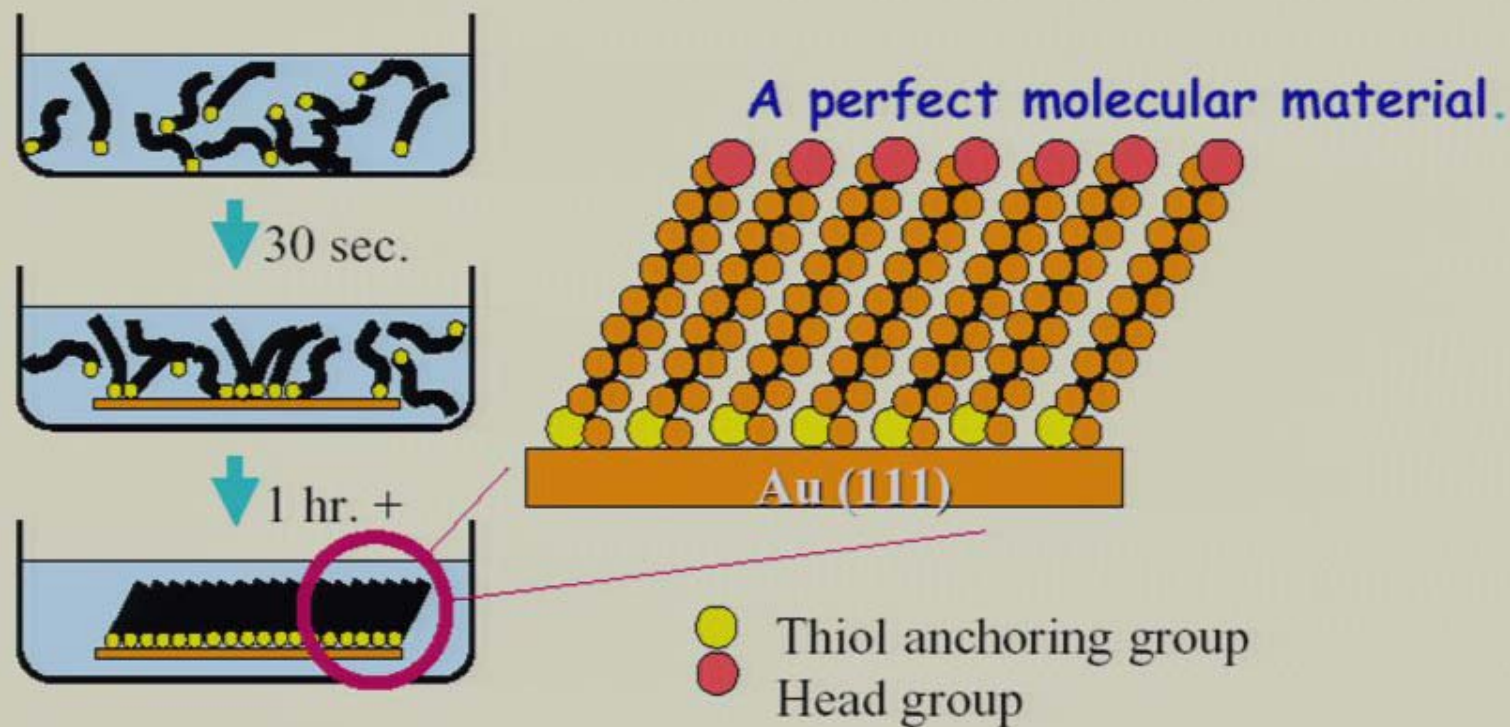
Etching



Bottom-Up: Growth as Self Assembly



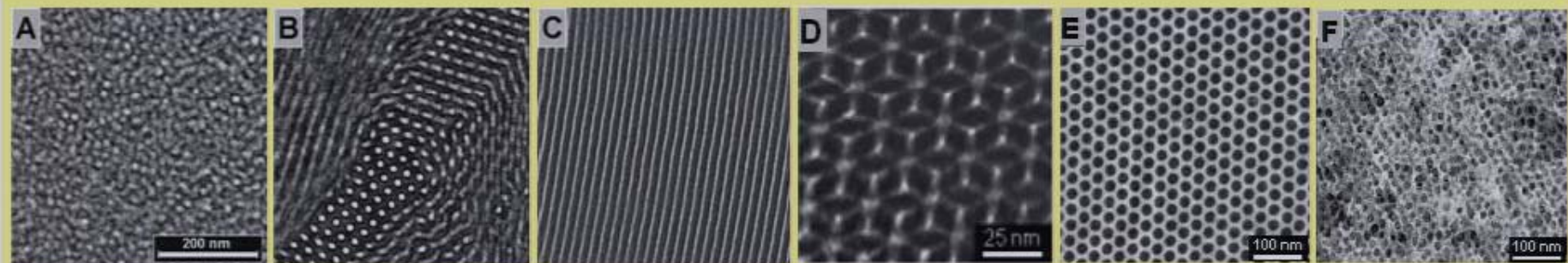
Self-Assembled Monolayers



Major discovery -- 1983

Nuzzo, RG; Allara, DL (1983): Adsorption of bifunctional organic disulfides on gold surfaces. J. Am. Chem. Soc. 105(13), 4481-4483.

Self-Assembly



TEM



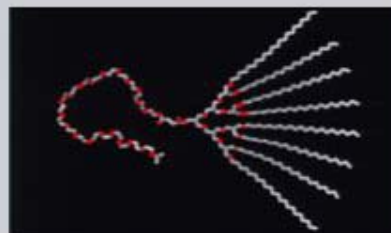
Science 278, 1795 (1997)

2005 CNF TCN: Nanotechnology, page 41

Utilizing Building Blocks



block copolymers

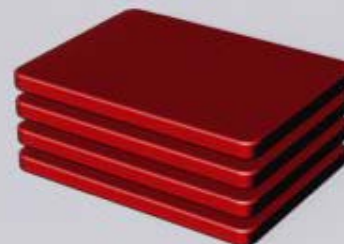
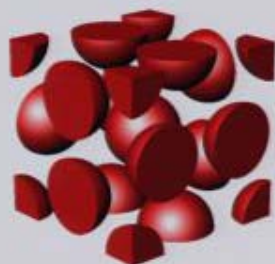
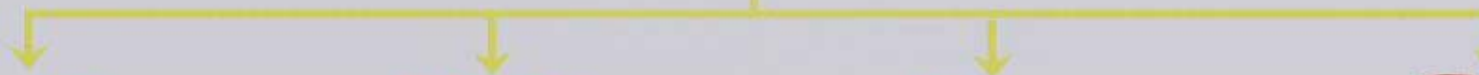


extended amphiphilic dendrons

"Morphology Control"



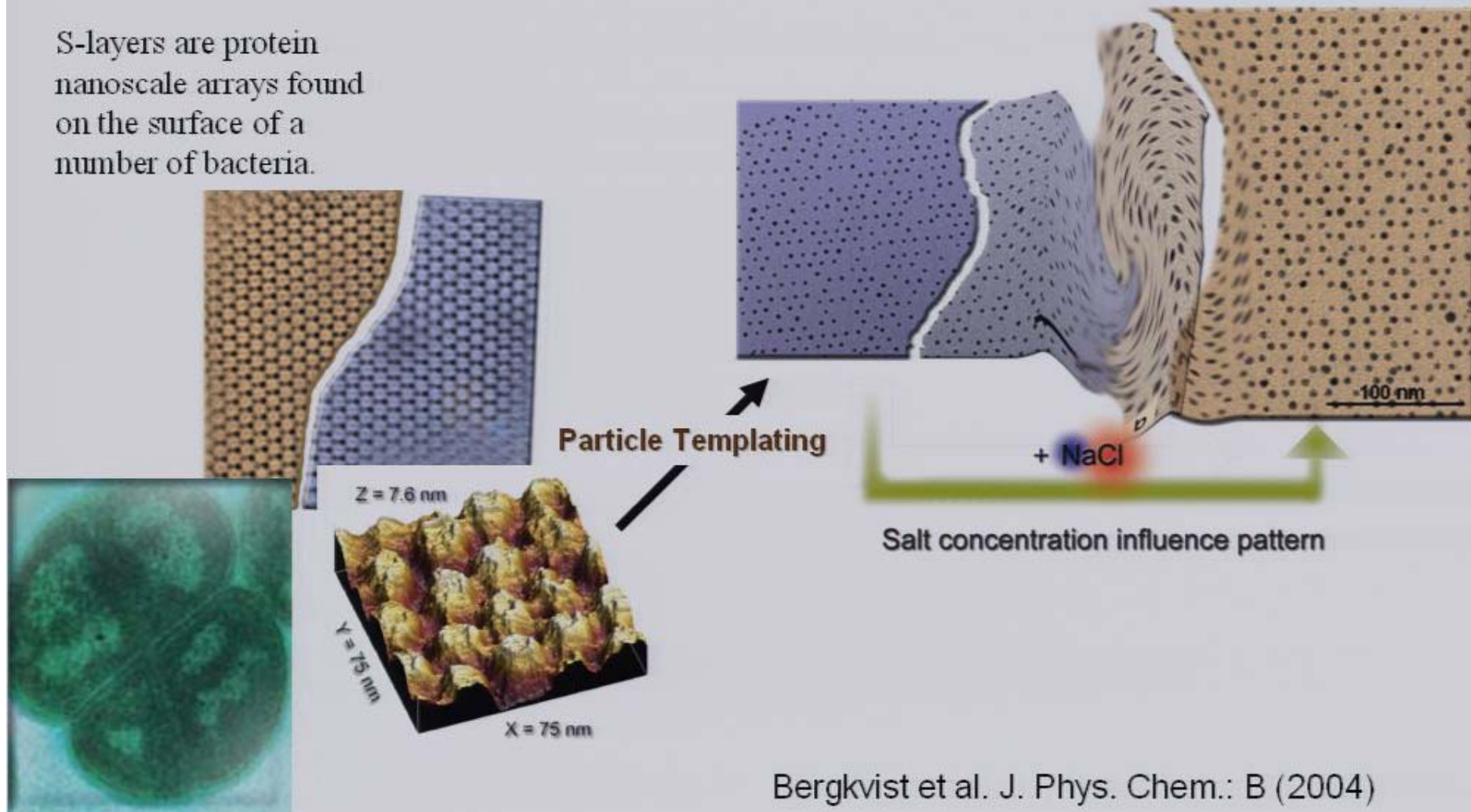
dendrimers



Science 305 (2004)

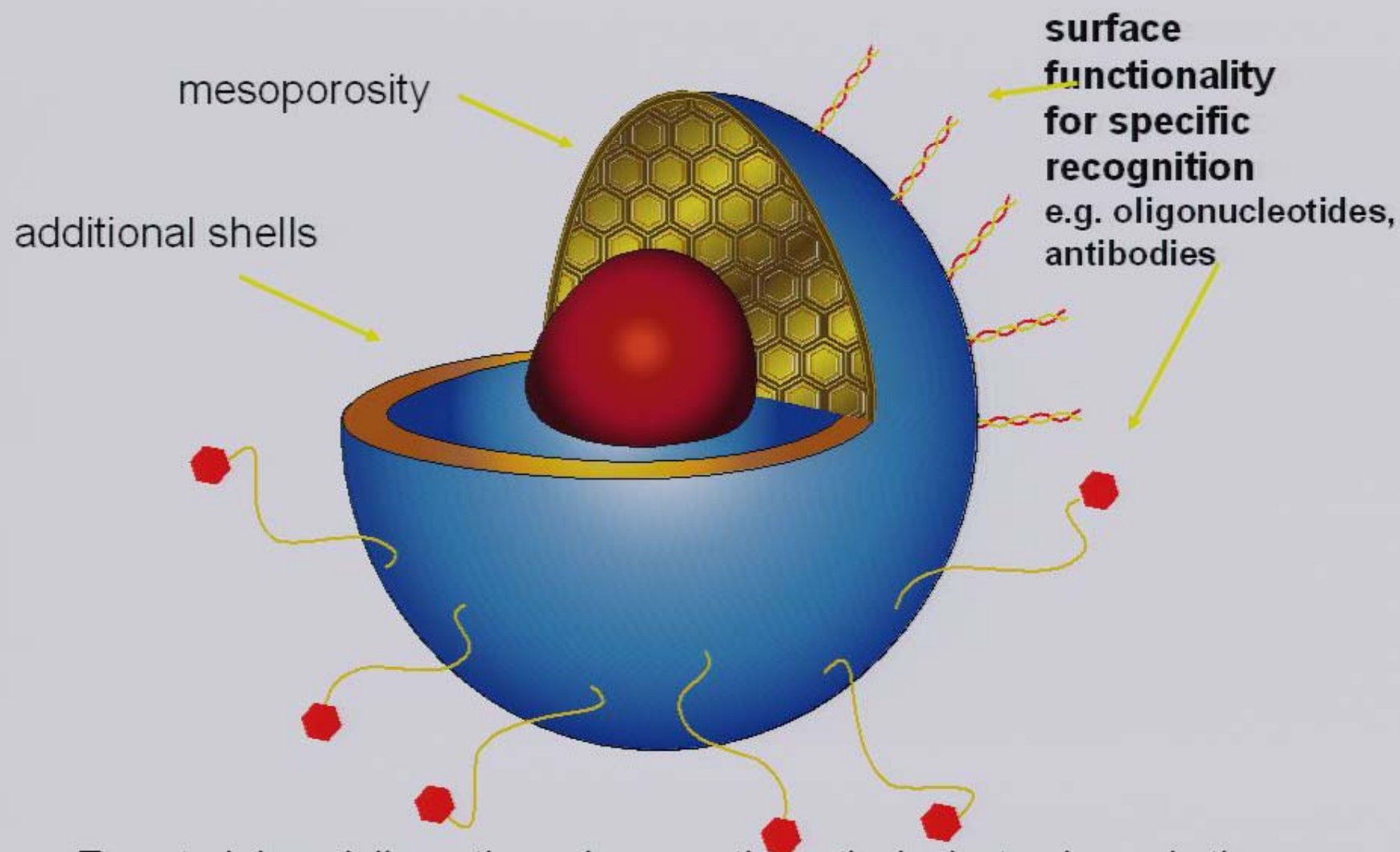
Bionanofabrication of Ordered Nanoparticle Arrays

S-layers are protein nanoscale arrays found on the surface of a number of bacteria.



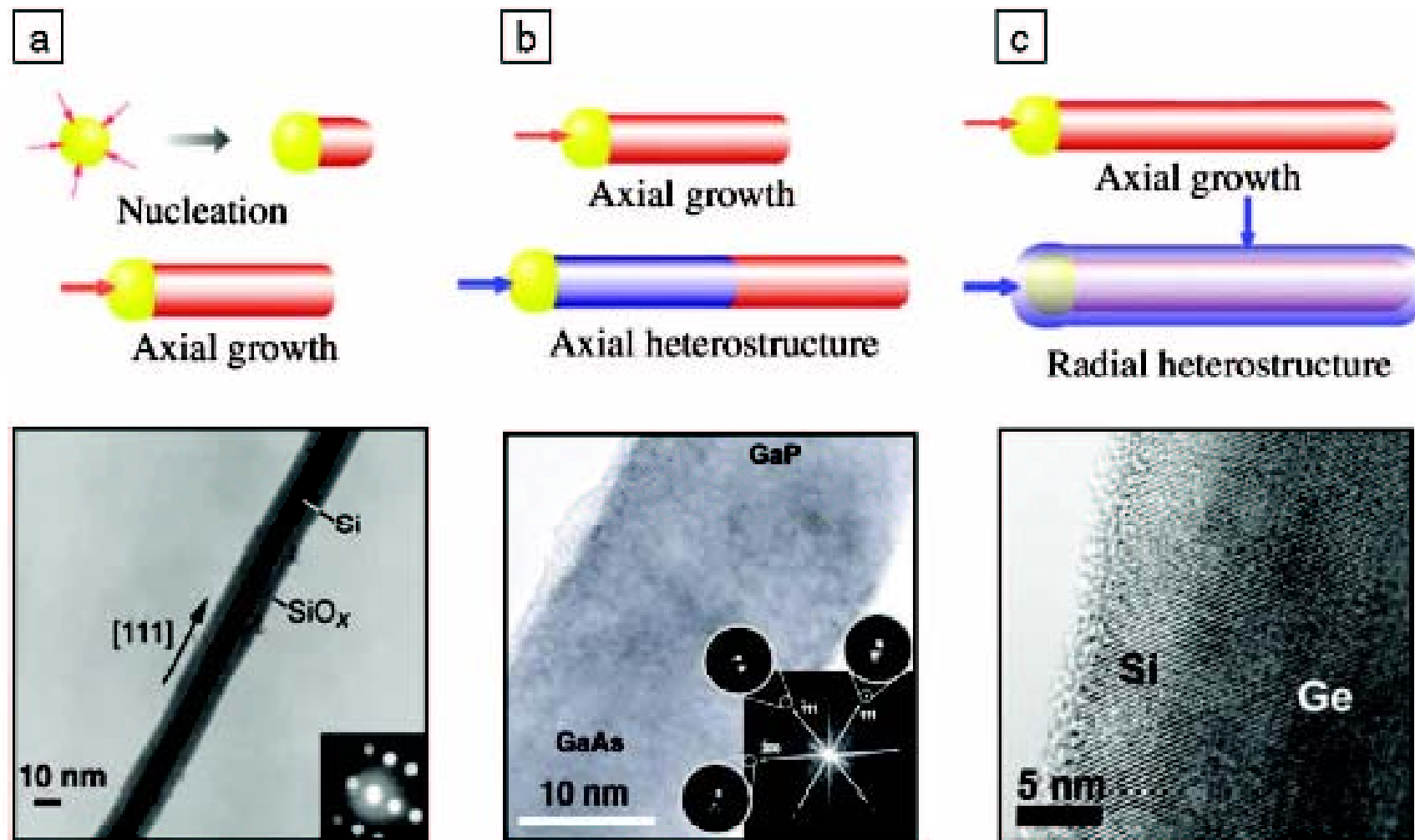
Bergkvist et al. J. Phys. Chem.: B (2004)

Built-In Multifunctionality



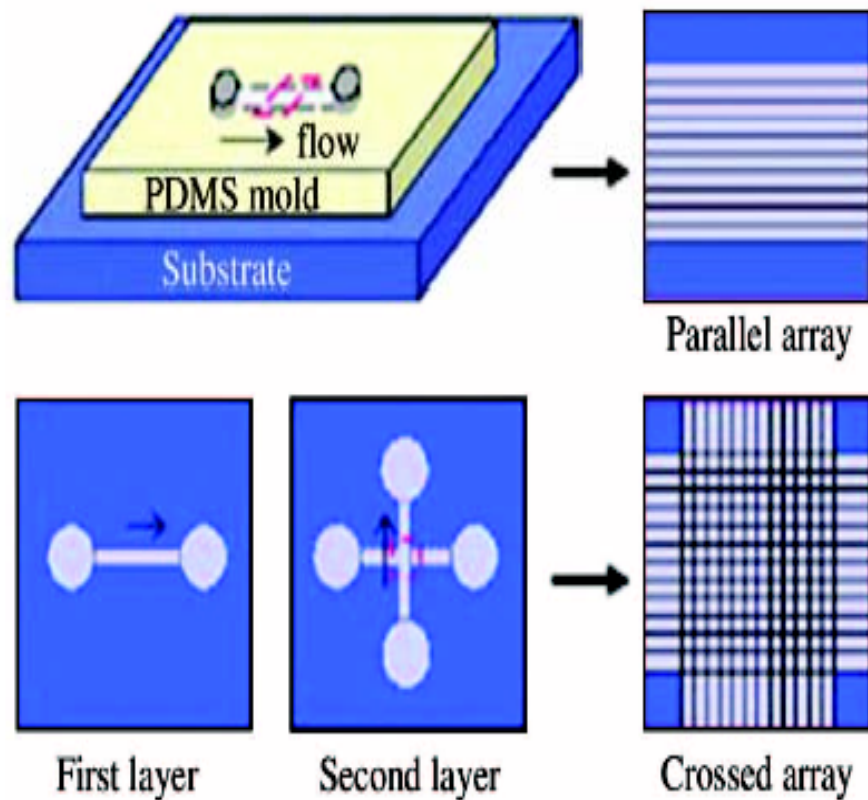
Targeted drug delivery through magnetic, optical, electronic, and other means for activation and control

SINGLE-CRYSTAL SEMICONDUCTOR NANOWIRES

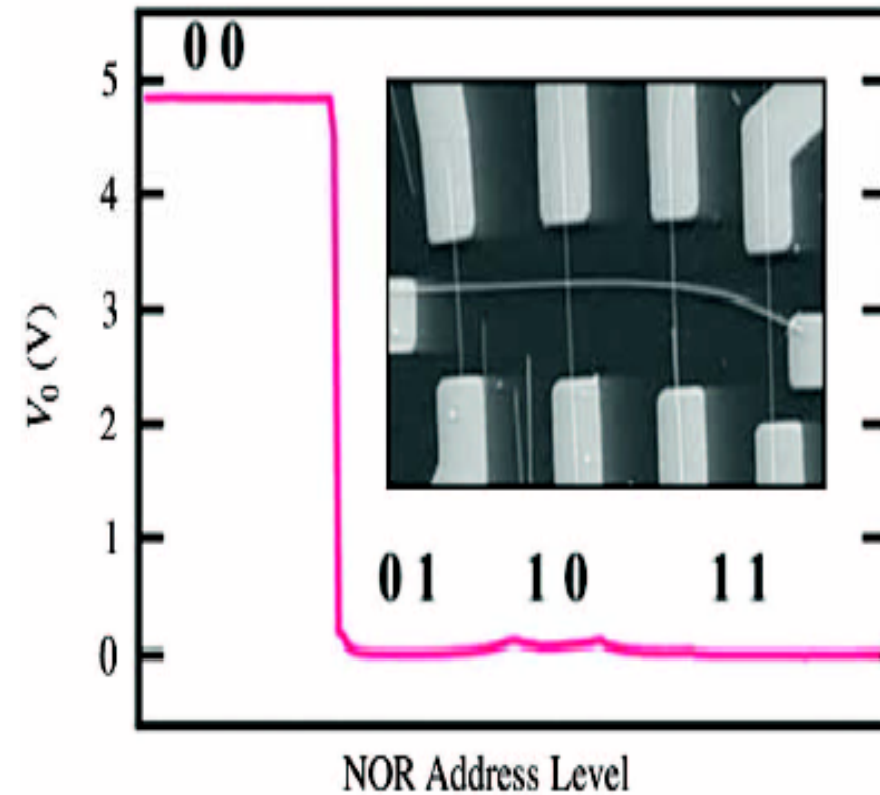


INTEGRATED NANOWIRE ELECTRONICS

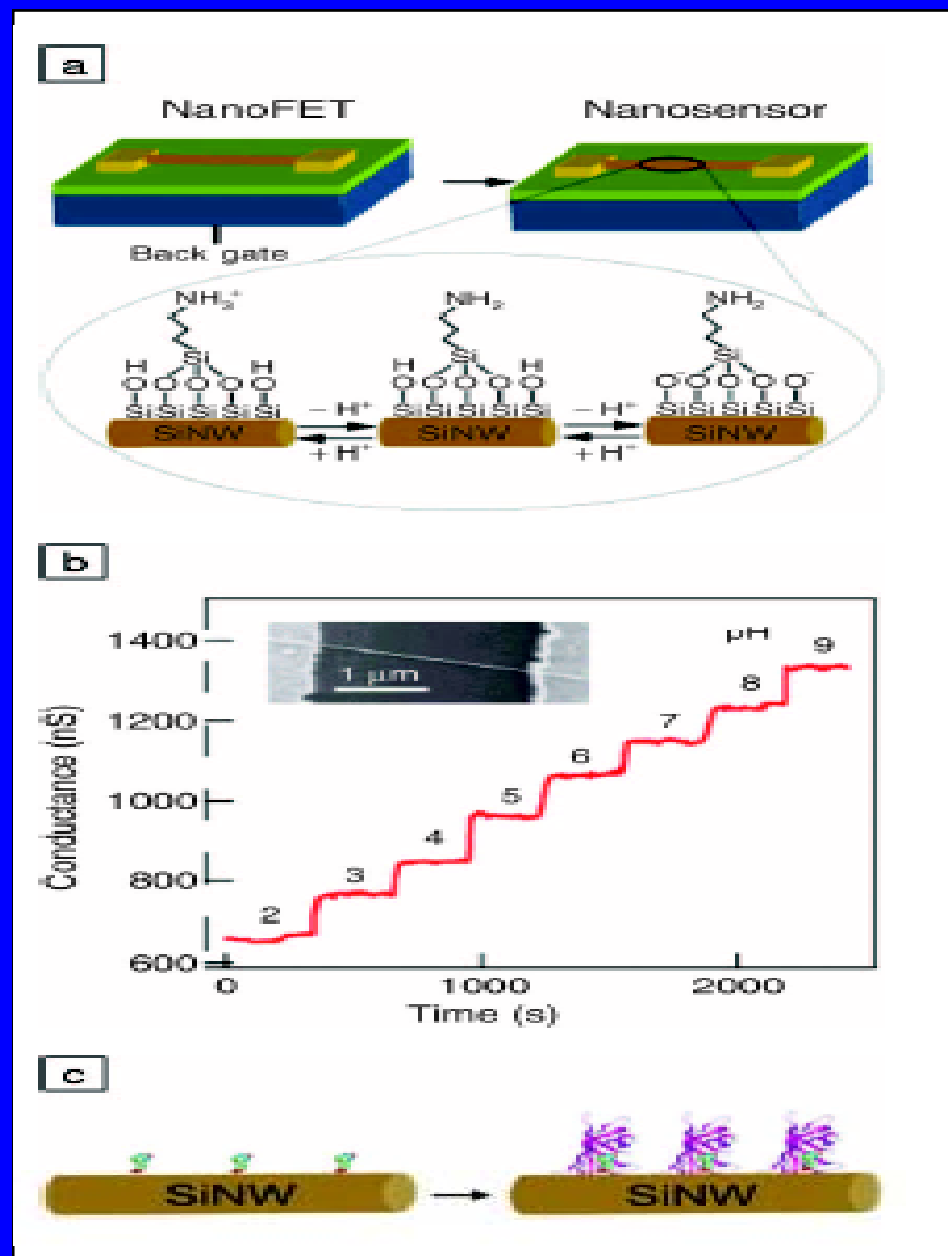
a



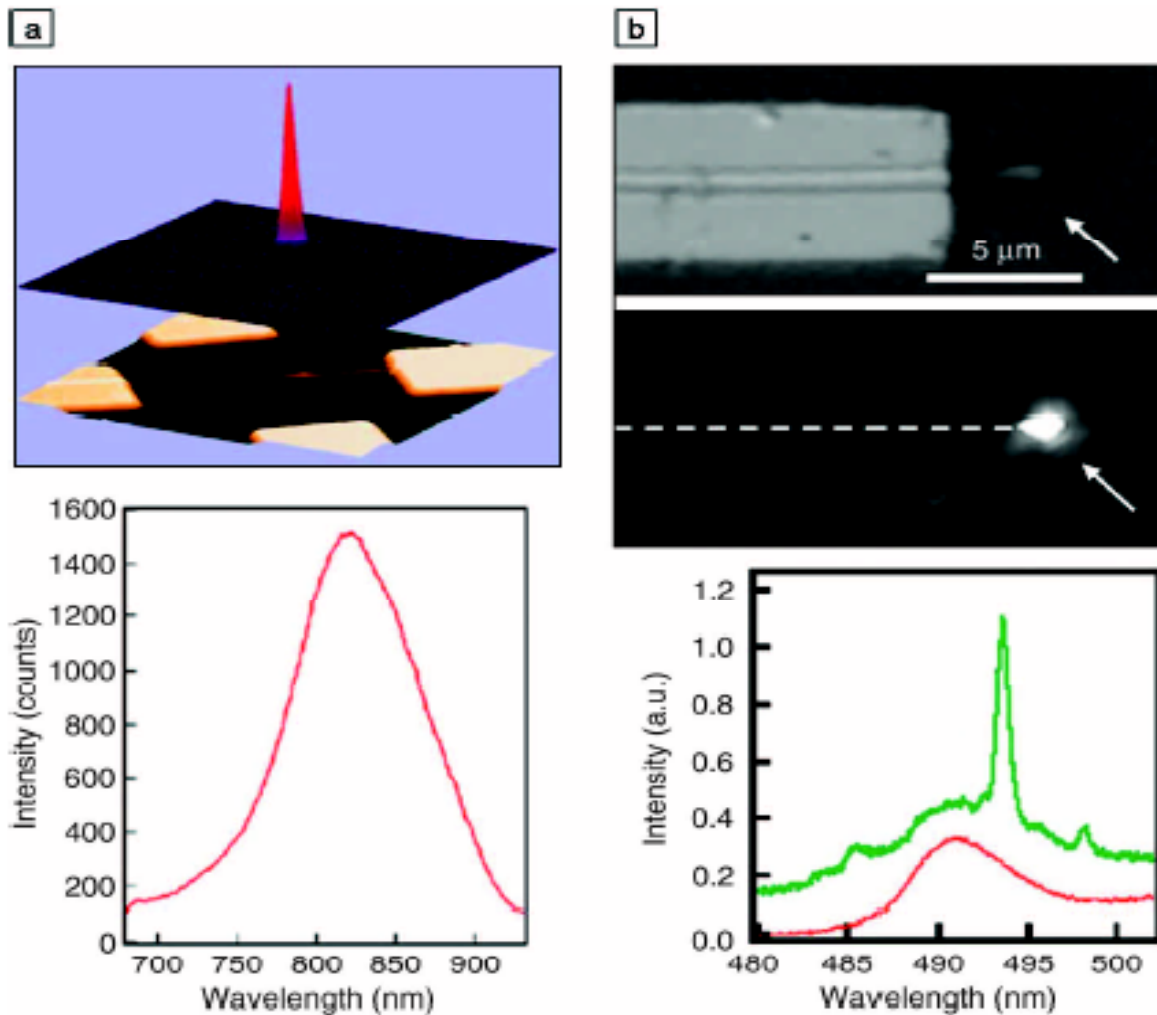
b



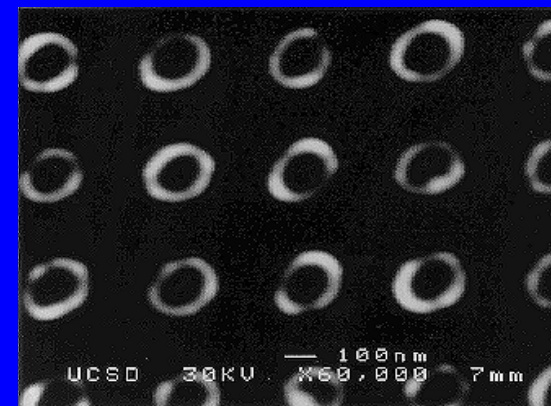
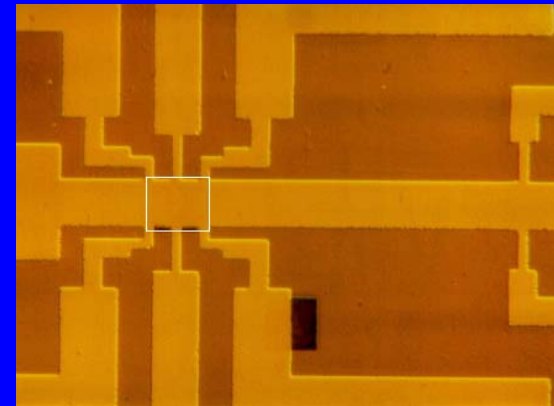
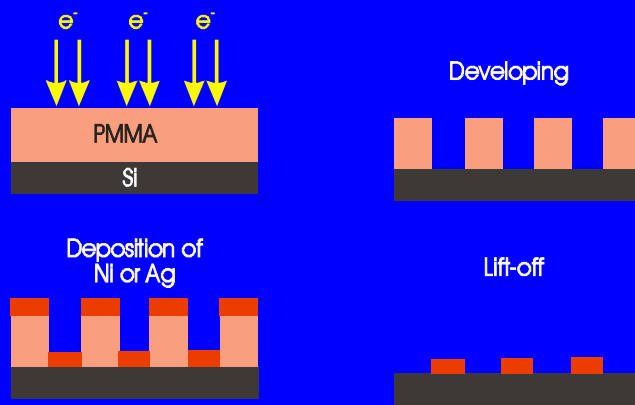
Silicon nanowire (SiNW) nanosensors



NANOWIRE PHOTONIC DEVICES

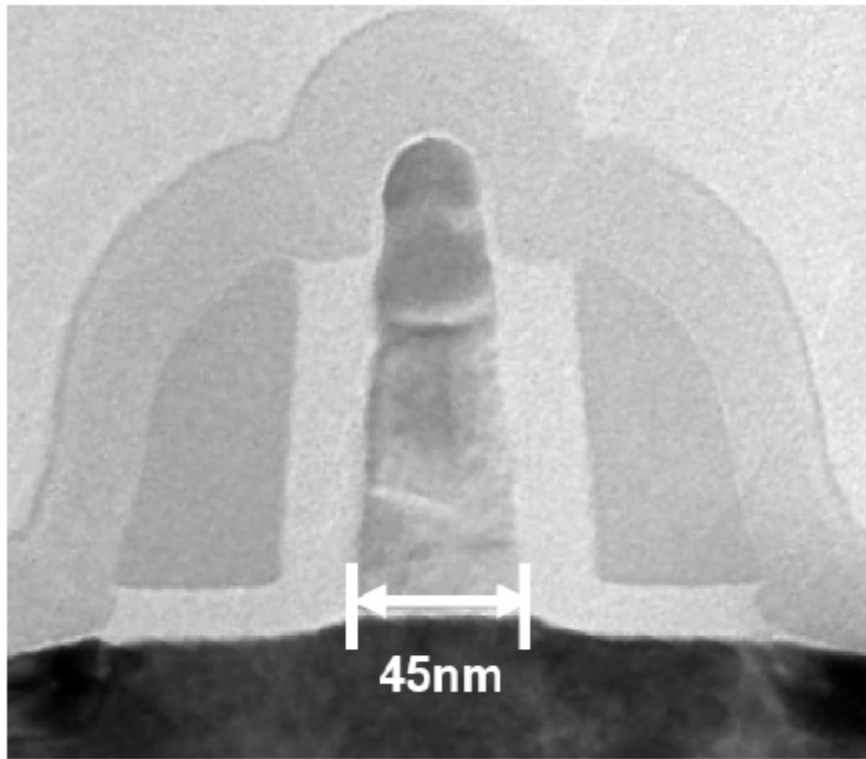


PUNTOS MAGNÉTICOS NANOMÉTRICOS



P. Prieto et al PRB 2000

BARRERAS DE 45 nm PARA DISPOSITIVOS MPU/CPU L-90nm

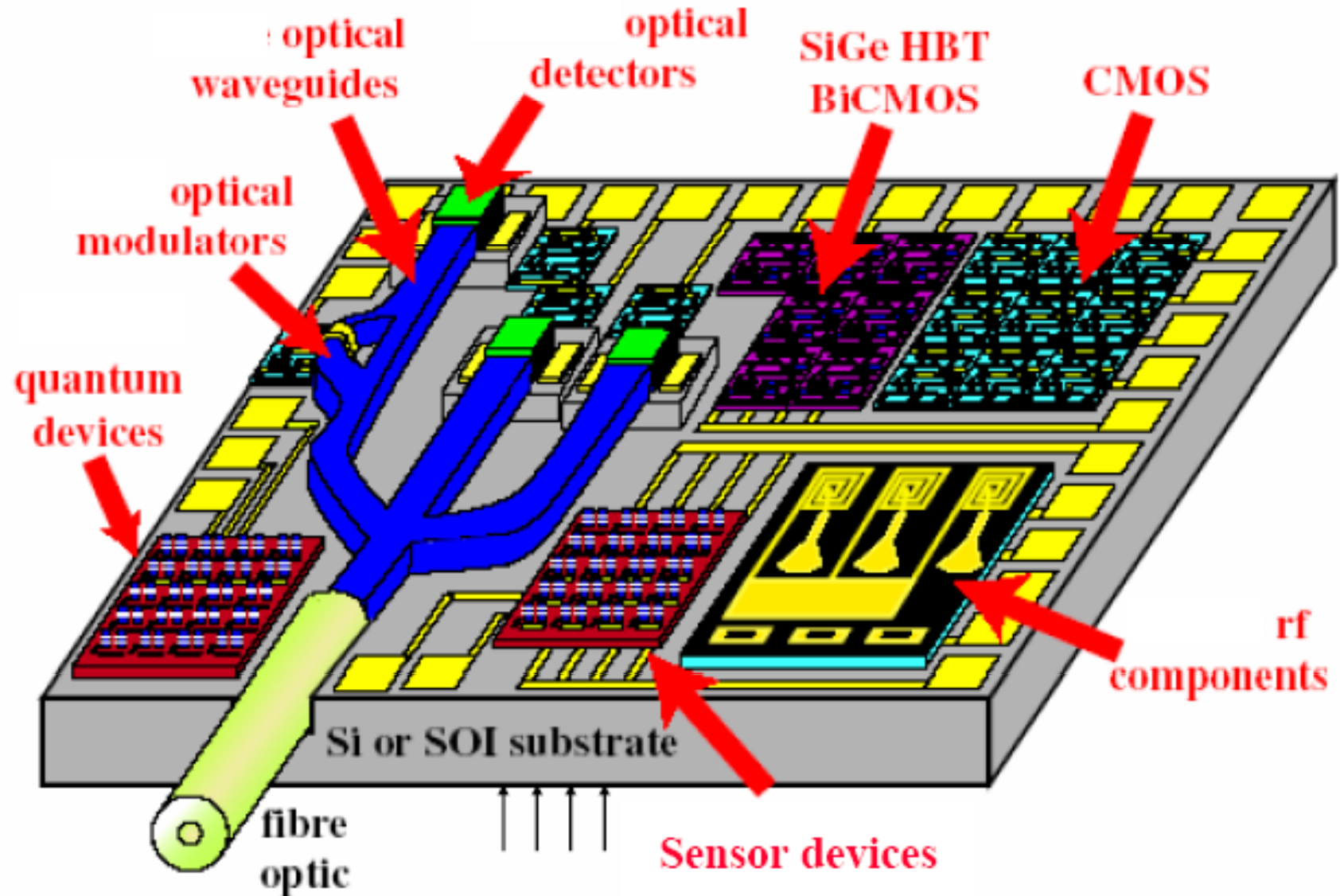


Parámetros de escalamiento de un dispositivo

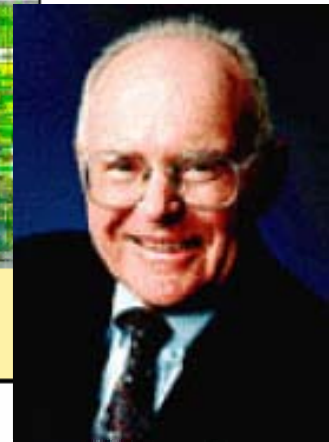
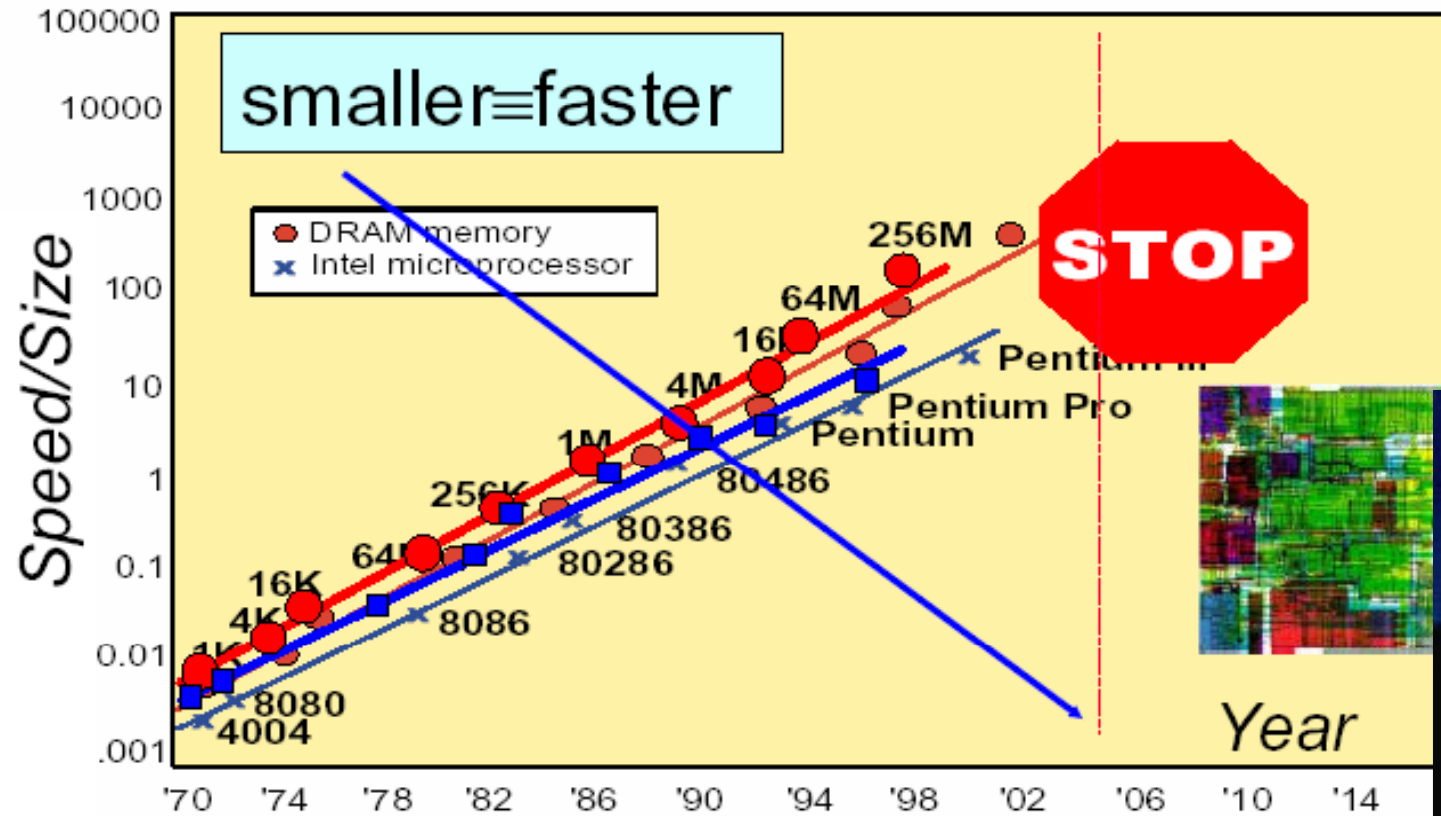
- Longitud de la barrera
- Voltaje aplicado
- Área del dispositivo
- tiempo de retraso
- Consumo de potencia

La longitud de la barrera de un MOSFET: 90 nm definidos en la mascara.
La longitud real es de 45 nm luego del proceso (143-330 átomos de Si)₁₉

Anatomía de un CHIP óptico



OTRO NANO-MUNDO: TECNOLOGIA DEL CHIP DE Si



- ✓ **La ley de Moore:** el número de transistores encapsulados en un chip se duplica cada 18 meses
- ✓ Transistores mucho más pequeños, más rápidos, de alta densidad, bajo consumo de energía